

Chapter 7

Topological Spintronics

韩伟

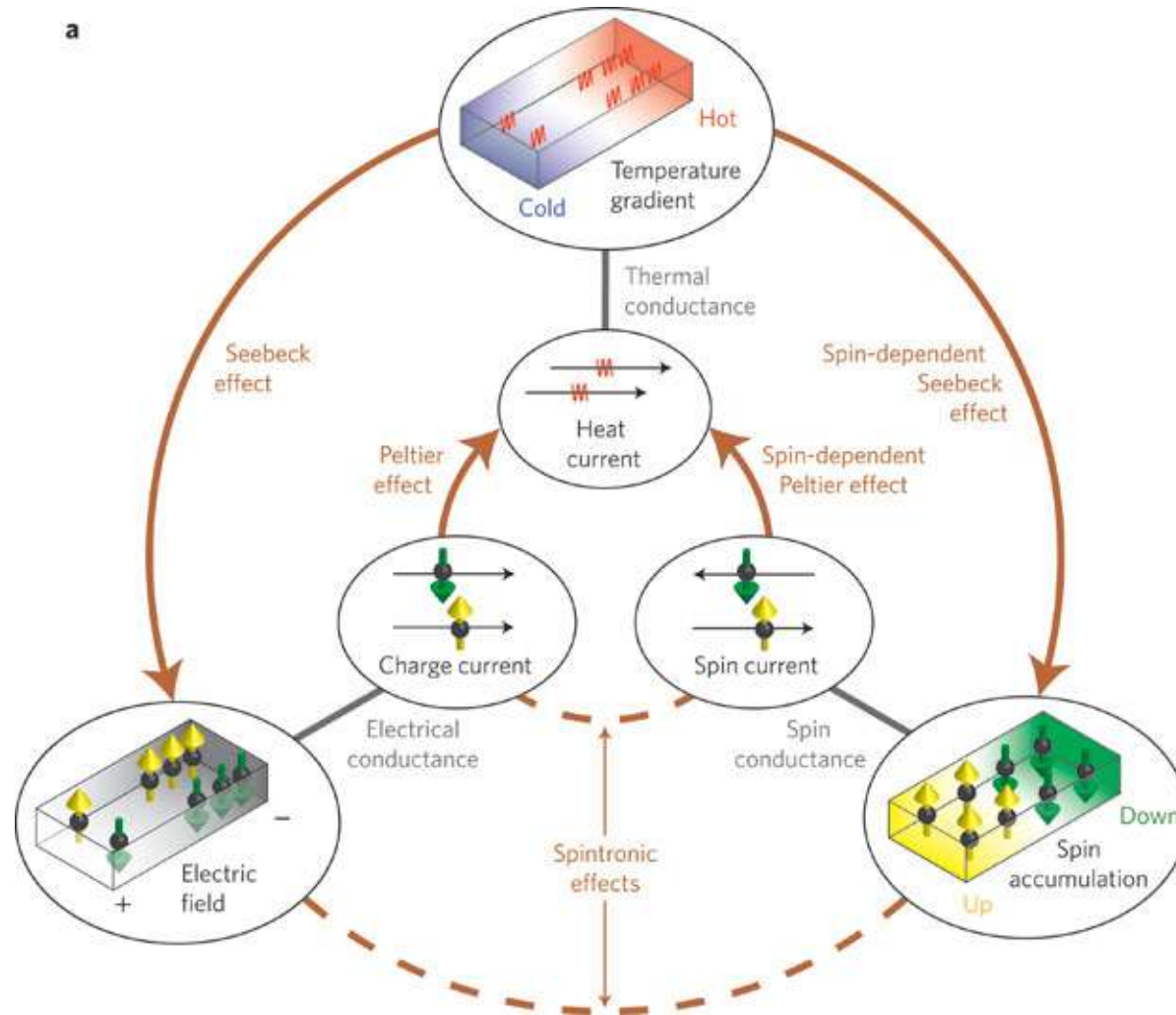
量子材料科学中心

2018年12月7日

Review of last class

- 1. Seebeck and Peltier effect**
- 2. Spin Seebeck effect**
- 3. Spin Peltier effect**
- 4. Thermal spin injection**
- 5. Thermal spin torque**
- 6. Spin energy**

Review of last class



Goennenwein & Bauer, Nature Nanotech. (2012)

Outline

1. Topology

2. Quantum anomalous Hall effect

3. Skyrmions

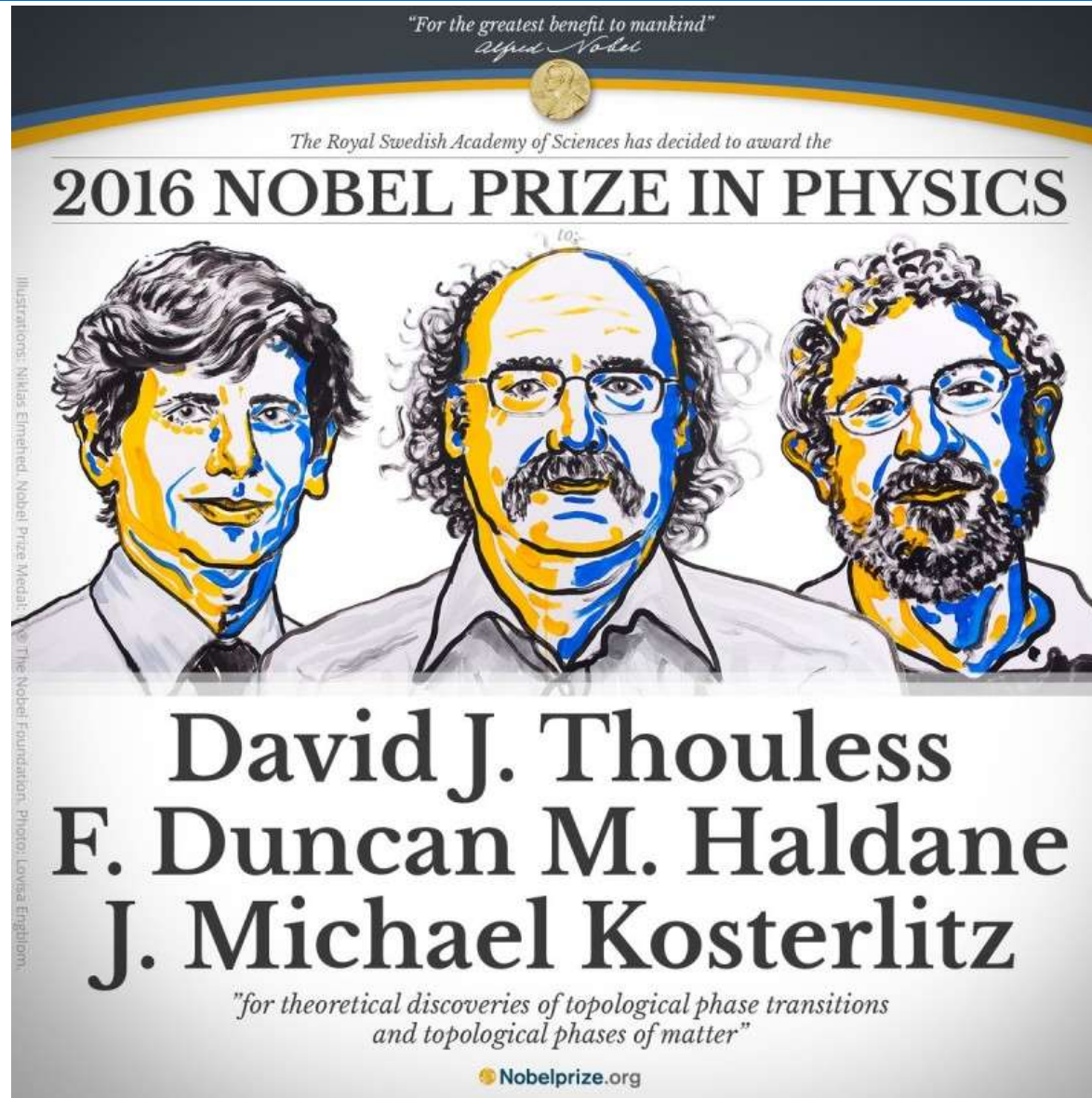
4. Spin-momentum locking of 3D TI

- **Spin injection**
- **Spin orbit torque**
- **Spin Seebeck effect**

Outline

1. Topology

Topology



Topology

”for theoretical discoveries of topological phase transitions and topological phases of matter”

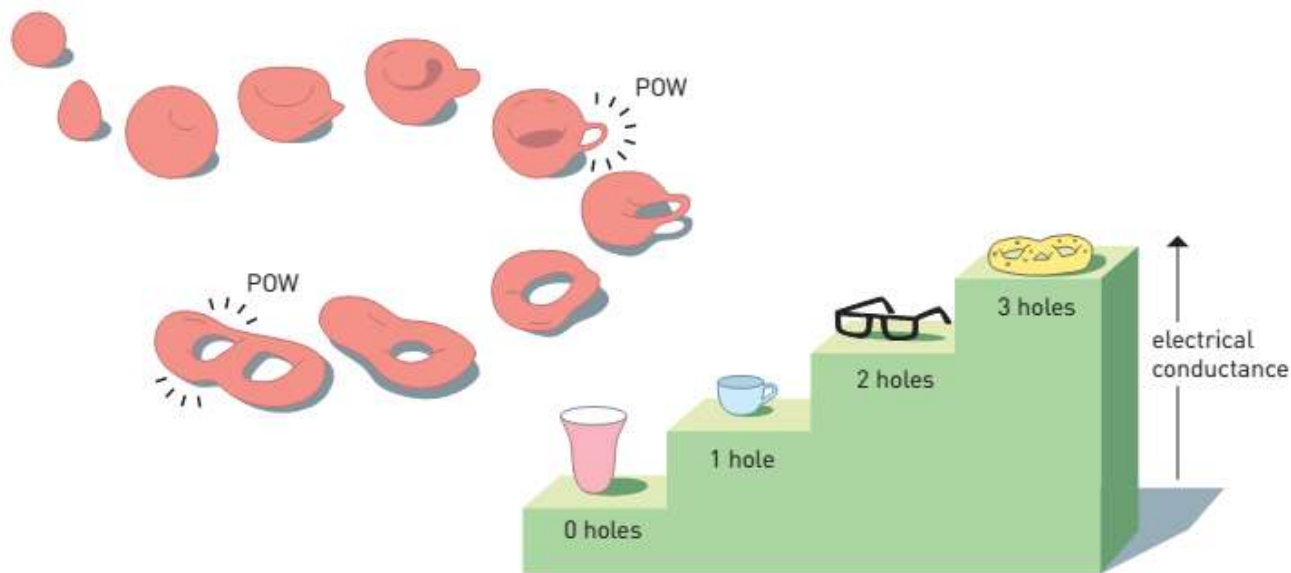
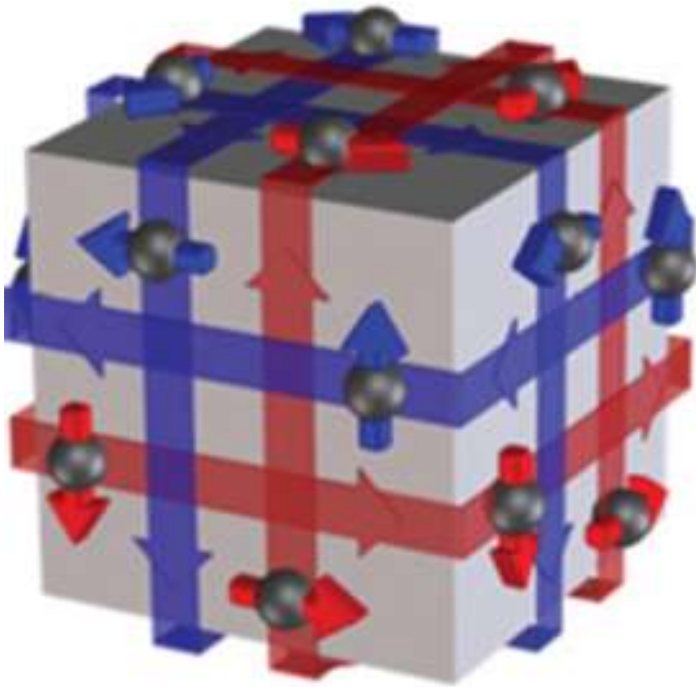


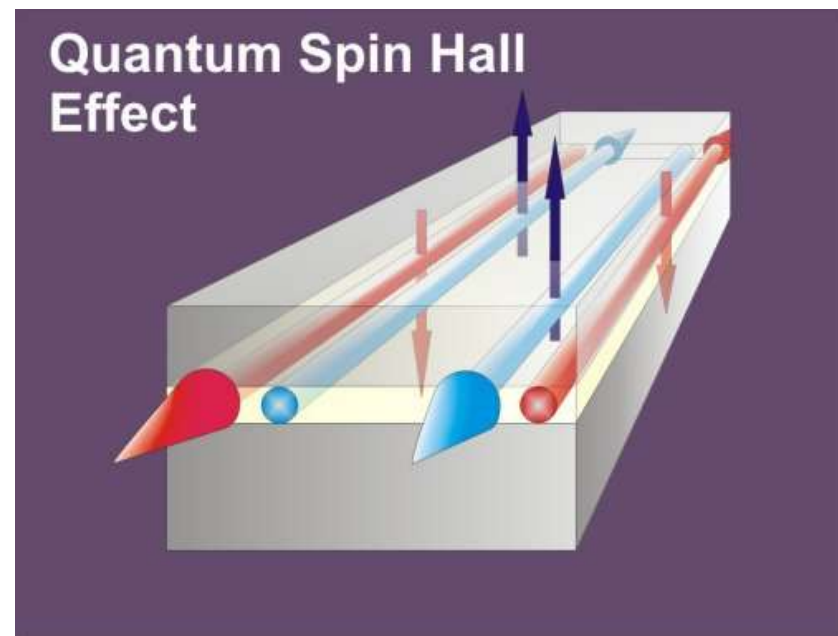
Illustration: ©Johan Jarnestad/The Royal Swedish Academy of Sciences

Topological insulator

3D Topological insulator

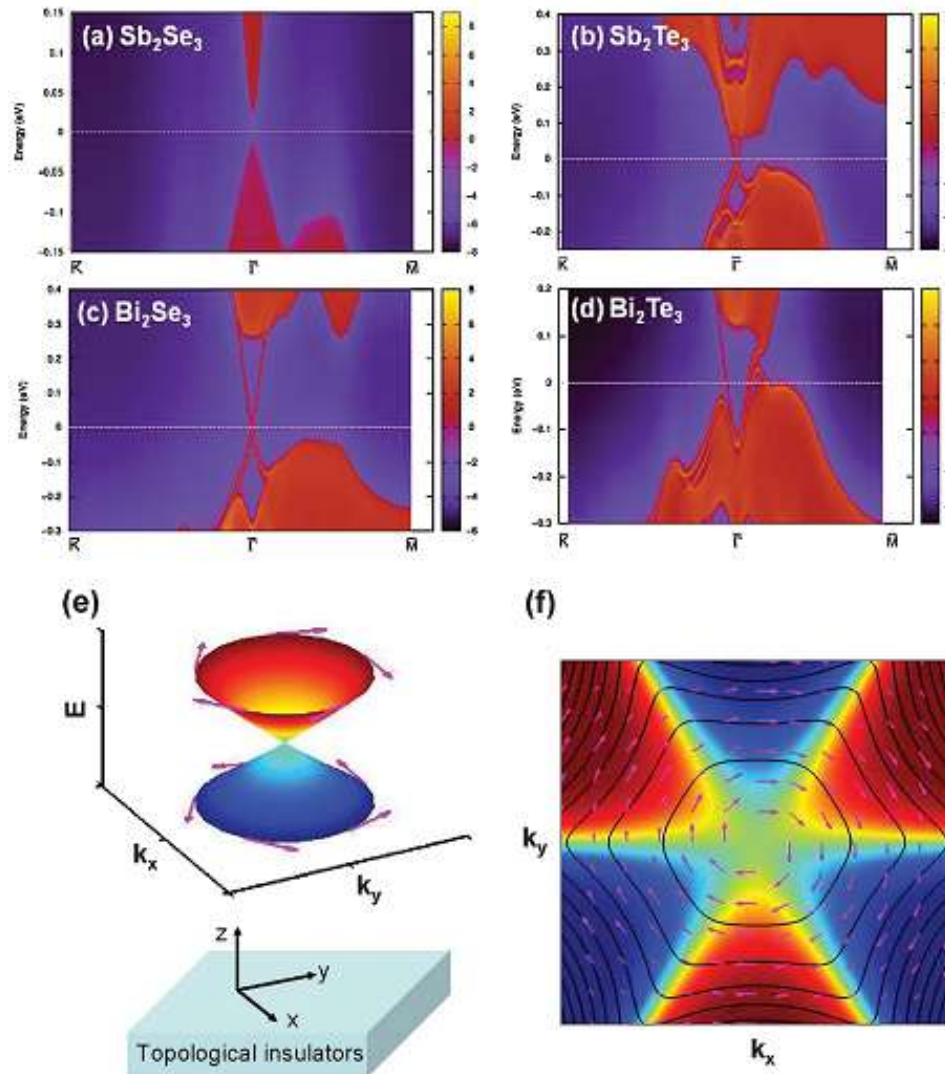


2D Topological insulator

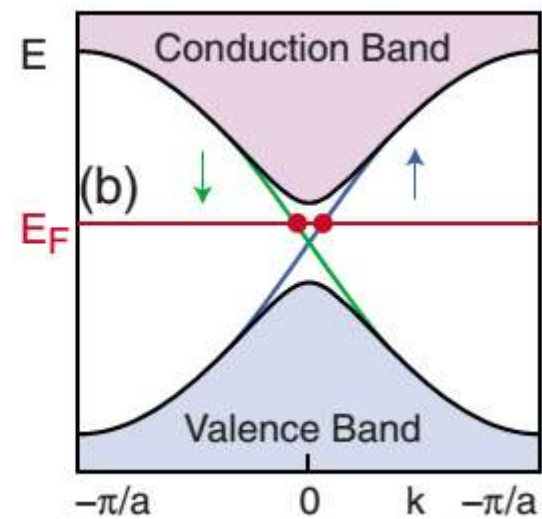
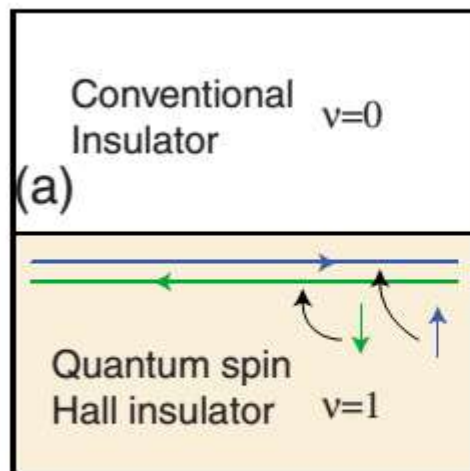
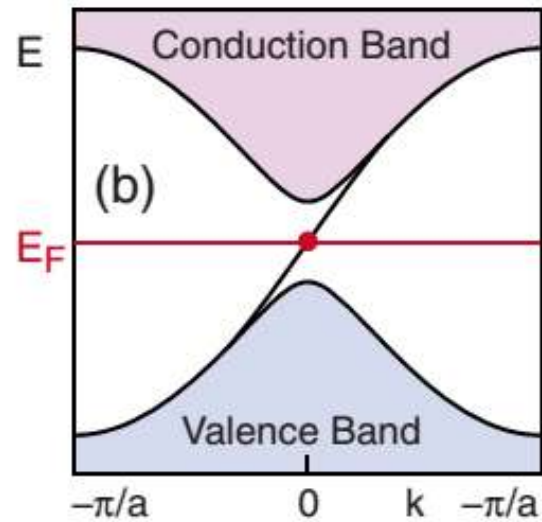
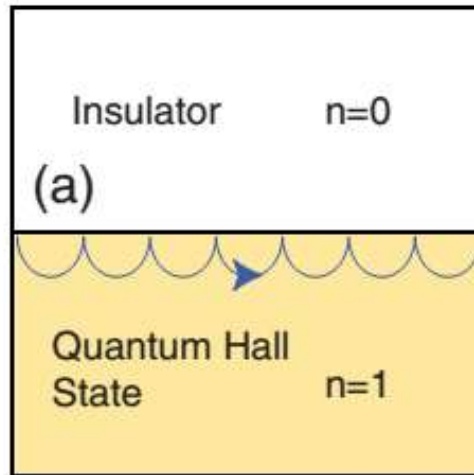


Hasan & Kane, Rev Mod Phys (2009)
Qi & Zhang, Rev Mod Phys (2011)

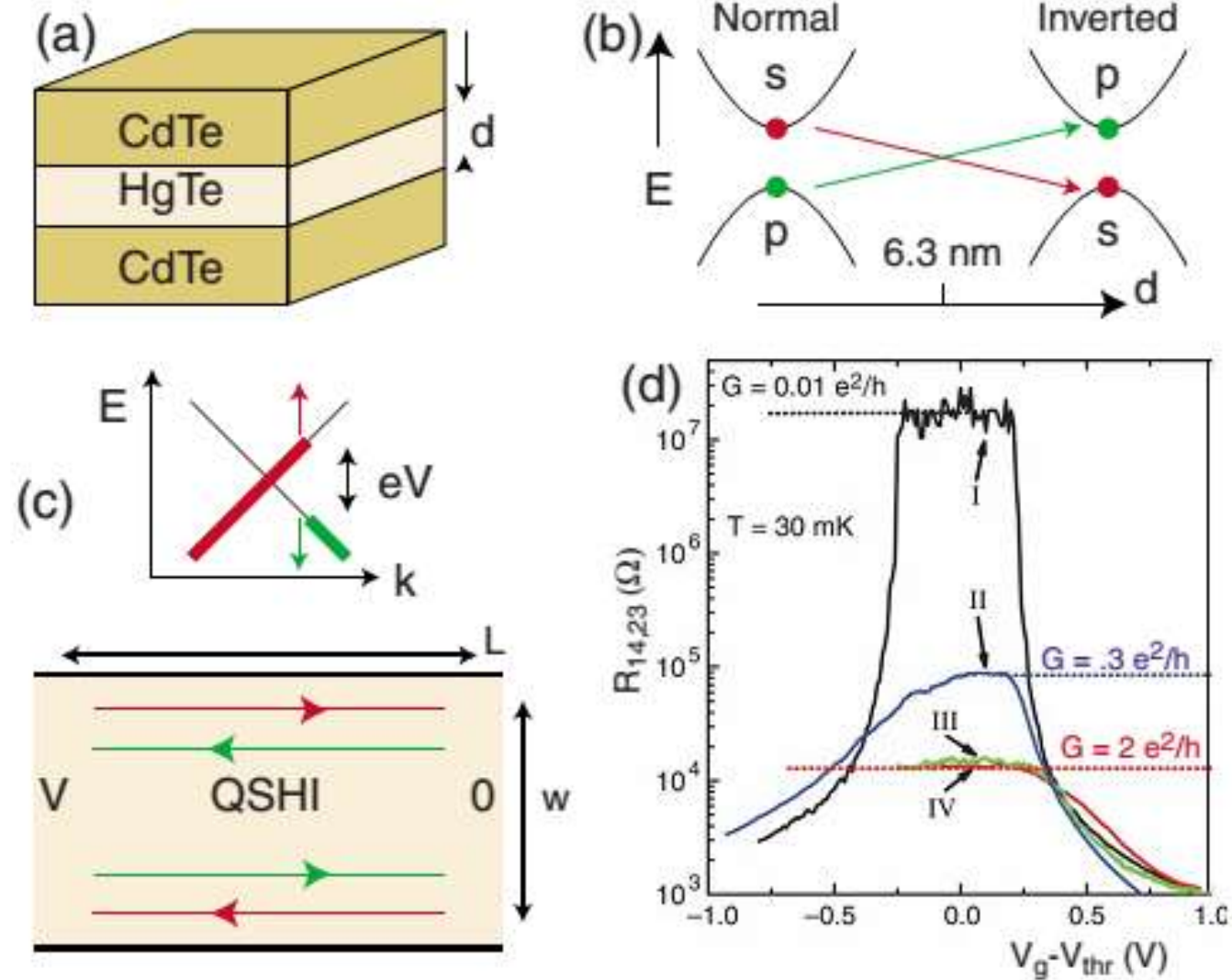
3D Topological insulator



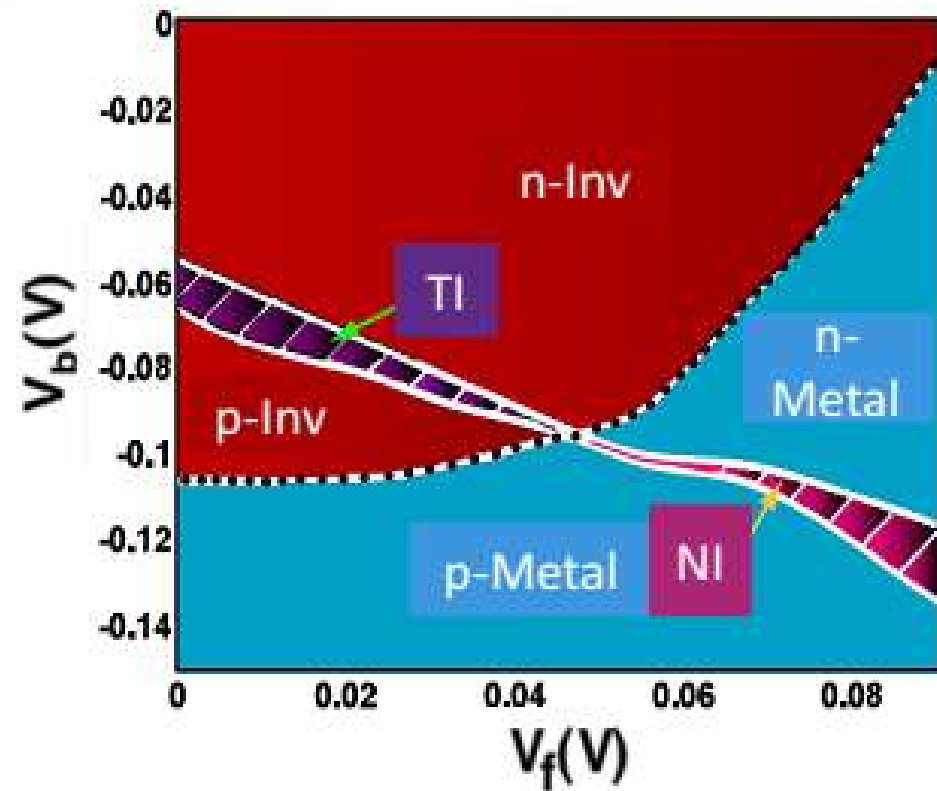
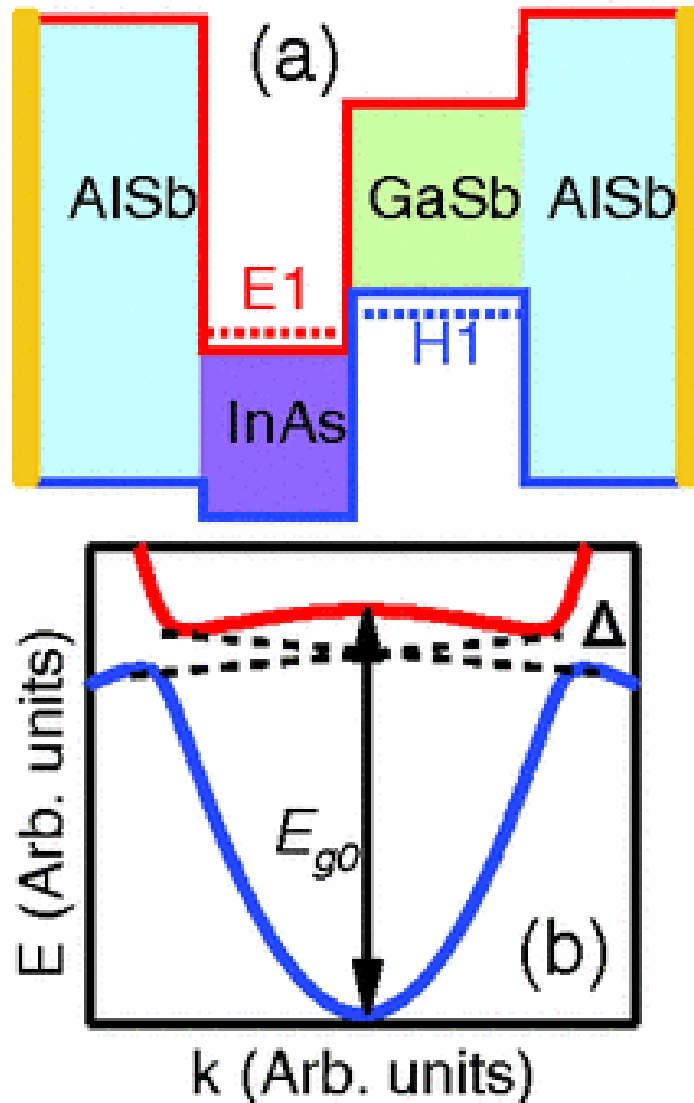
2D Topological insulator



2D Topological insulator



2D Topological insulator

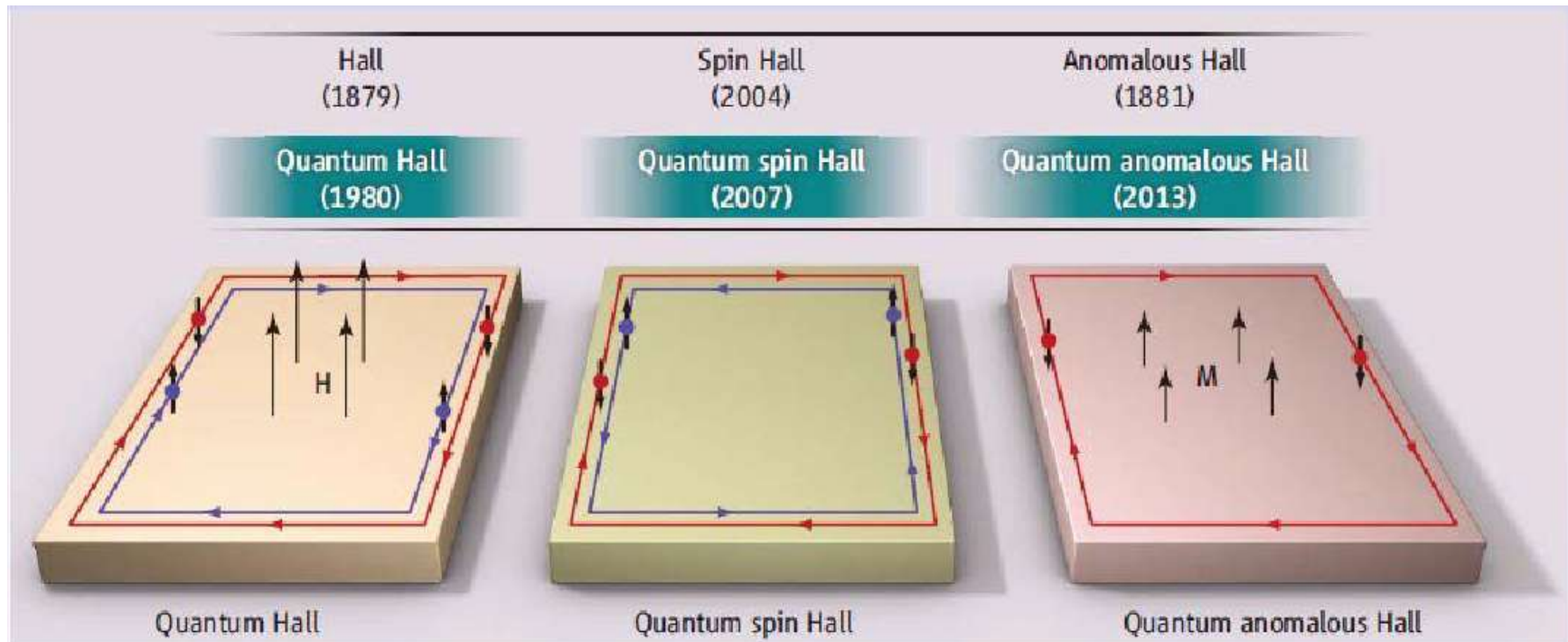


From Prof. Du Ruirui 12

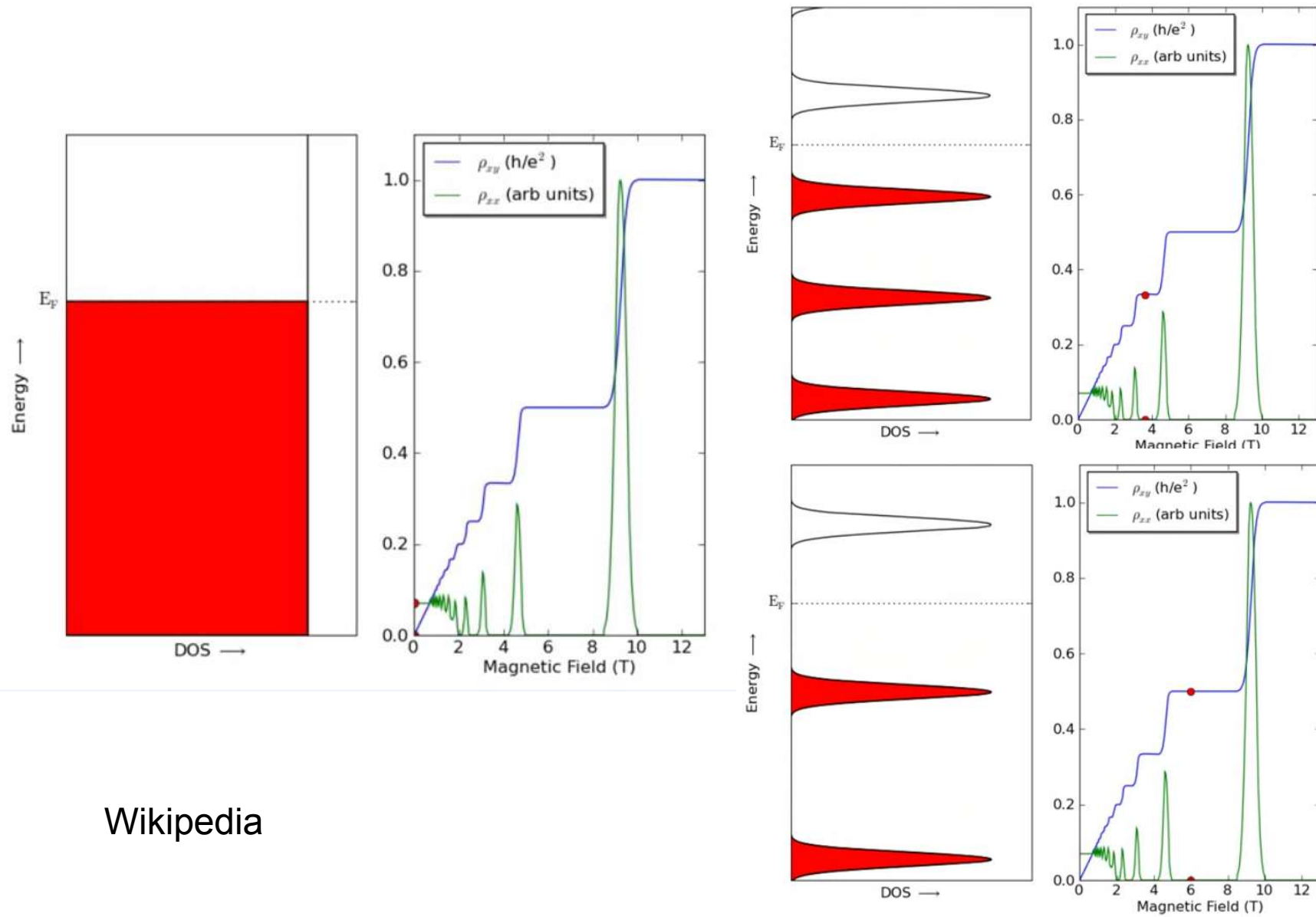
Outline

2. Quantum anomalous Hall effect

Hall effect



Quantum Hall effect



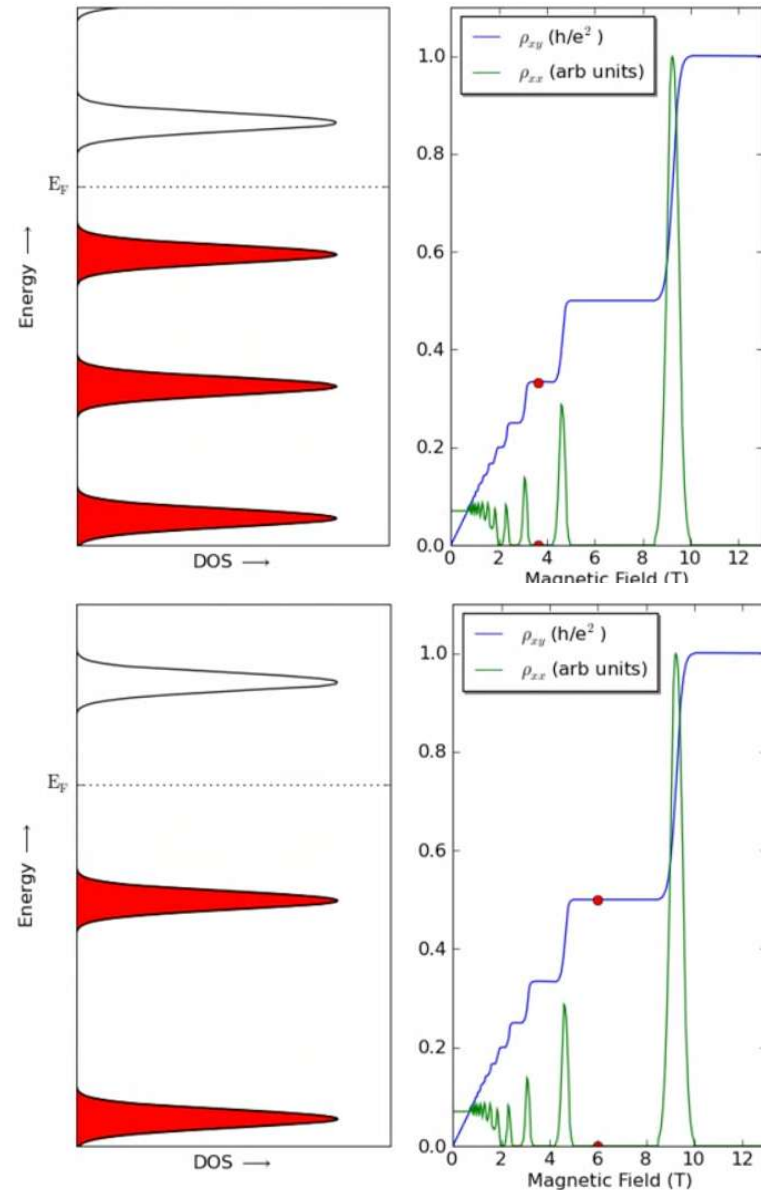
Wikipedia

Quantum Hall effect

A Strong magnetic field is needed!

Whether a magnetic field is necessary?

YES!



Quantum Hall effect

VOLUME 61, NUMBER 18

PHYSICAL REVIEW LETTERS

31 OCTOBER 1988

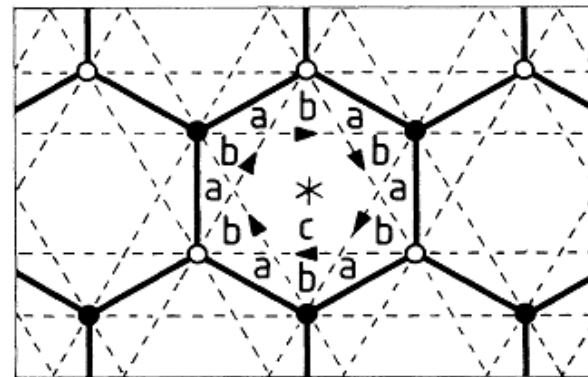
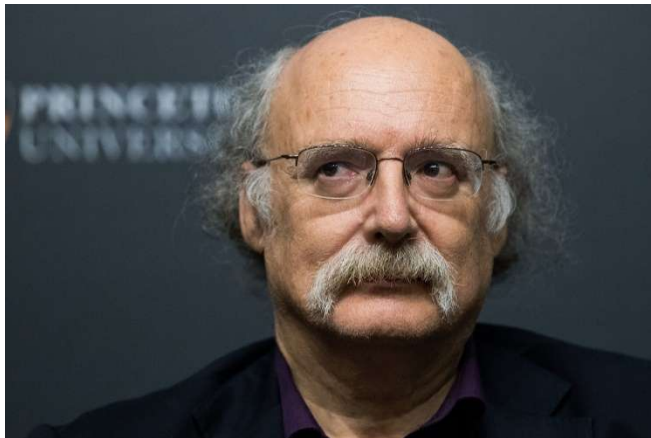
Model for a Quantum Hall Effect without Landau Levels: Condensed-Matter Realization of the “Parity Anomaly”

F. D. M. Haldane

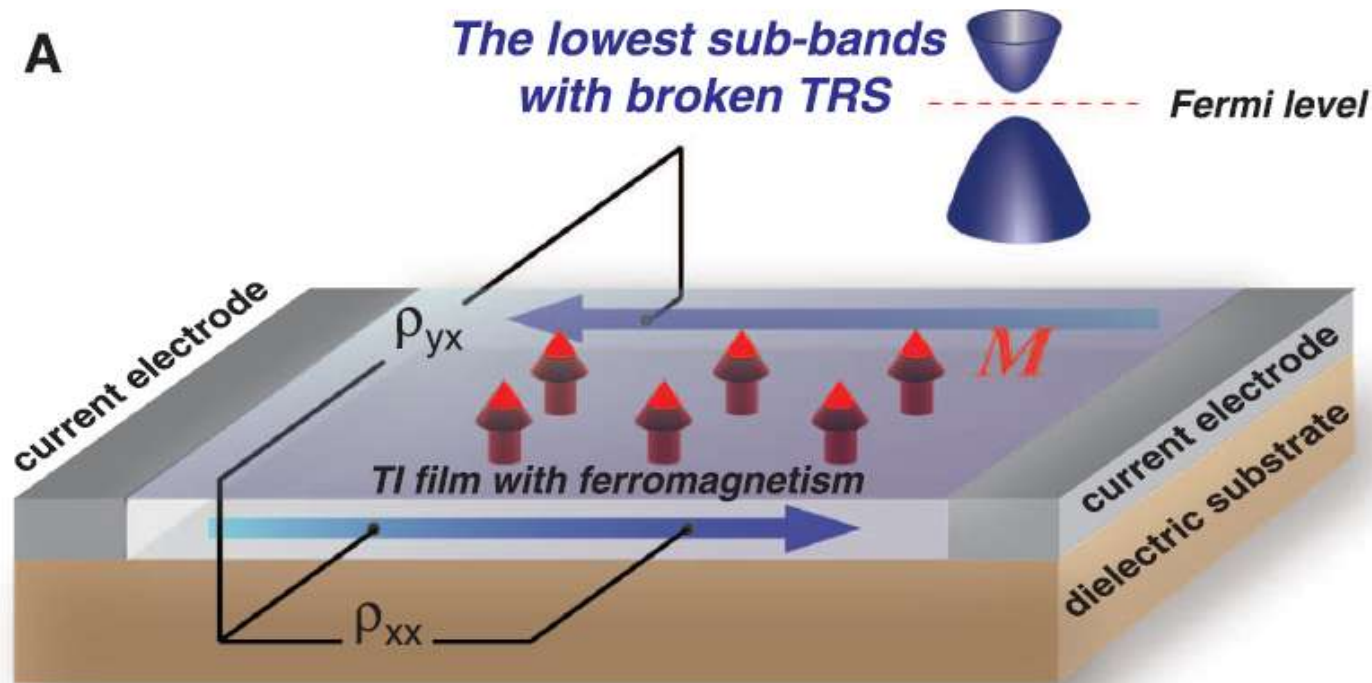
Department of Physics, University of California, San Diego, La Jolla, California 92093

(Received 16 September 1987)

A two-dimensional condensed-matter lattice model is presented which exhibits a nonzero quantization of the Hall conductance σ^{xy} in the *absence* of an external magnetic field. Massless fermions *without spectral doubling* occur at critical values of the model parameters, and exhibit the so-called “parity anomaly” of (2+1)-dimensional field theories.

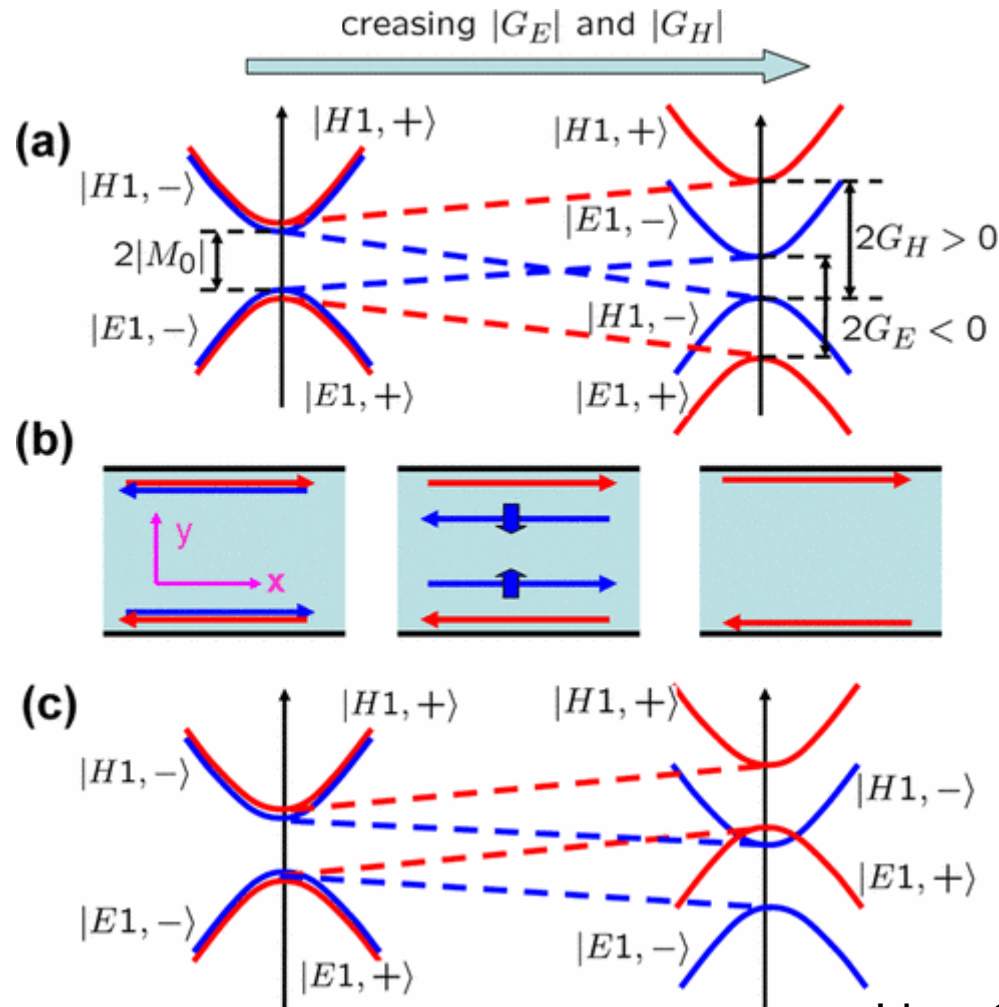


Quantum Hall effect



Quantum anomalous Hall effect

$\text{Hg}_{1-y}\text{Mn}_y\text{Te}$ Quantum Wells



Liu, et al, PRL (2008)₁₉

Quantum anomalous Hall effect

Hg_{1-y}Mn_yTe Quantum Wells

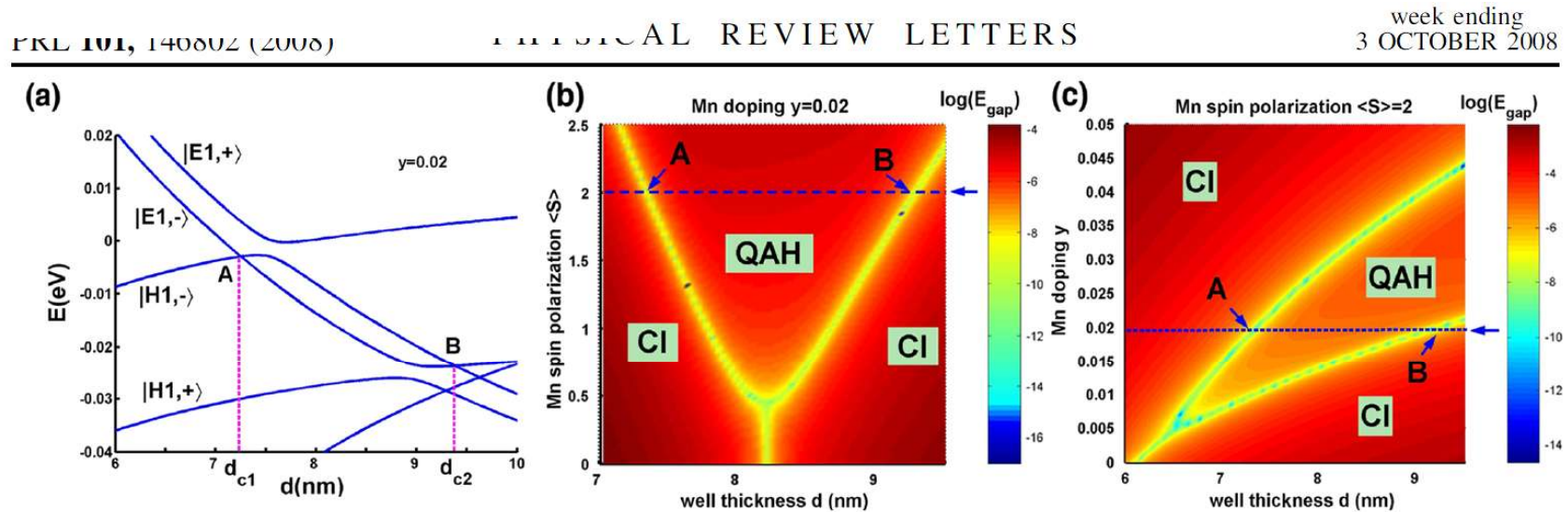
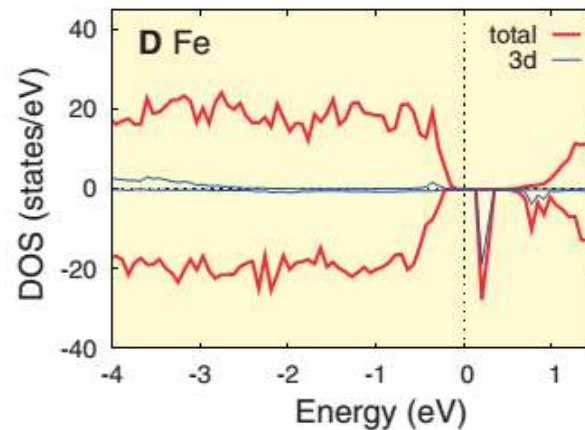
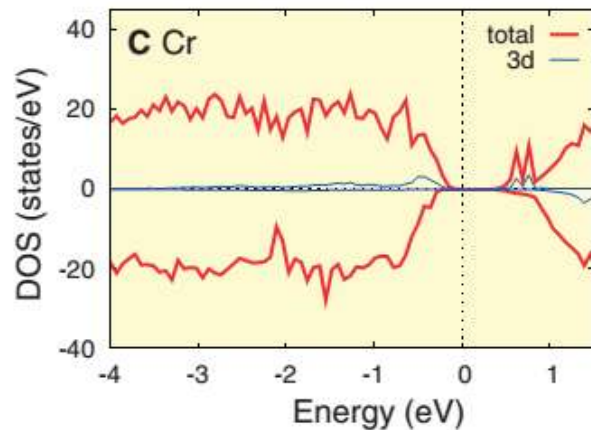
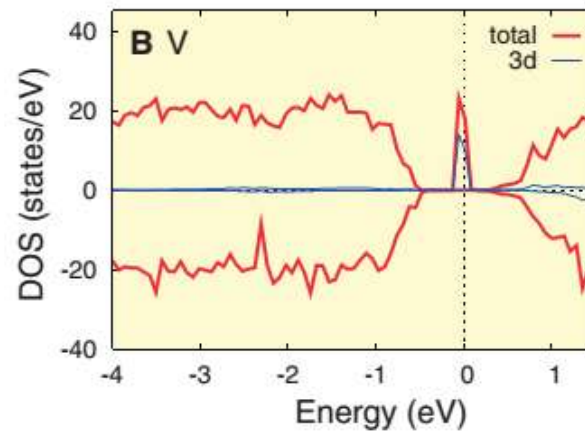
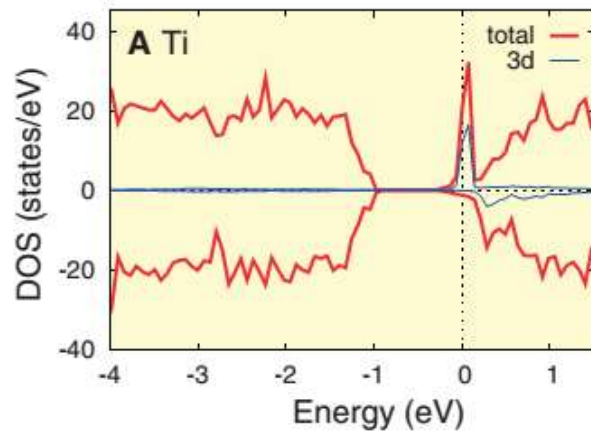


FIG. 2 (color online). (a) The energy levels for $|E1, \pm\rangle$ and $|H1, \pm\rangle$ are plotted as a function of the QW thickness. Two crossing points (A and B) are labeled in the figure. The energy gap ($\log(E_{\text{gap}})$ used here) is plotted as a function of the well thickness d versus the Mn magnetic moment $\langle S \rangle$ in (b), versus the Mn doping concentration y in (c). Dashed blue line in (b) or (c) refers to the line along which (a) is plotted. The points “A” and “B” correspond to the two Dirac-type crossing points. Two different phases, conventional insulator (CI) with $\sigma_H = 0$ and QAH state with $\sigma_H = -e^2/h$, are separated by the gap closing line in the figures.

Liu, et al, PRL (2008)

Quantum anomalous Hall effect

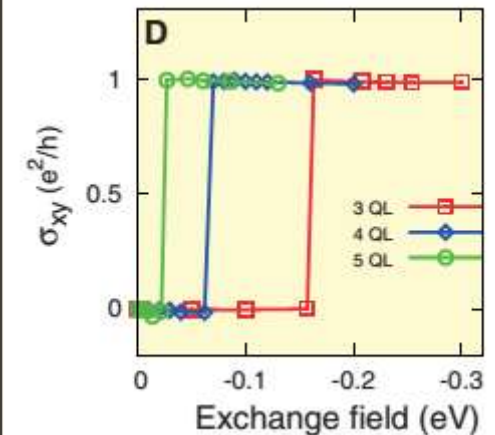
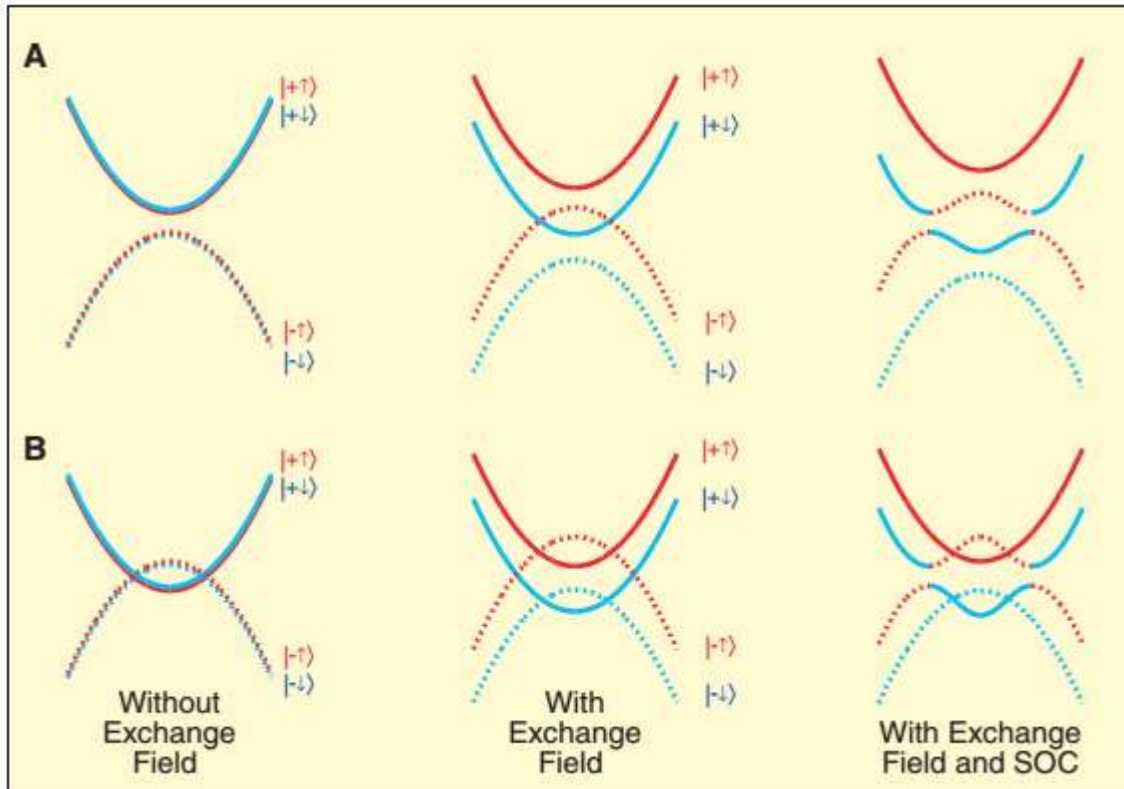
FM doped BiSeTe



Yu, et al, Science (2010)

Quantum anomalous Hall effect

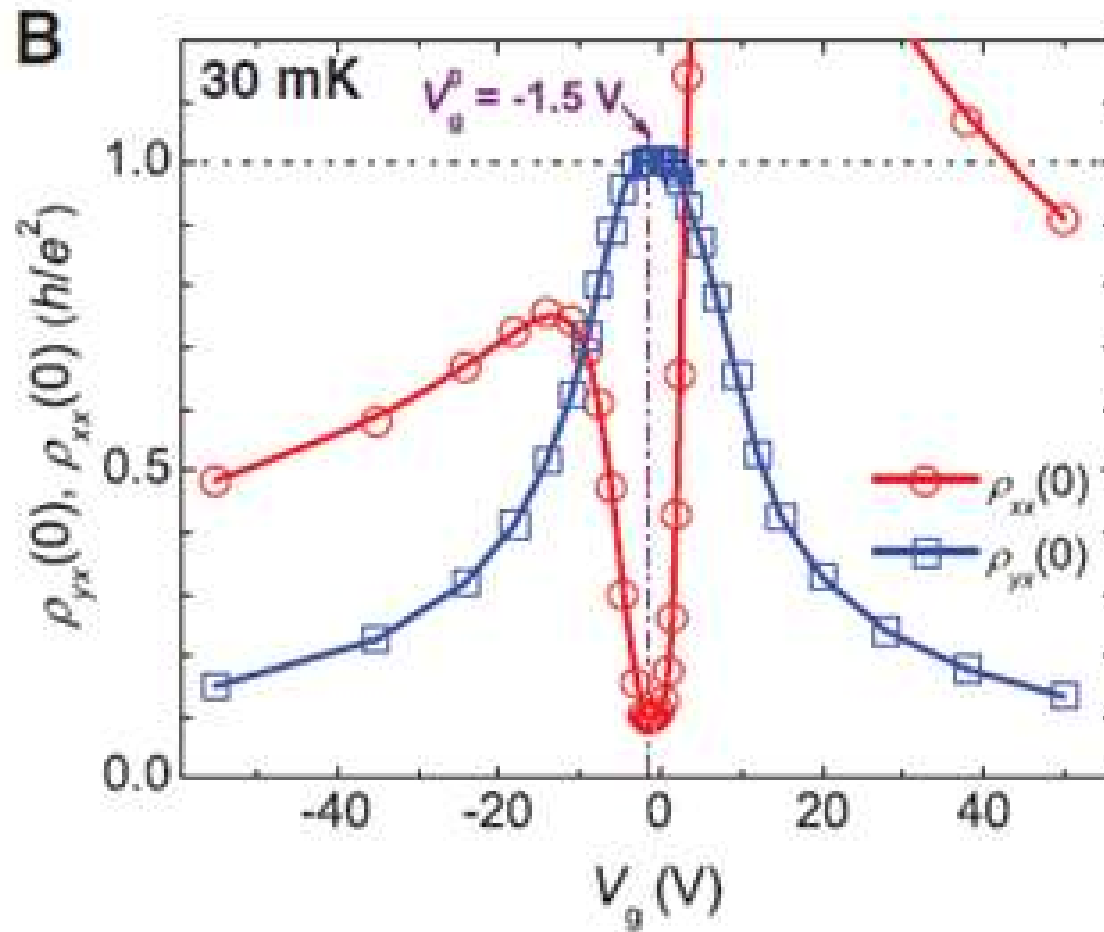
FM doped BiSeTe



FM doped TI

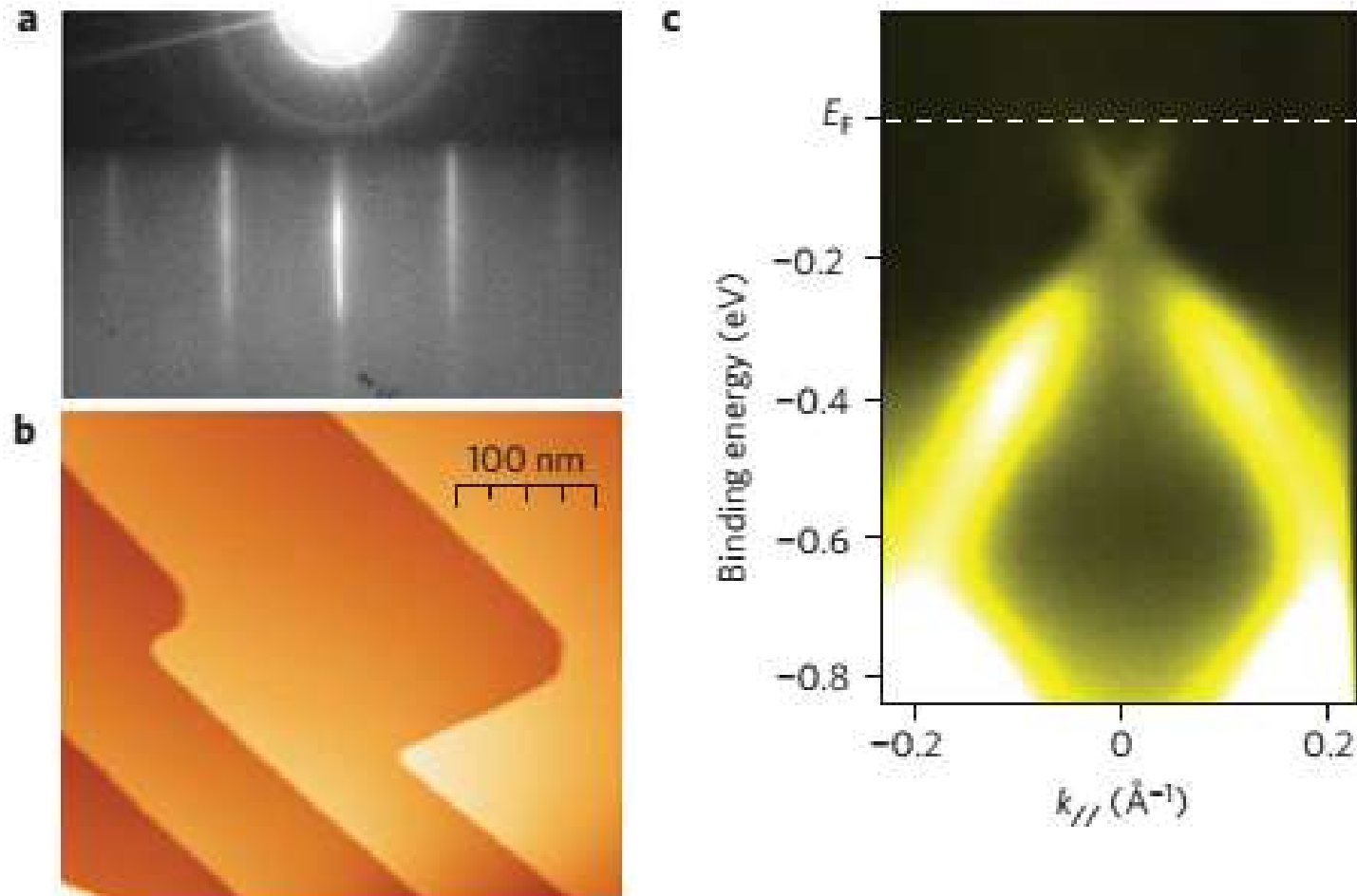
@FM order lead Hall conductance quantized in units of e^2/h ;
open energy gap at Dirac point;

Quantum anomalous Hall effect



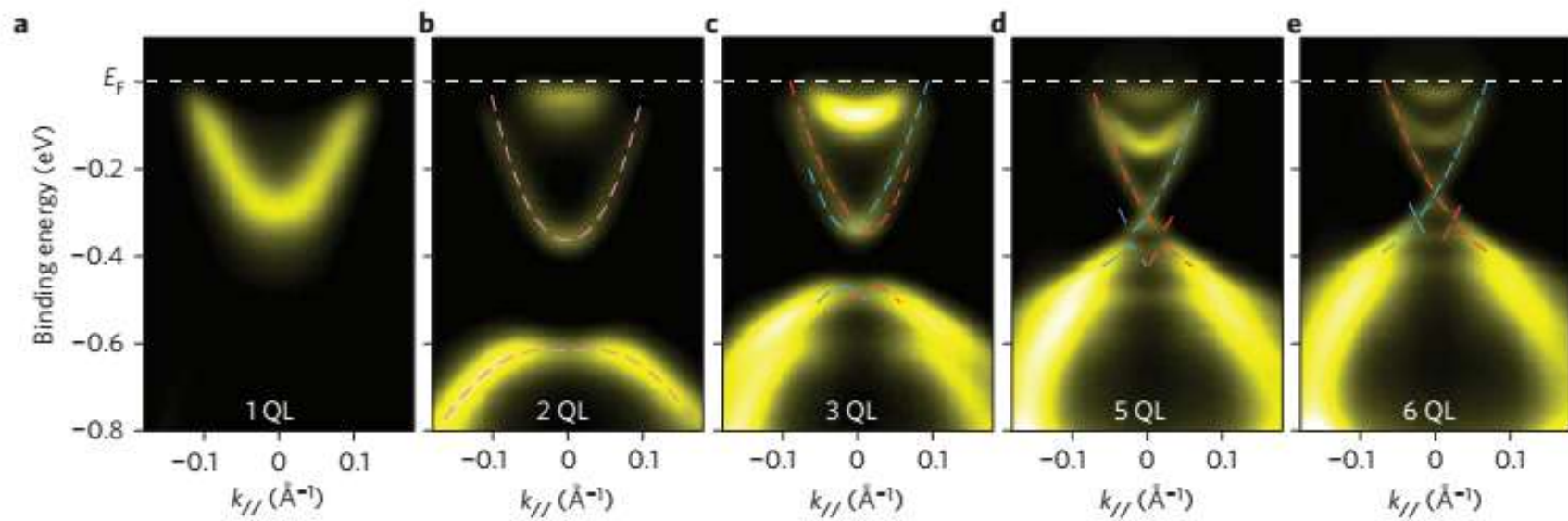
Chang, et al, Science (2013)

Bi₂Se₃ — TI

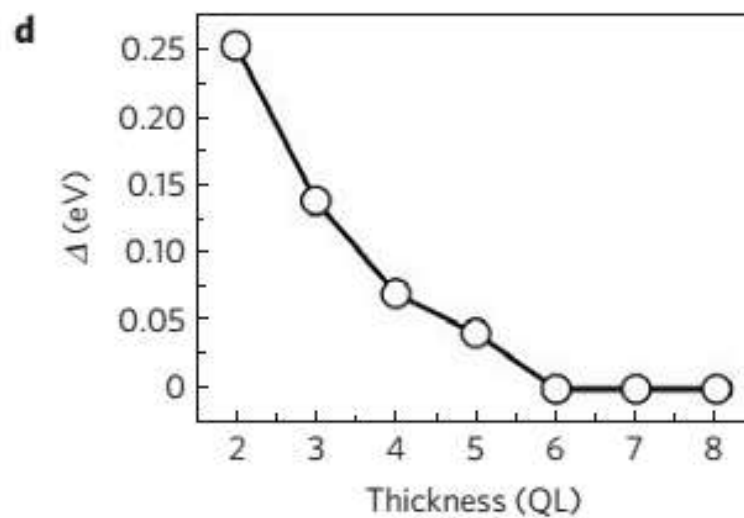
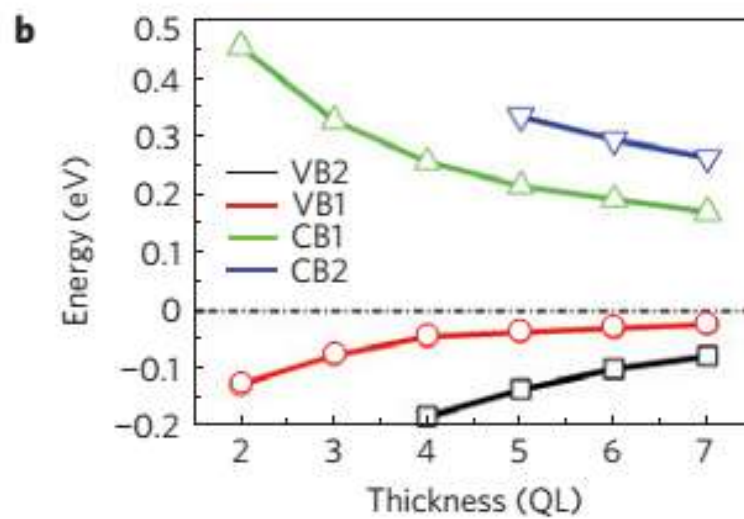
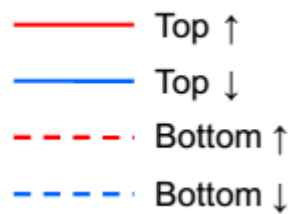
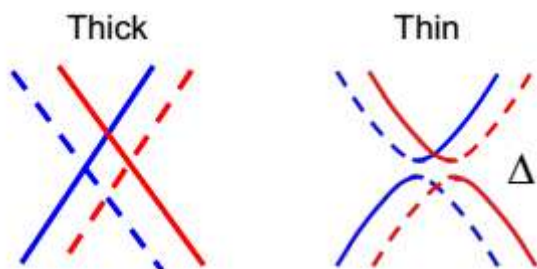


Zhang, et al, Nature Physics (2010)

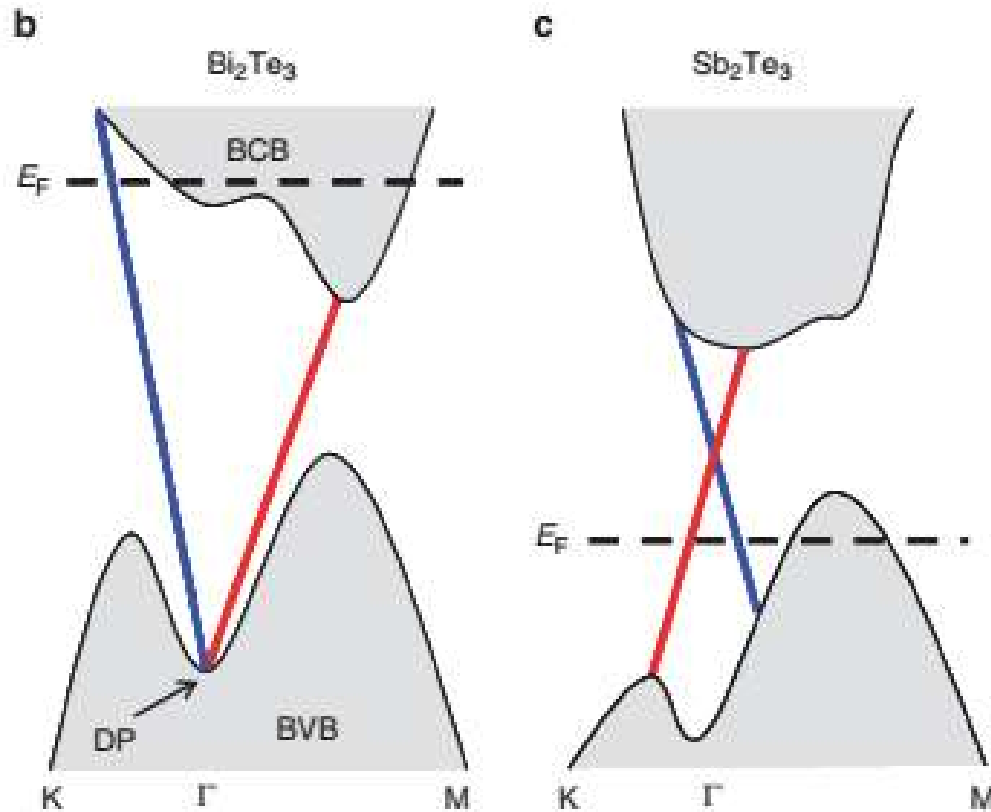
Bi₂Se₃ — TI



Bi₂Se₃ -- TI

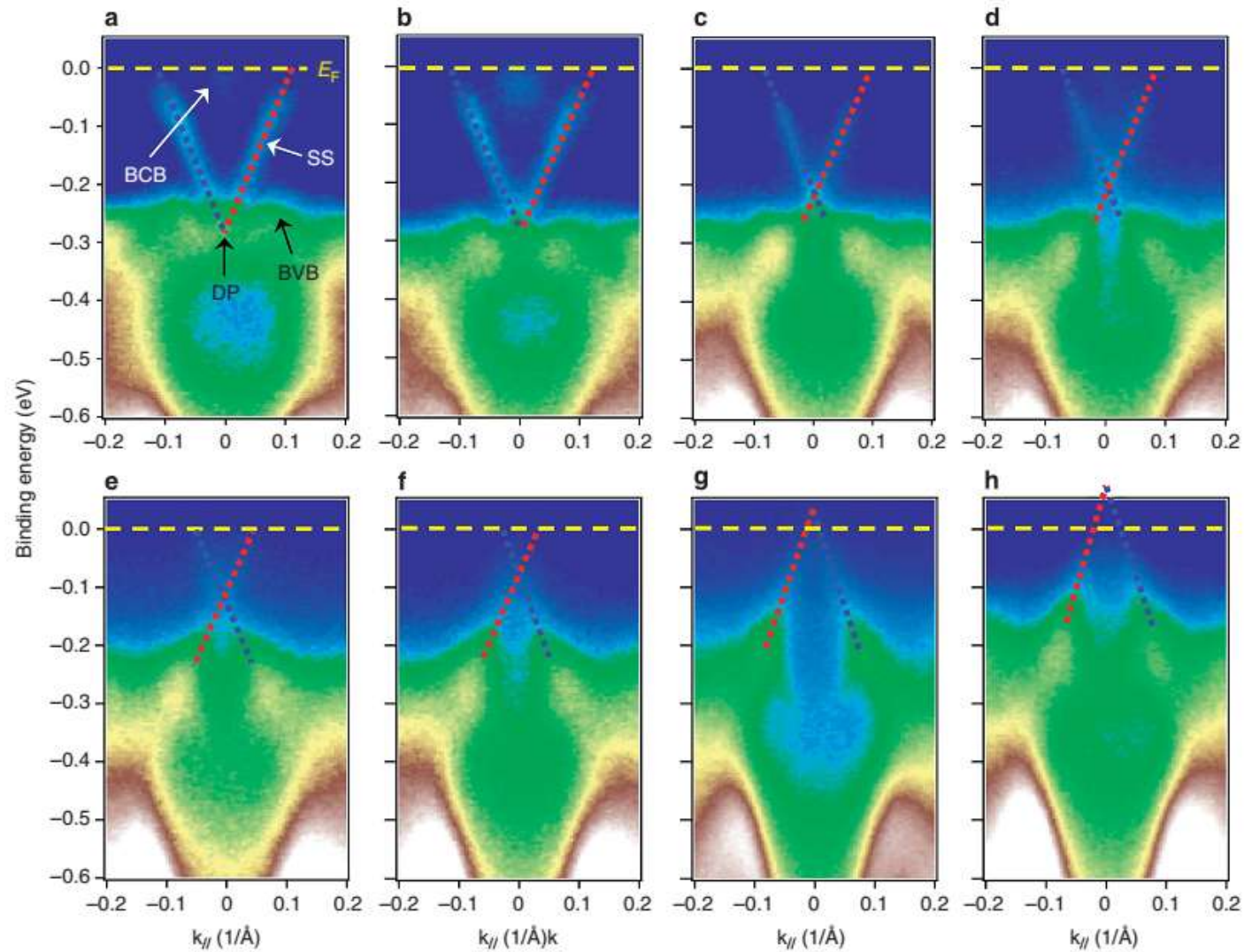


Tuning Fermi Level TI



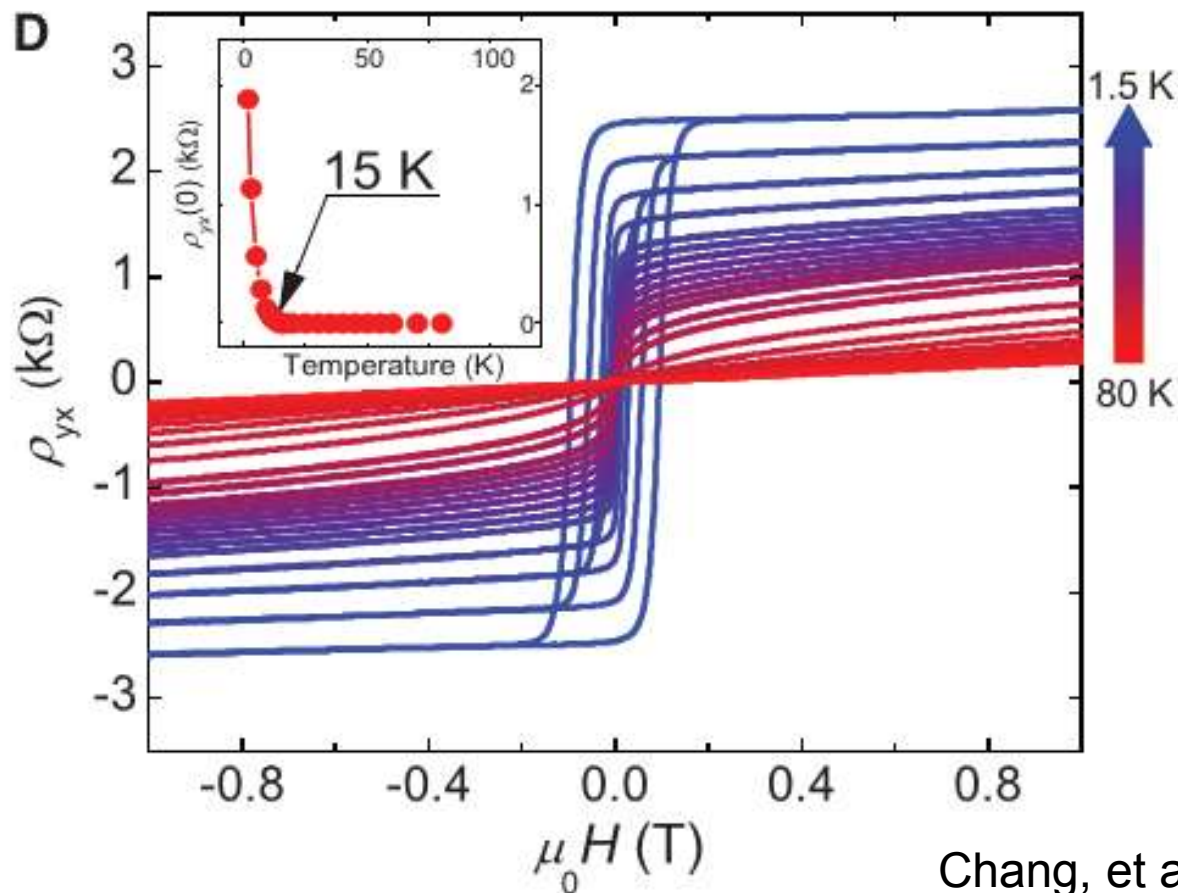
Zhang, et al, Nature Communications (2011)

Tuning Fermi Level TI



Quantum anomalous Hall effect

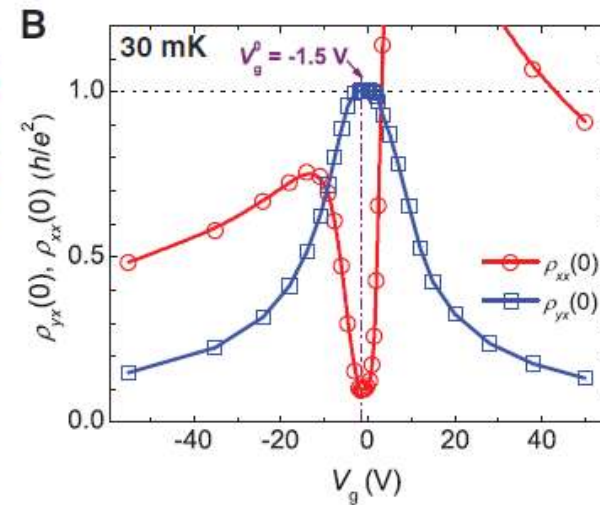
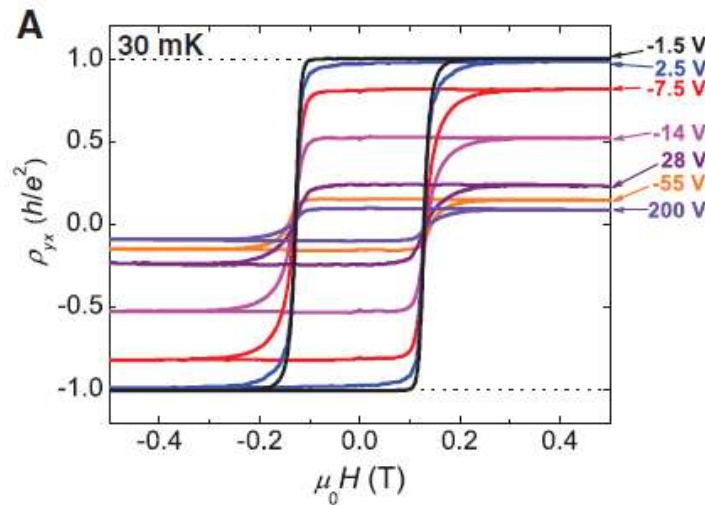
Cr doped (Bi,Sb)Te₃



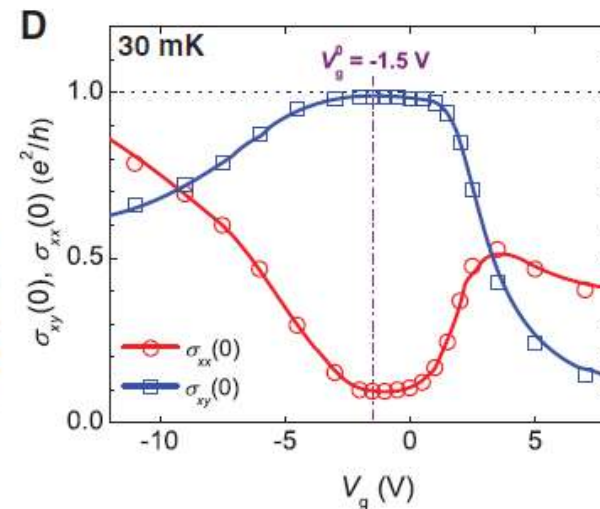
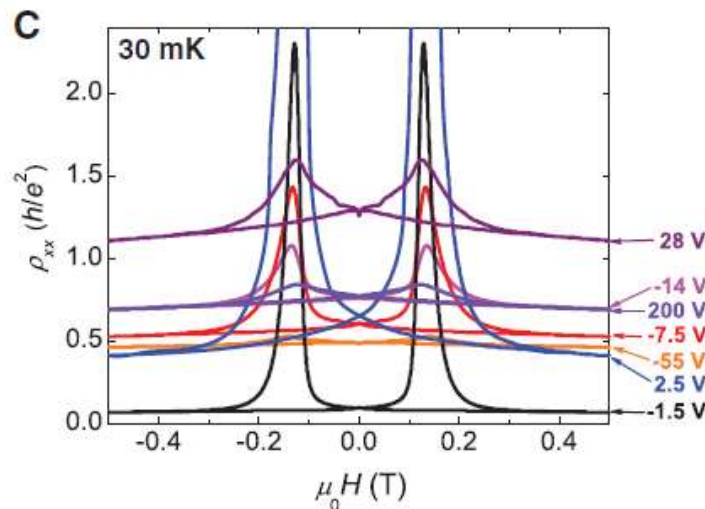
Chang, et al, Science (2013)

Quantum anomalous Hall effect

Cr doped (Bi,Sb)Te₃



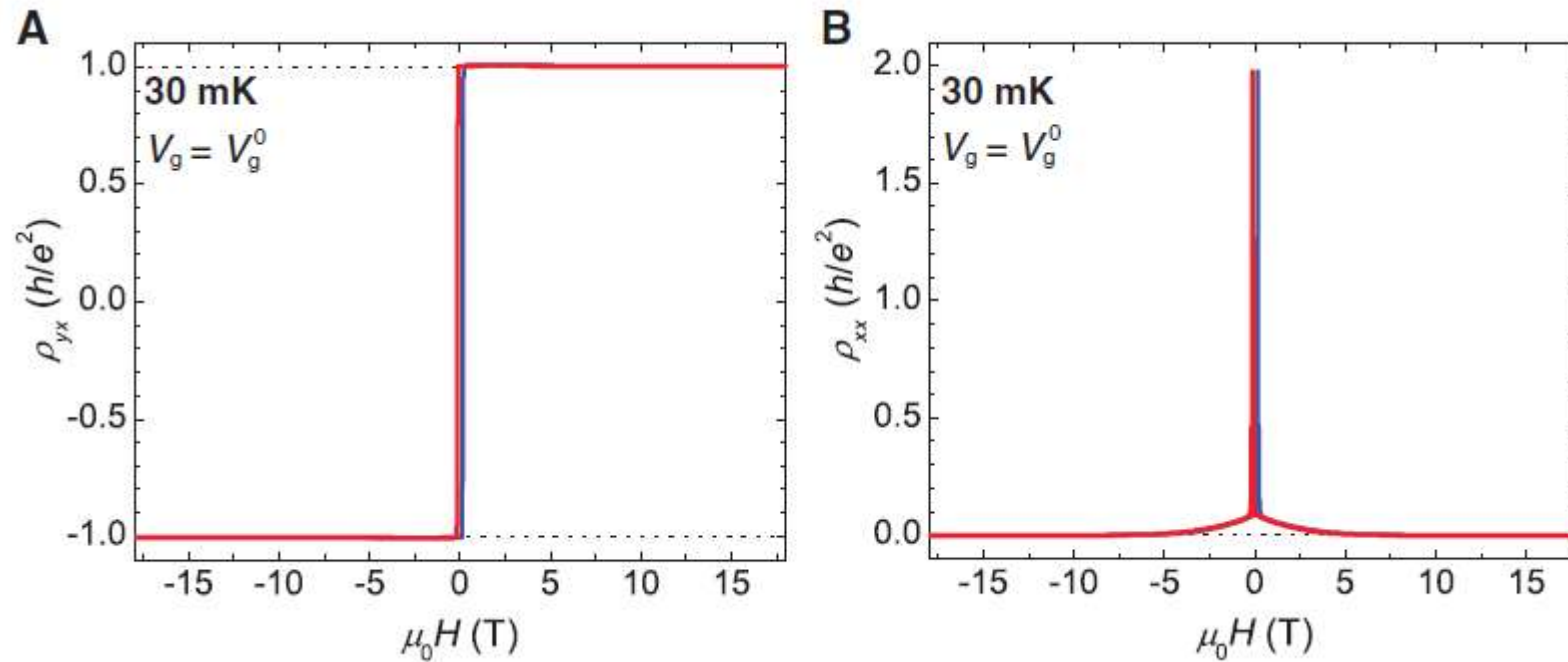
0.098 h/e²



0.987 e²/h

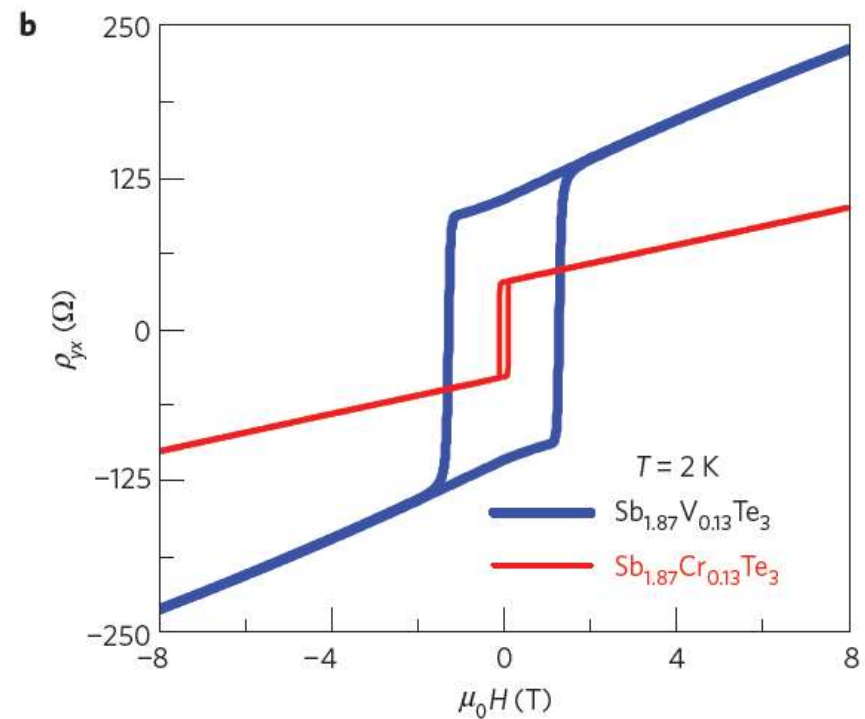
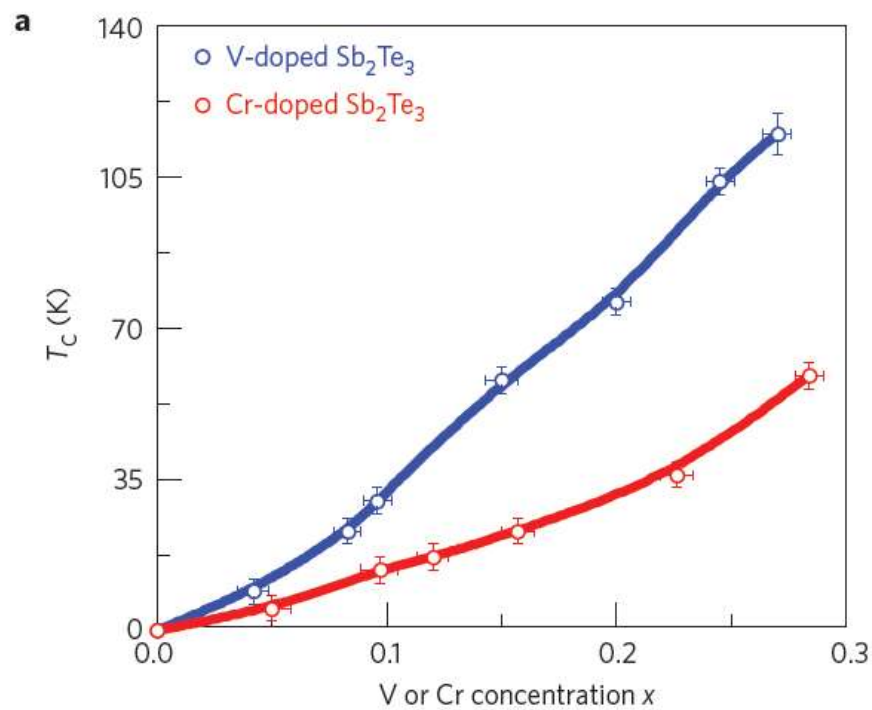
Quantum anomalous Hall effect

Cr doped (Bi,Sb)Te₃



Quantum anomalous Hall effect

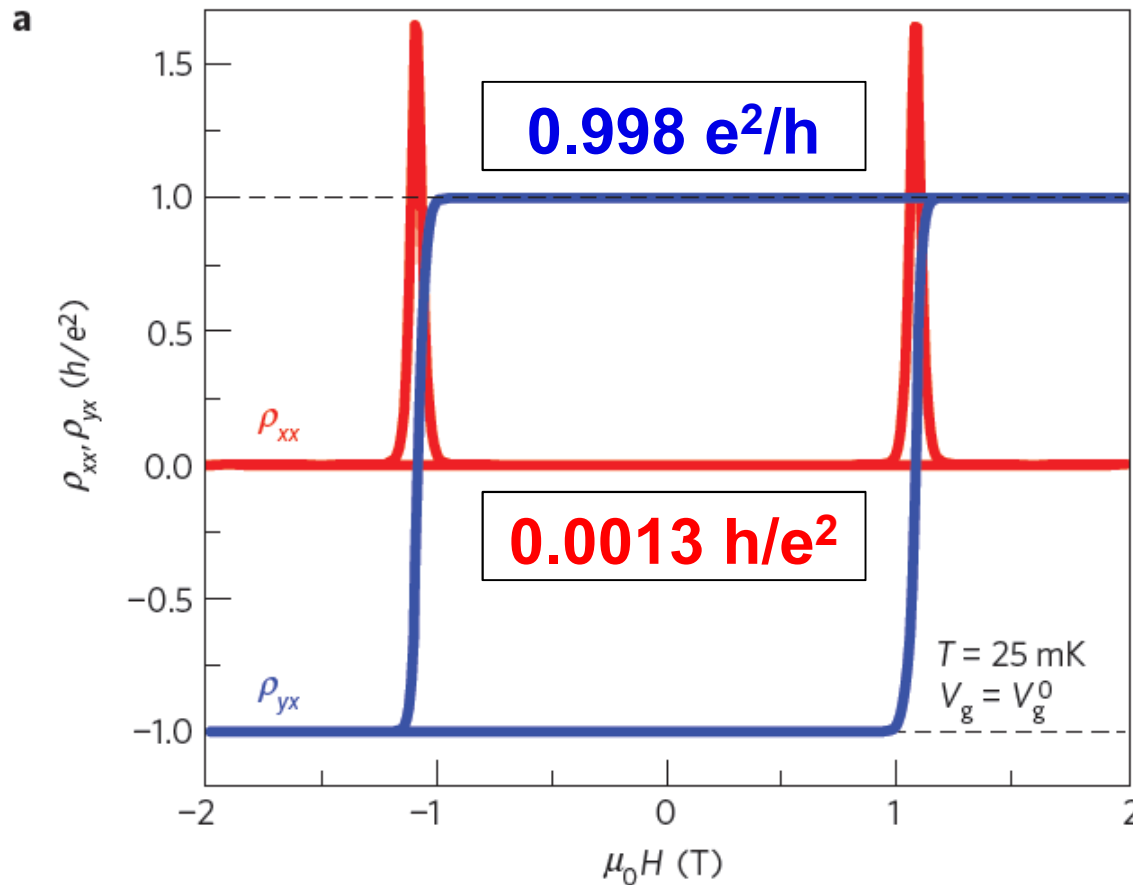
V doped (Bi,Sb)Te₃



Higher T_C , larger anisotropy

Quantum anomalous Hall effect

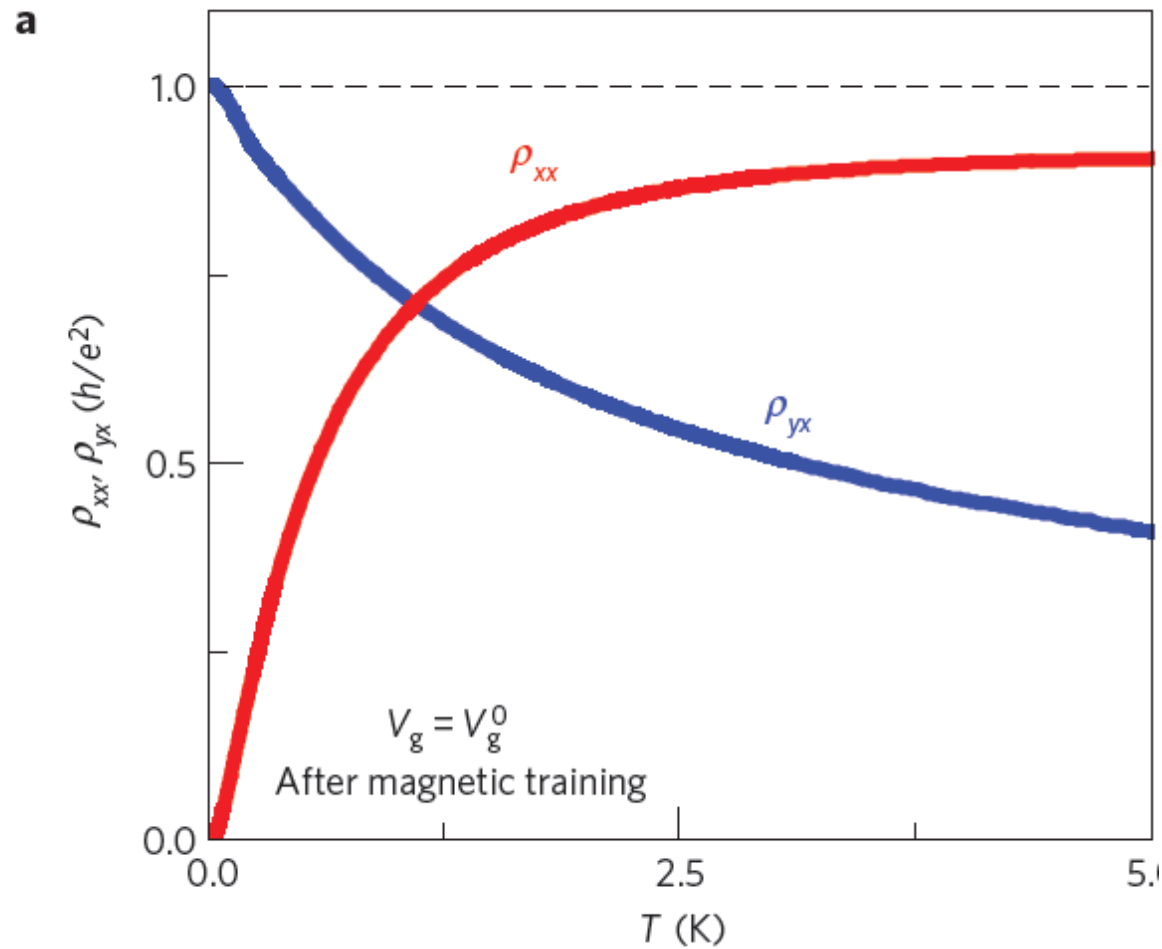
V doped (Bi,Sb)Te₃



Chang, et al, Nature Materials (2015)

Quantum anomalous Hall effect

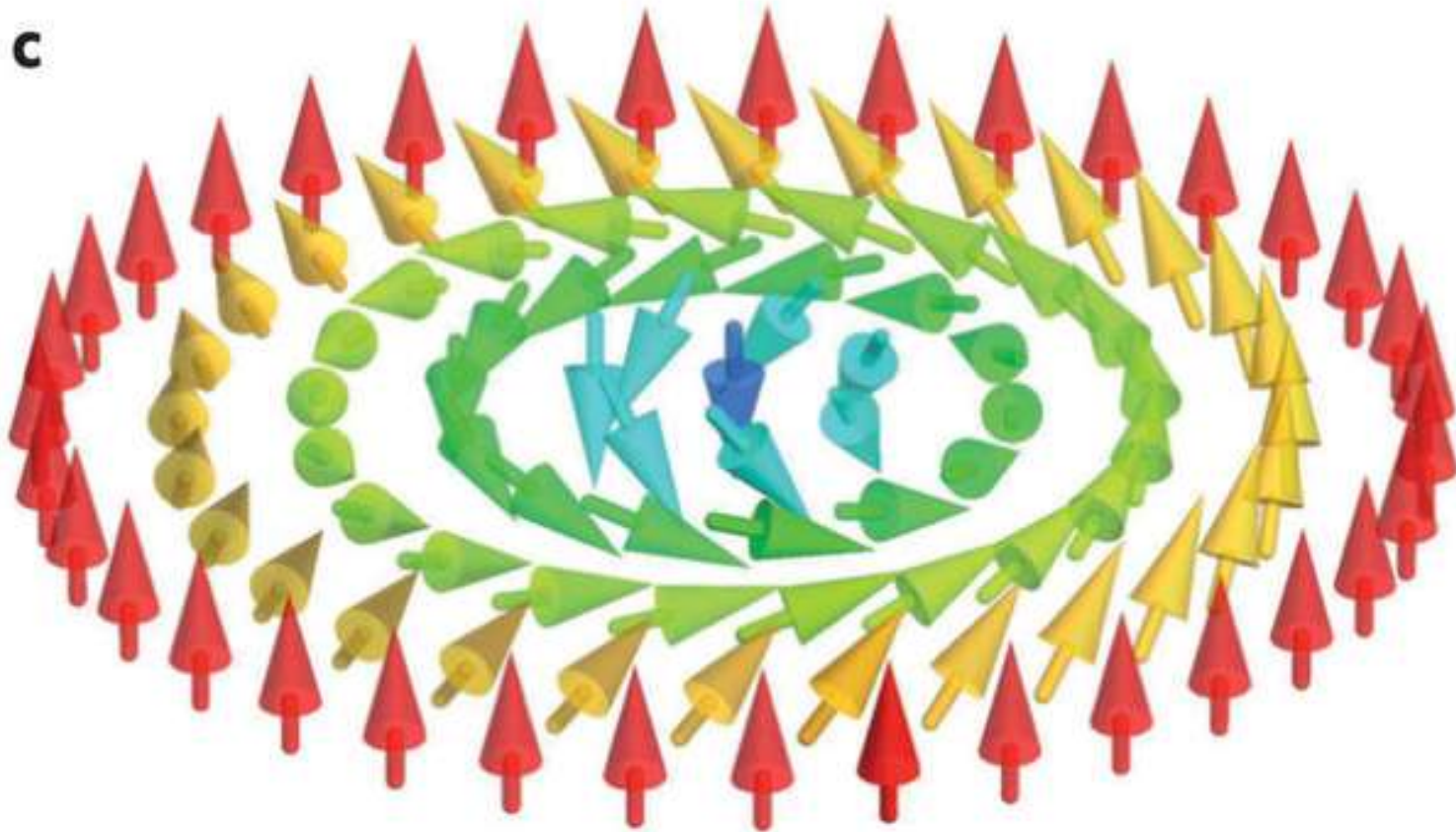
V doped (Bi,Sb)Te₃



Outline

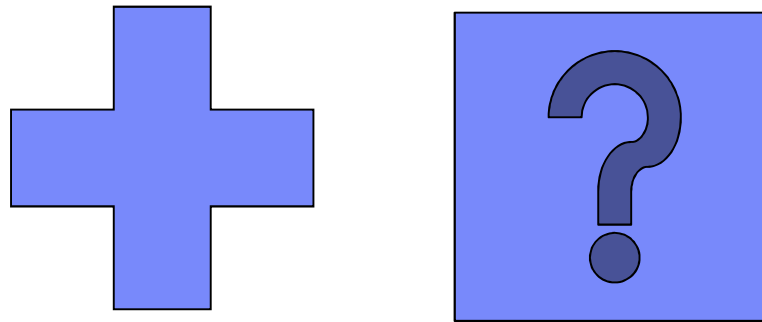
3. Skyrmions

Topology in real space



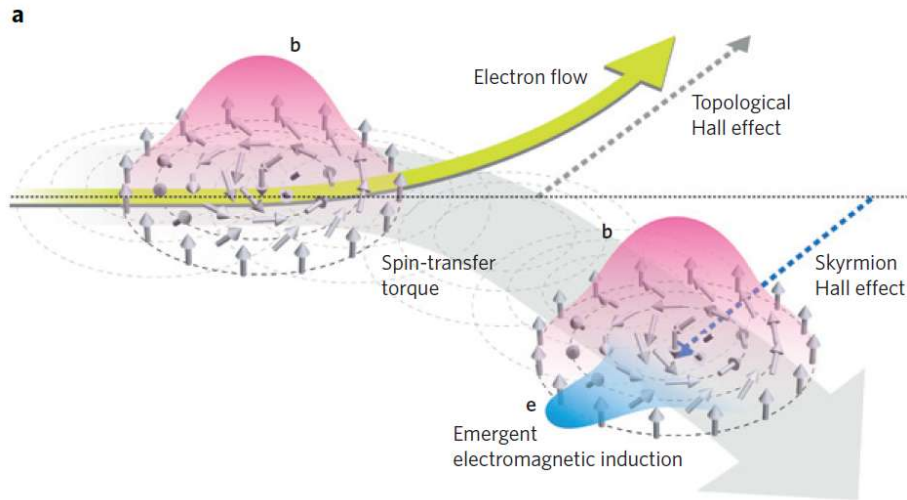
Questions?

Topology in momentum space

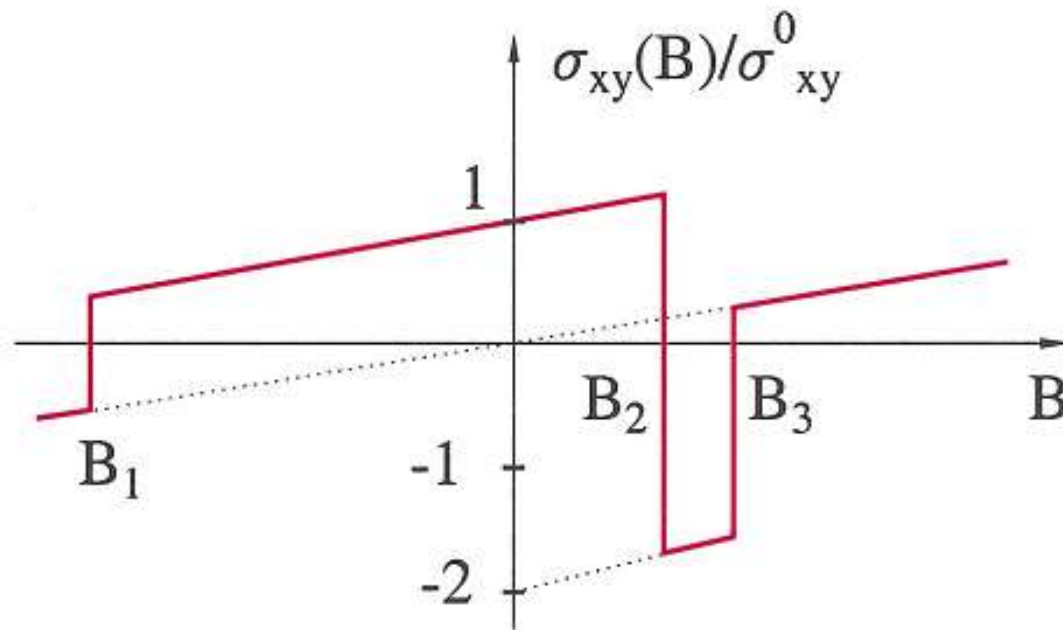


Topology in real space

Topological Hall effect

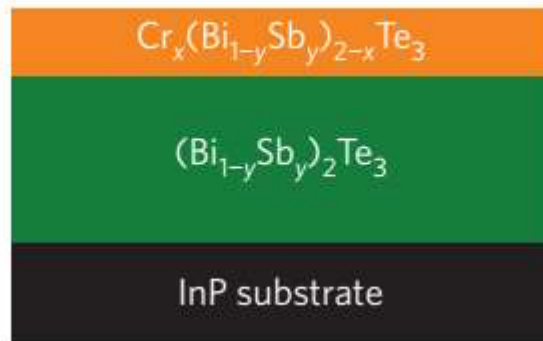


conduction electrons & localized spins

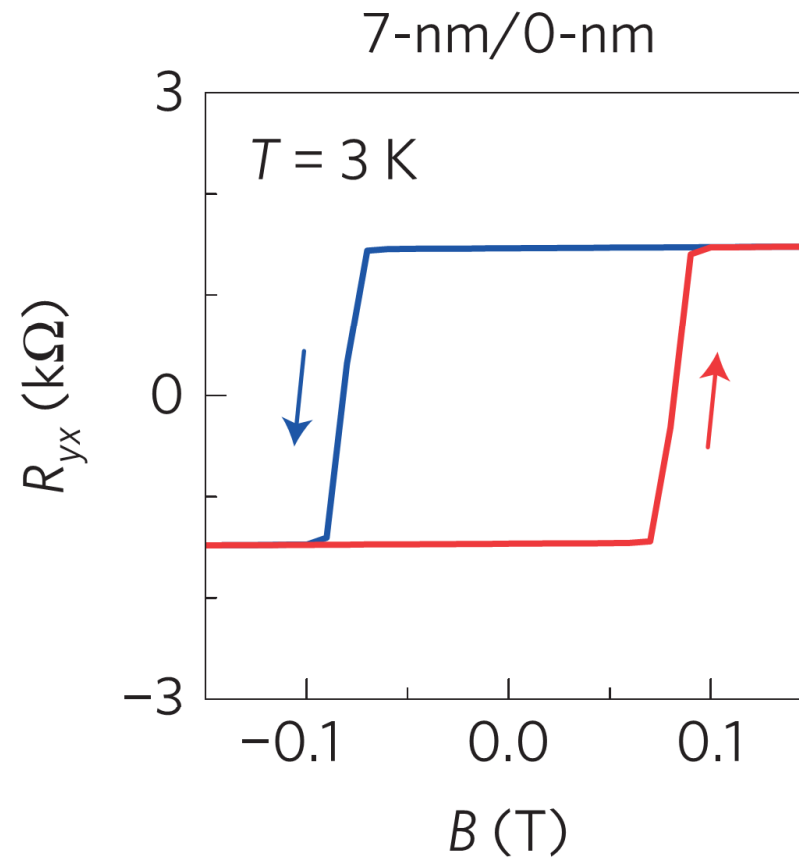


Topological Hall effect

a

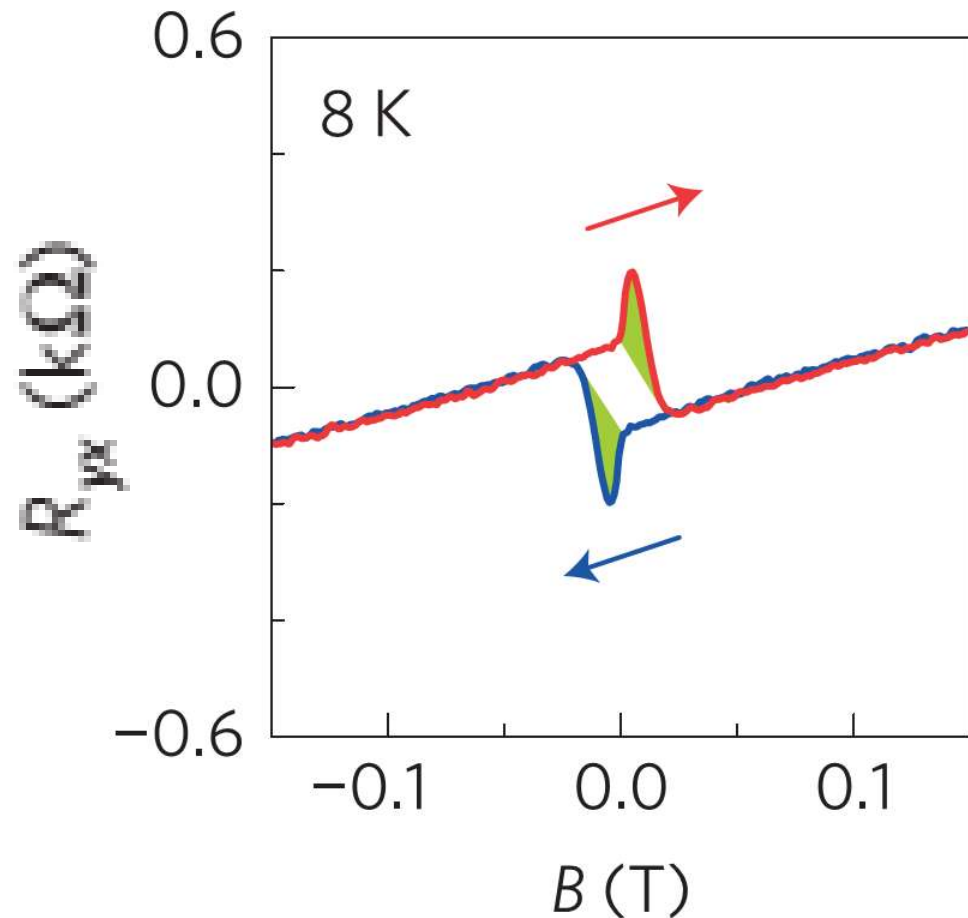
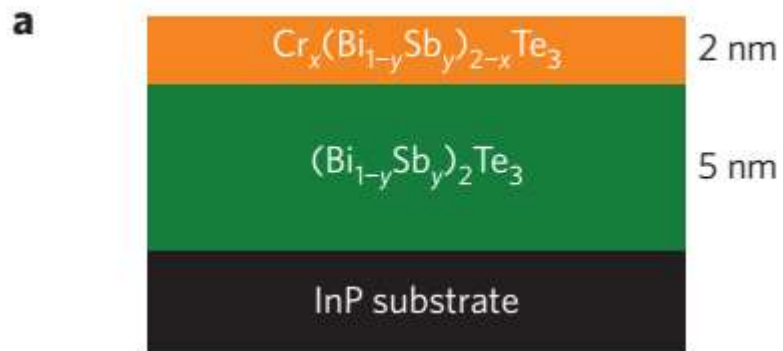


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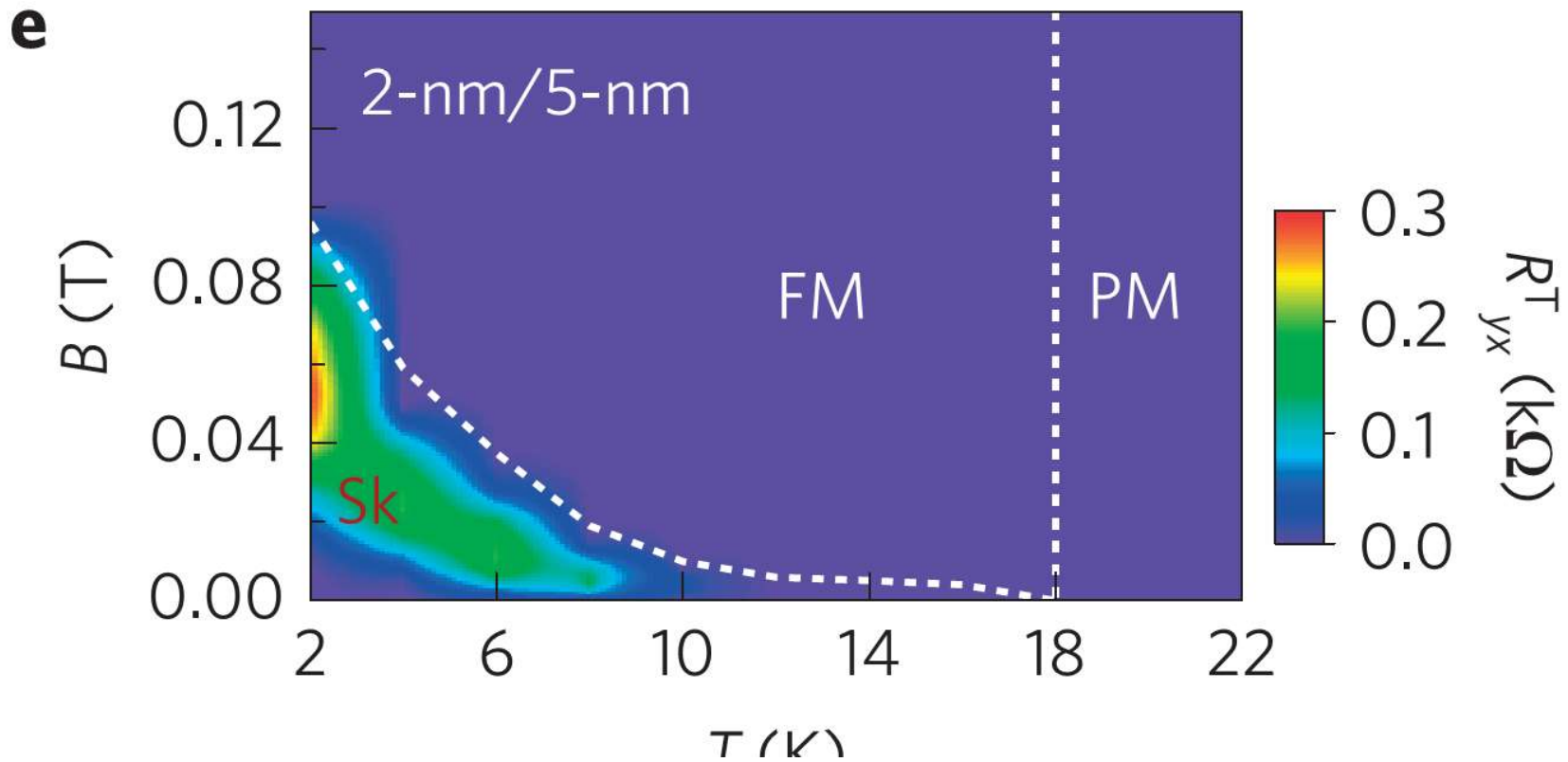
Yasuda, et al, Nature Physics (2016)

Topological Hall effect



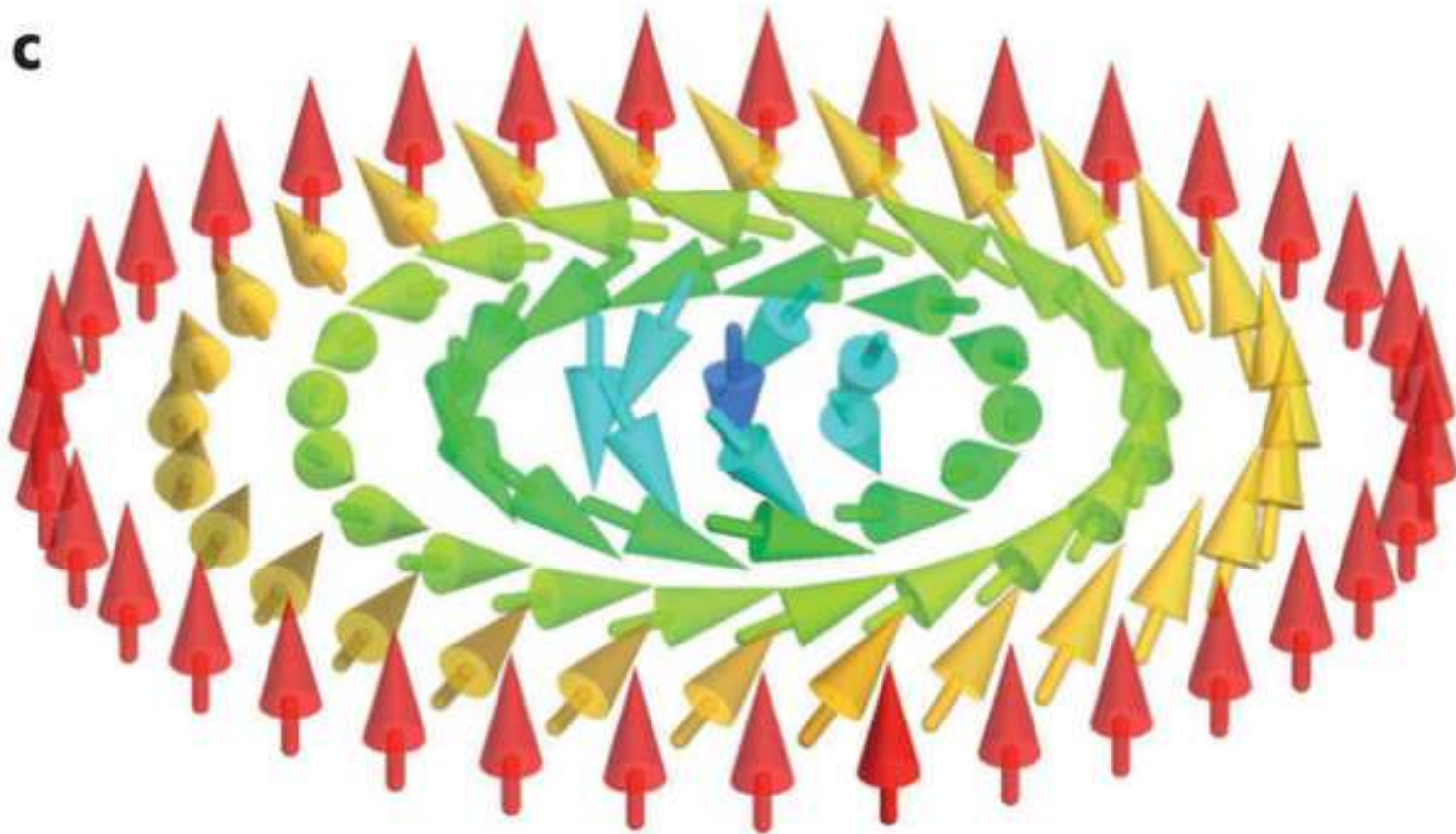
Yasuda, et al, Nature Physics (2016)

Topological Hall effect



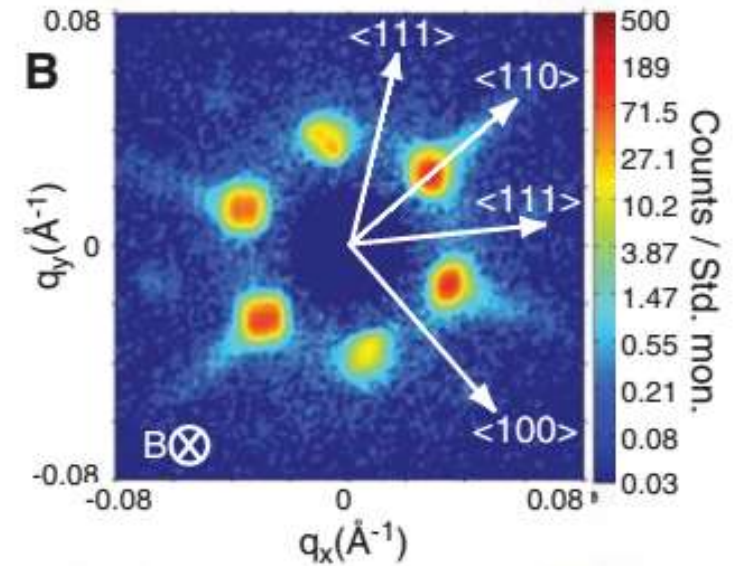
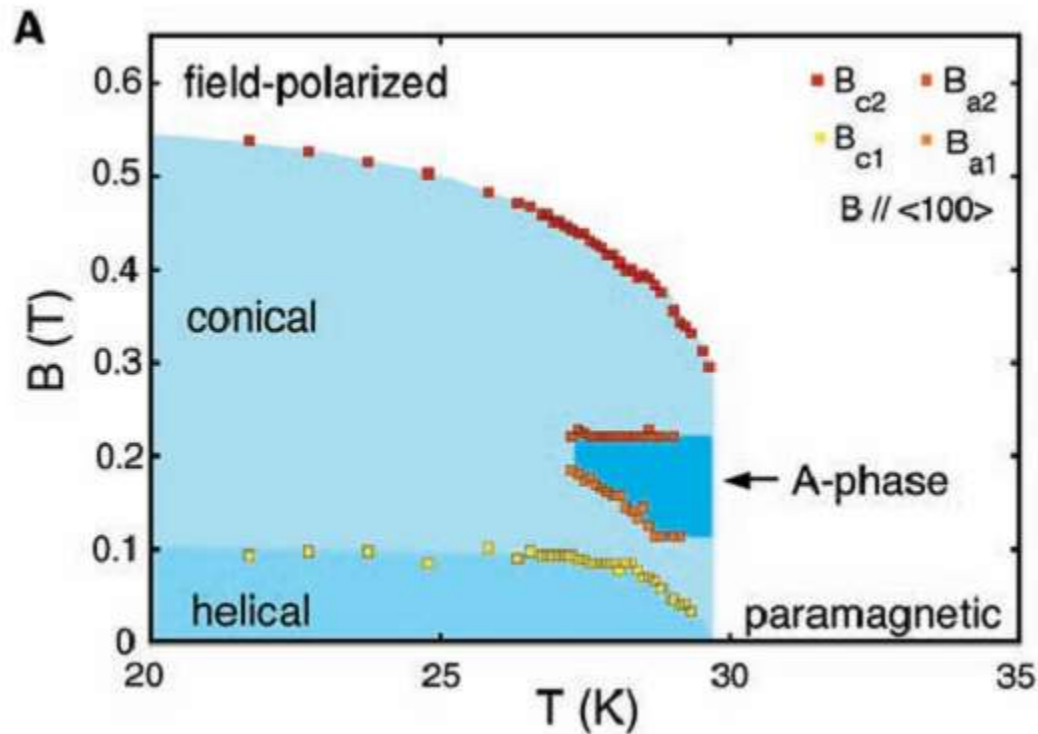
休息10分钟

Topology in real space



Observation

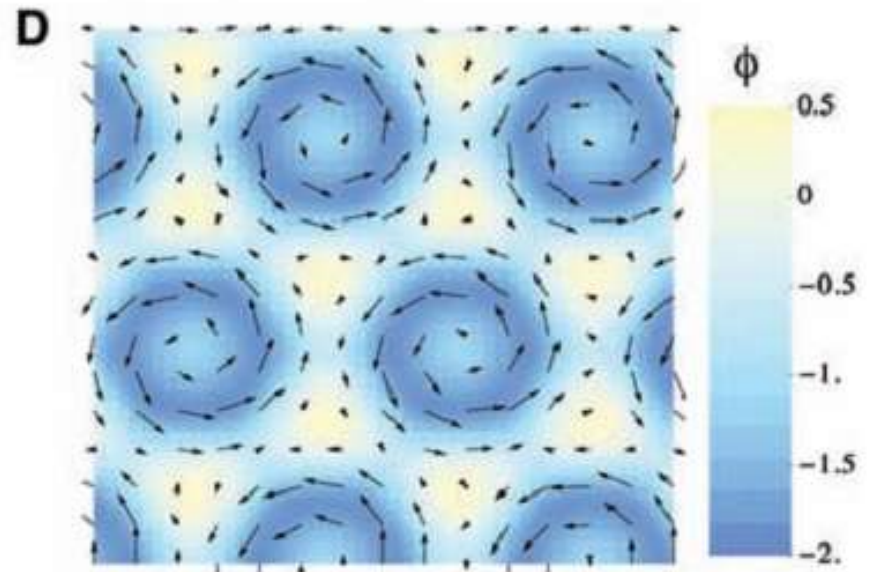
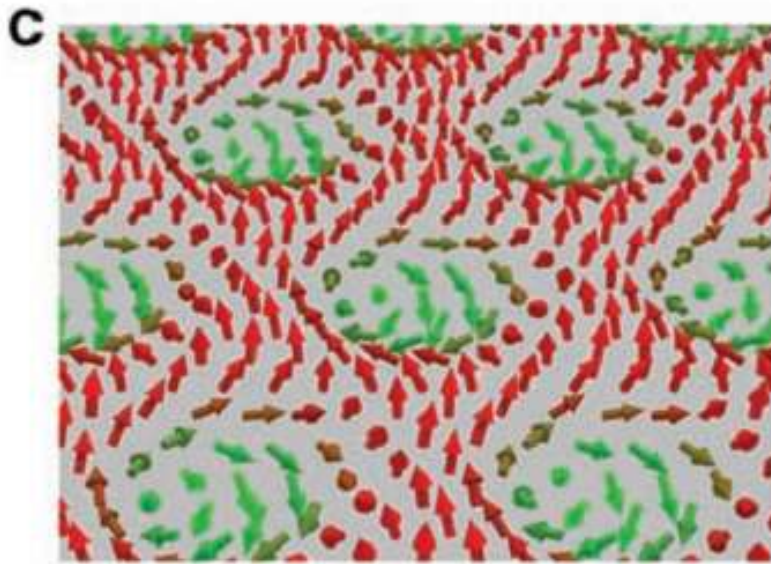
Neutron Scattering: MnSi



Muhlbauer, et al, Science (2009)

Observation

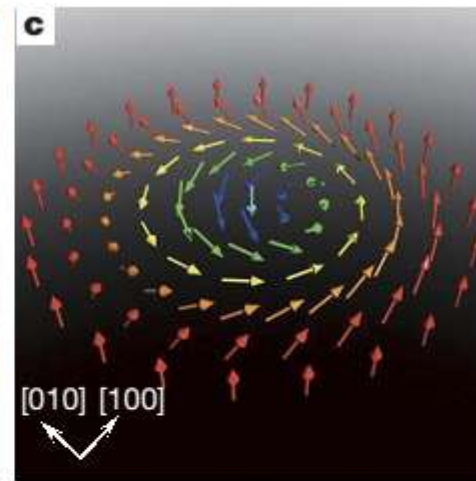
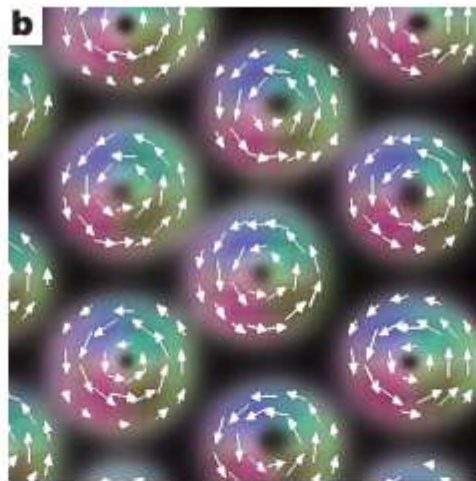
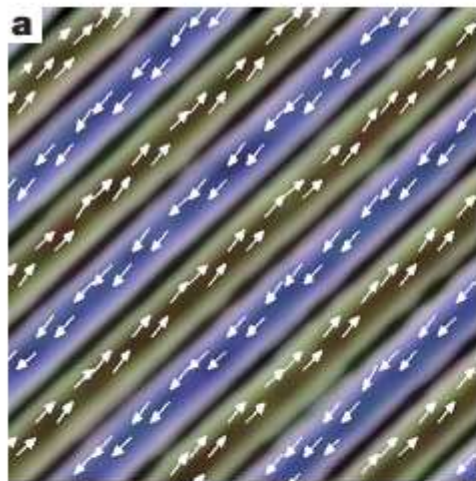
Neutron Scattering



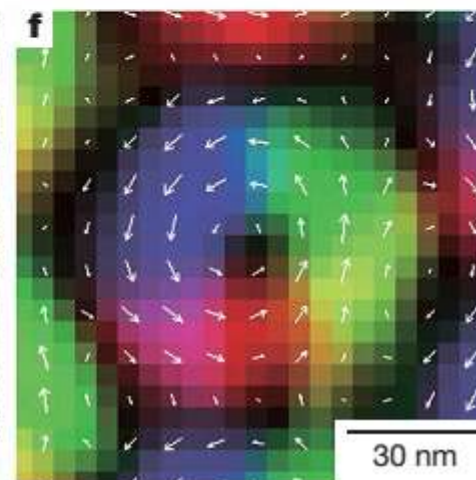
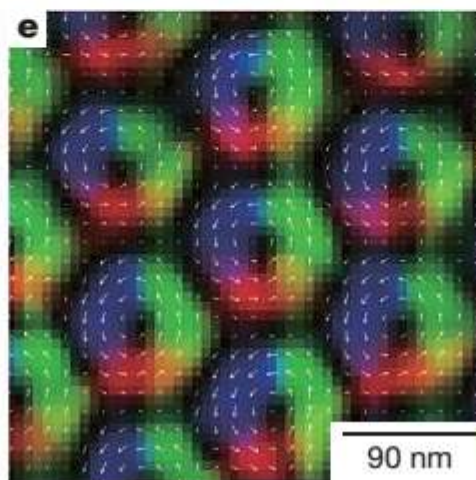
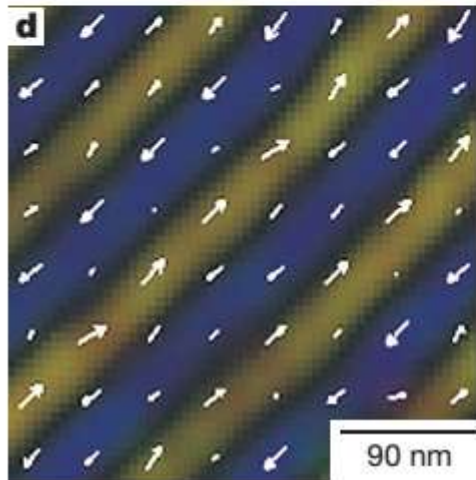
Muhlbauer, et al, Science (2009)

Observation

Lorentz TEM: $\text{Fe}_{0.5}\text{Co}_{0.5}\text{Si}$



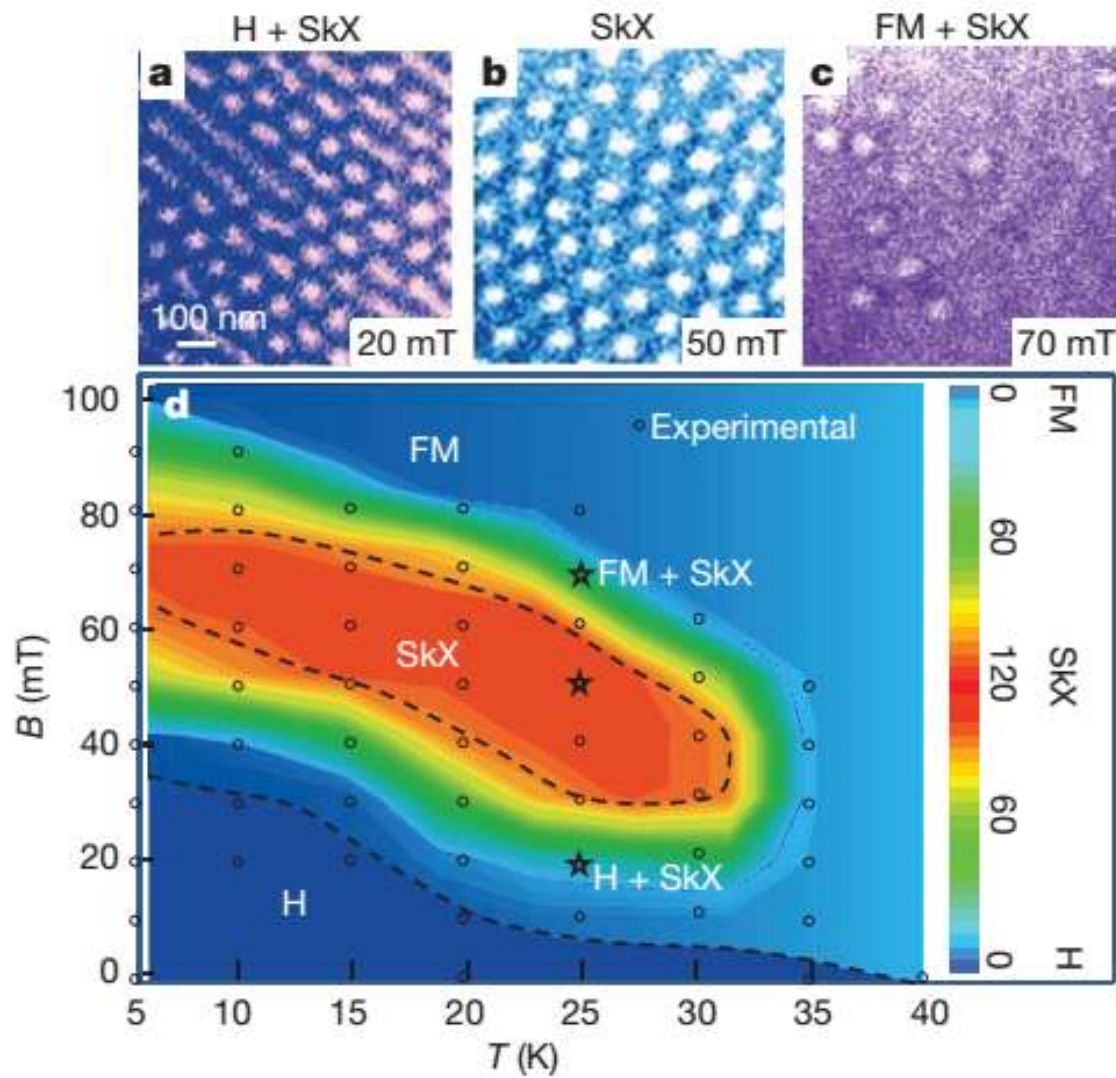
Theory



Experiment

Observation

Lorentz TEM: $\text{Fe}_{0.5}\text{Co}_{0.5}\text{Si}$



Topological Hall effect

VOLUME 93, NUMBER 9

PHYSICAL REVIEW LETTERS

week ending
27 AUGUST 2004

Topological Hall Effect and Berry Phase in Magnetic Nanostructures

P. Bruno,¹ V. K. Dugaev,^{1,2} and M. Taillefumier^{1,3}

¹*Max-Planck-Institut für Mikrostrukturphysik, Weinberg 2, 06120 Halle, Germany*

²*Institute for Problems of Materials Science, NASU, Vilde 5, 58001 Chernovtsy, Ukraine*

³*Laboratoire Louis Néel, CNRS, Boite Postale 166, 38042 Grenoble CEDEX 09, France*

(Received 21 October 2003; published 27 August 2004)

We discuss the anomalous Hall effect in a two-dimensional electron gas subject to a spatially varying magnetization. This topological Hall effect does not require any spin-orbit coupling and arises solely from Berry phase acquired by an electron moving in a smoothly varying magnetization. We propose an experiment with a structure containing 2D electrons or holes of diluted magnetic semiconductor subject to the stray field of a lattice of magnetic nanocylinders. The striking behavior predicted for such a system (of which all relevant parameters are well known) allows one to observe unambiguously the topological Hall effect and to distinguish it from other mechanisms.

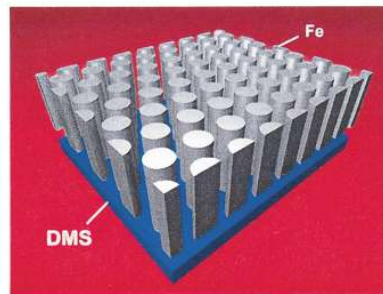
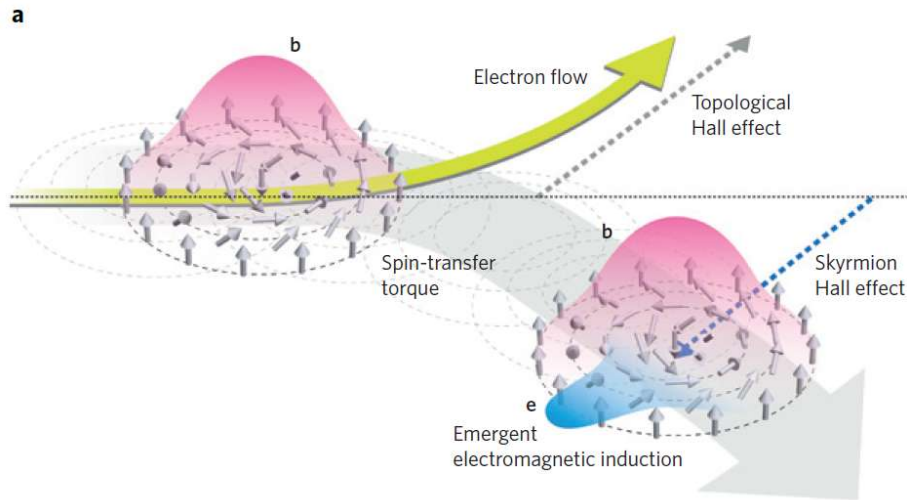
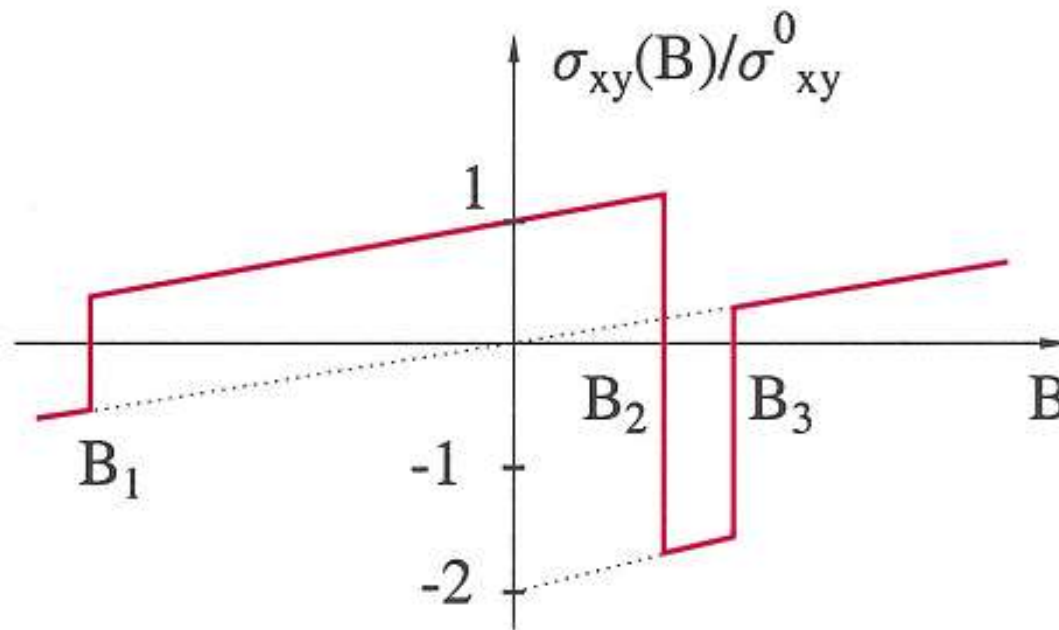


FIG. 1 (color). The proposed structure consisting of a triangular lattice of magnetic nanocylinders on top of 2D diluted magnetic semiconductor.

Topological Hall effect



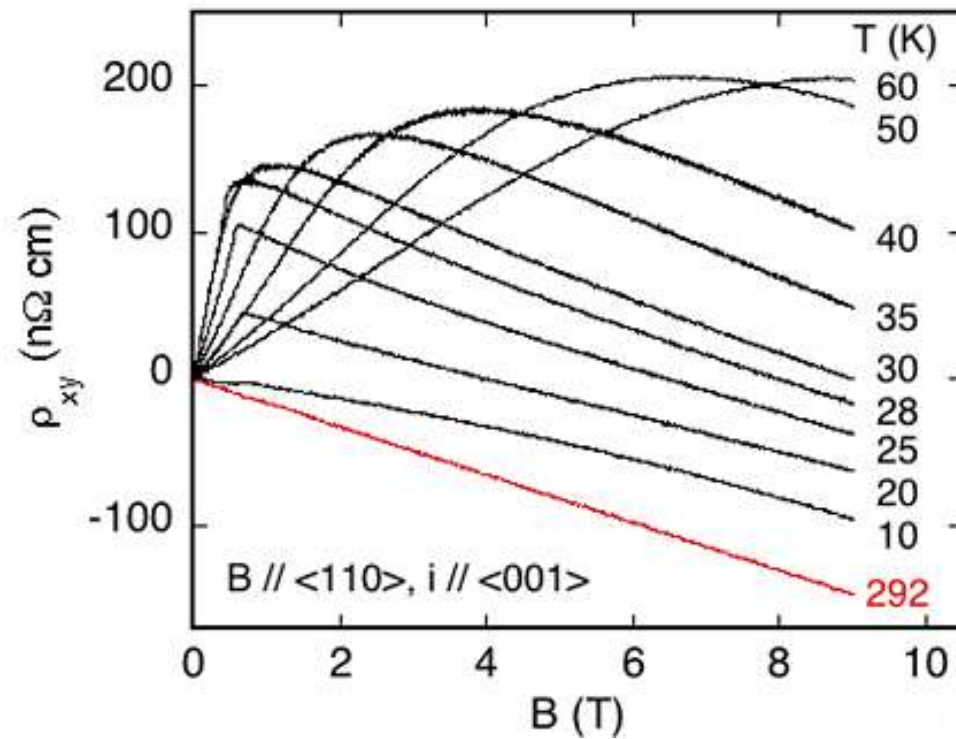
conduction electrons & localized spins



Observation

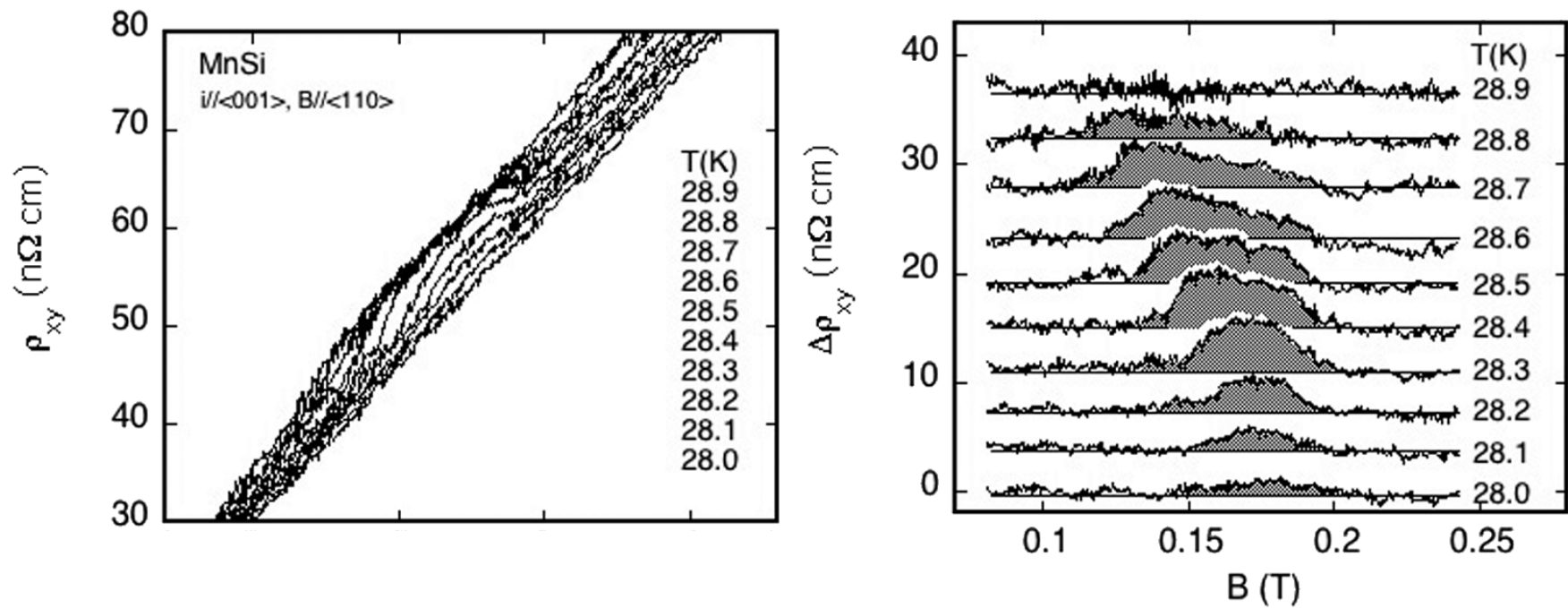
Topological Hall effect: MnSi

AHE



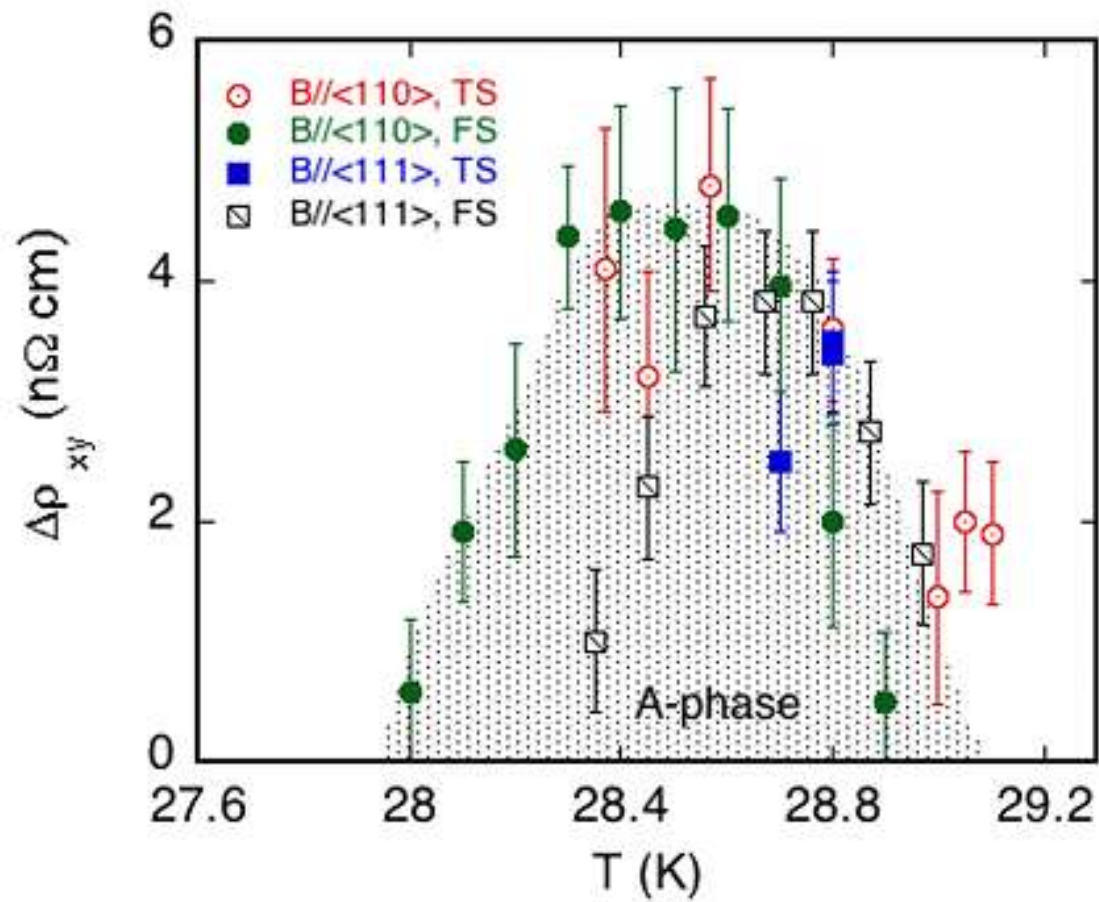
Observation

Topological Hall effect: MnSi



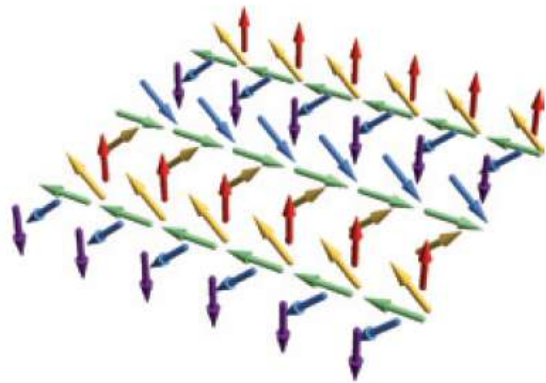
Observation

Topological Hall effect: MnSi



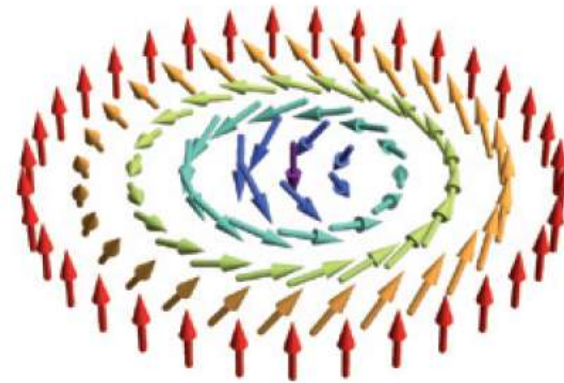
Skyrmion

a



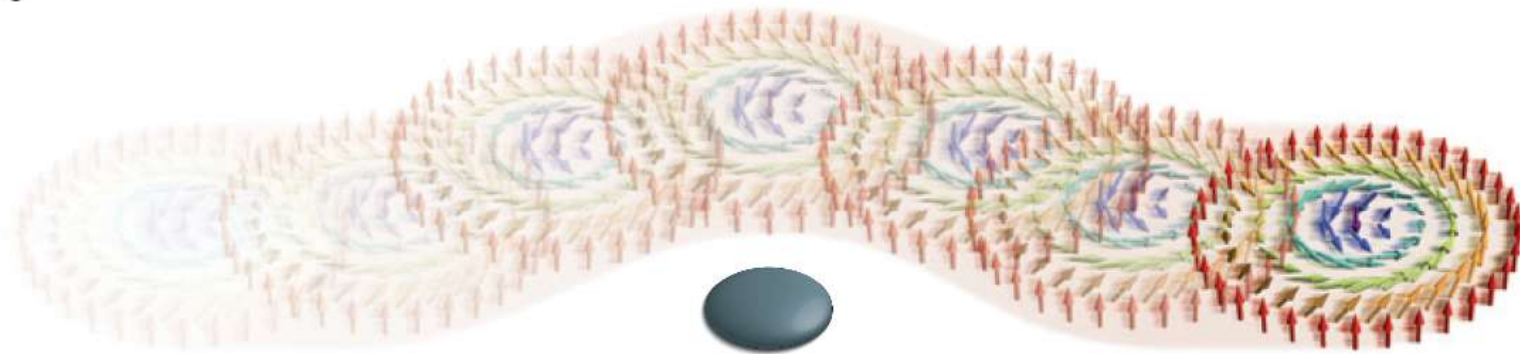
Helix

b



Skyrmion

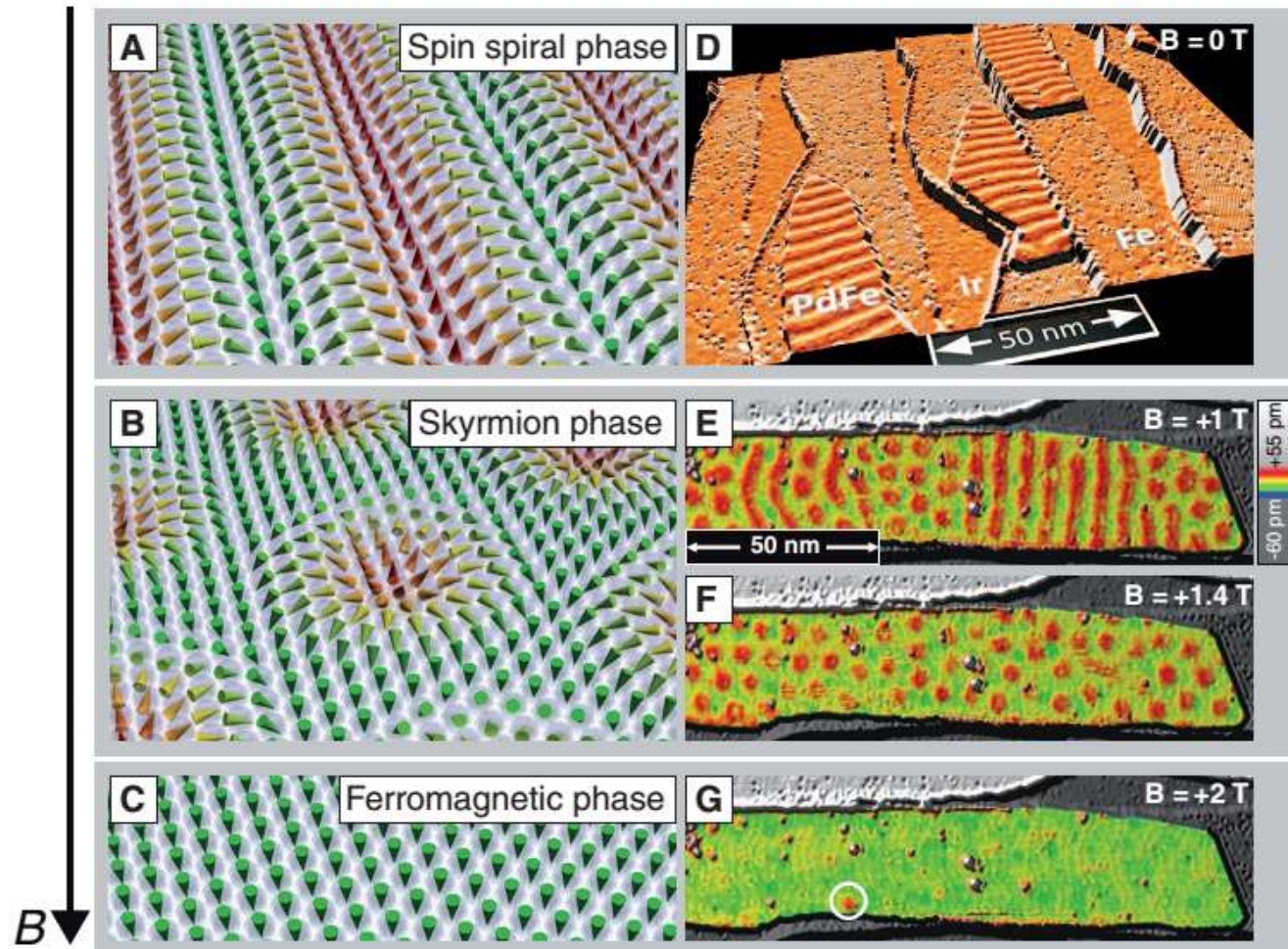
c



Skyrmion moving around obstacle

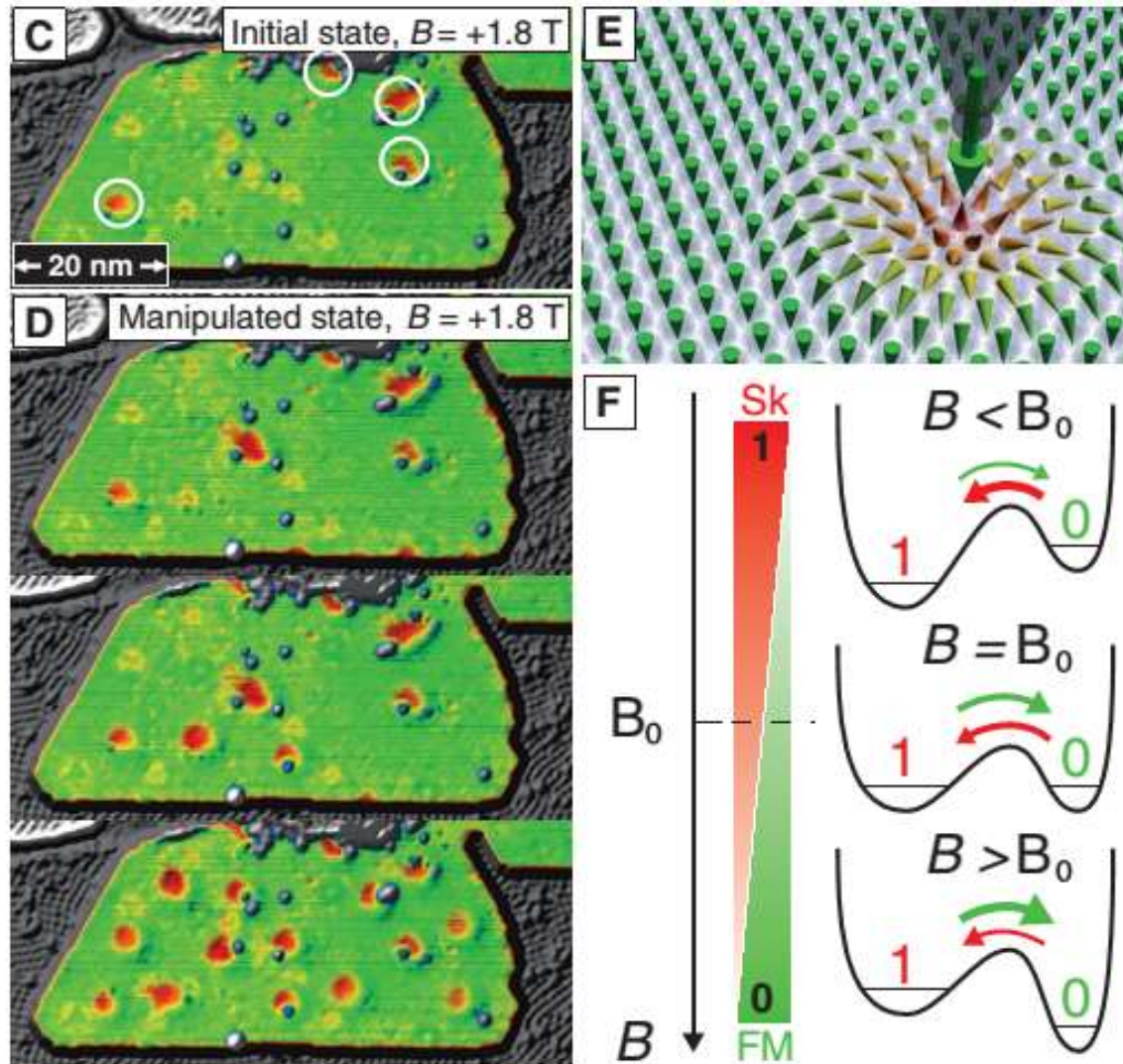
Rosch, et al, Nature Nanotechnology (2013)

Write a skyrmion

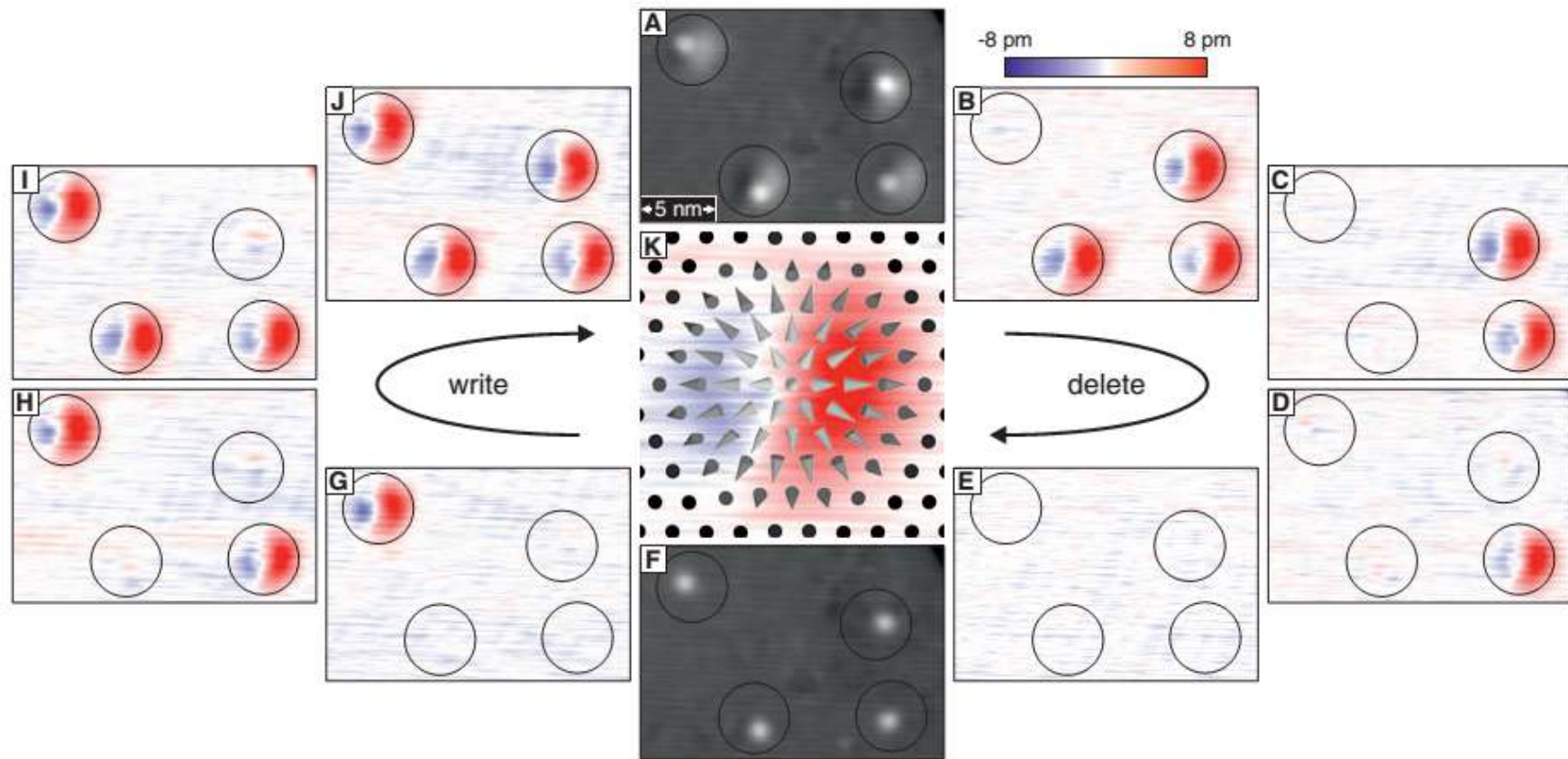


Romming, et al, Science (2013)

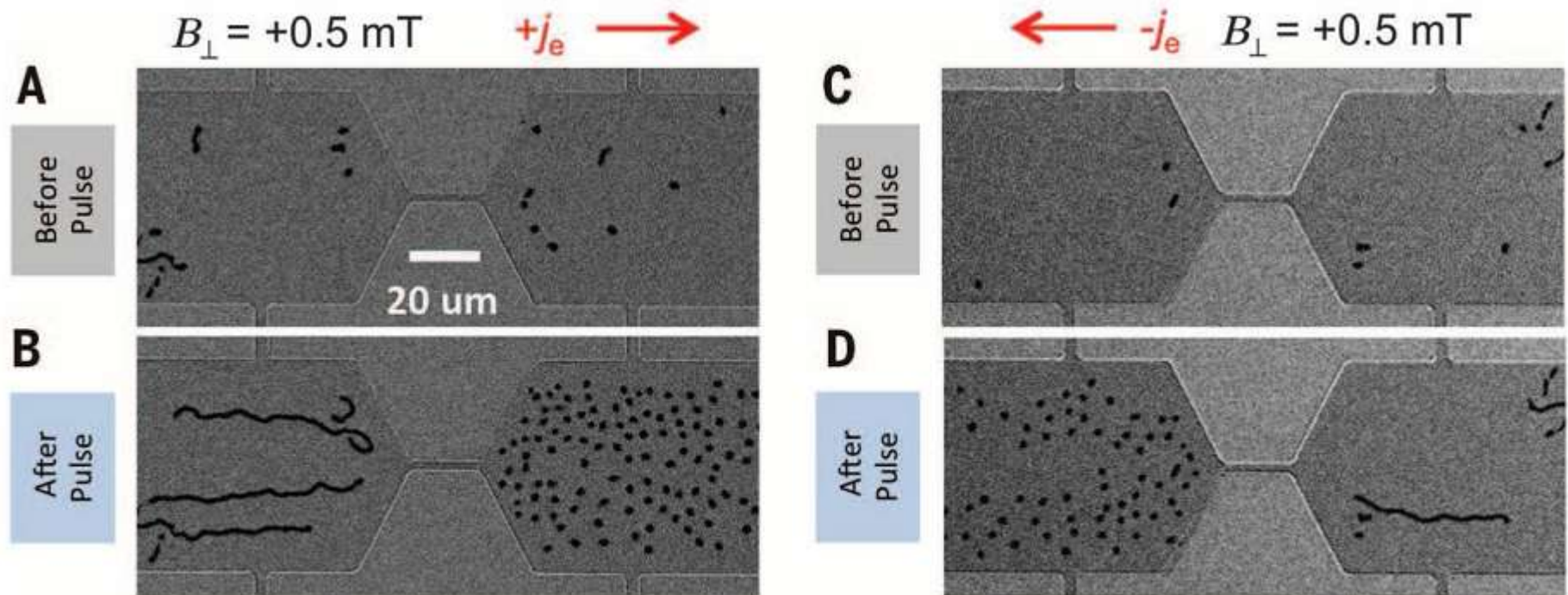
Write a skyrmion



Write and delete a skyrmion



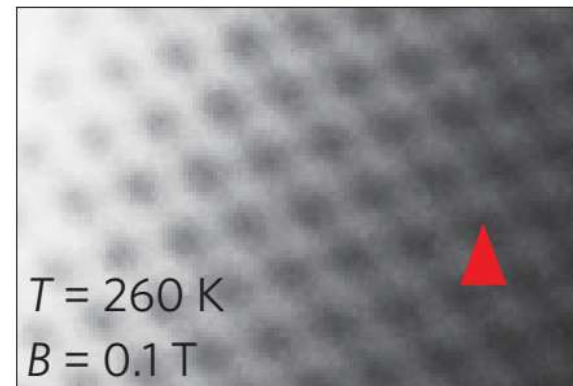
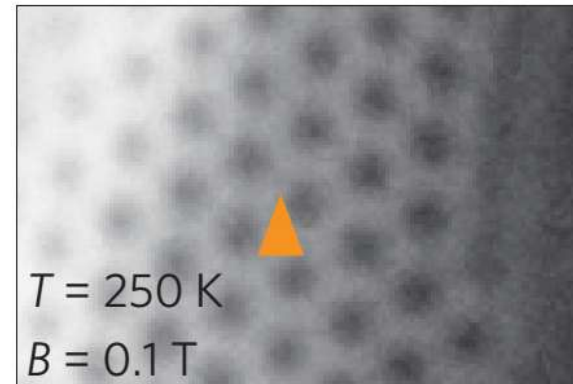
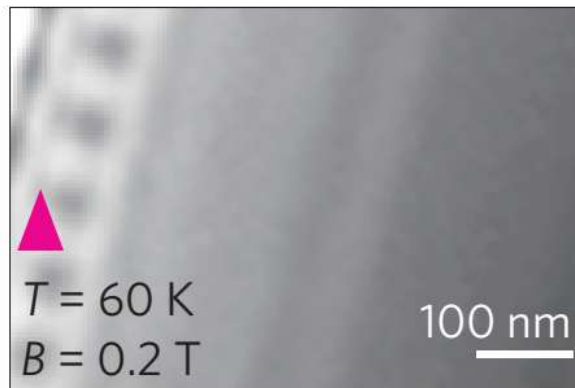
Create a skyrmion



Jiang, et al, Science (2015)

Near Room temperature Skyrmion

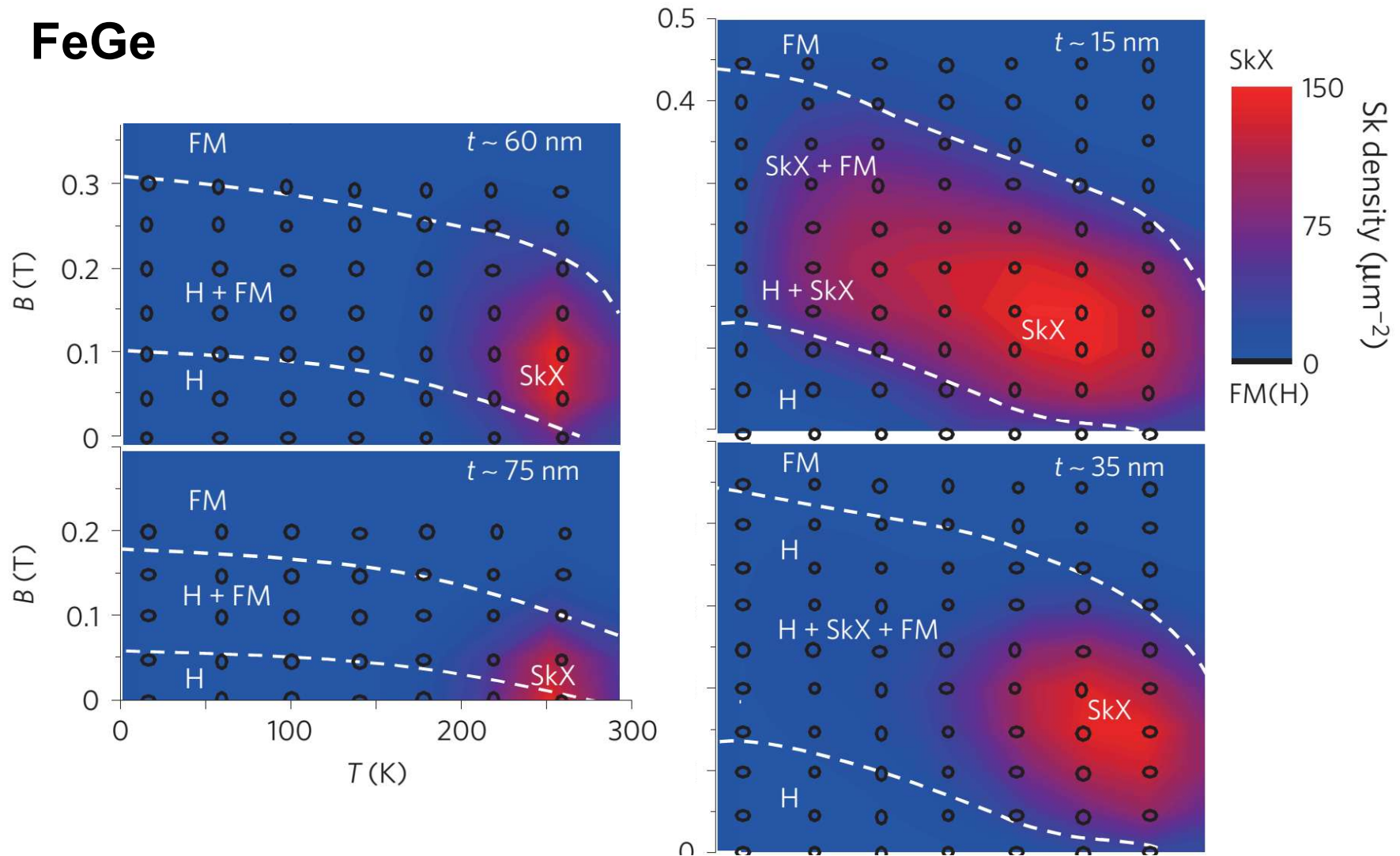
FeGe: 10 nm



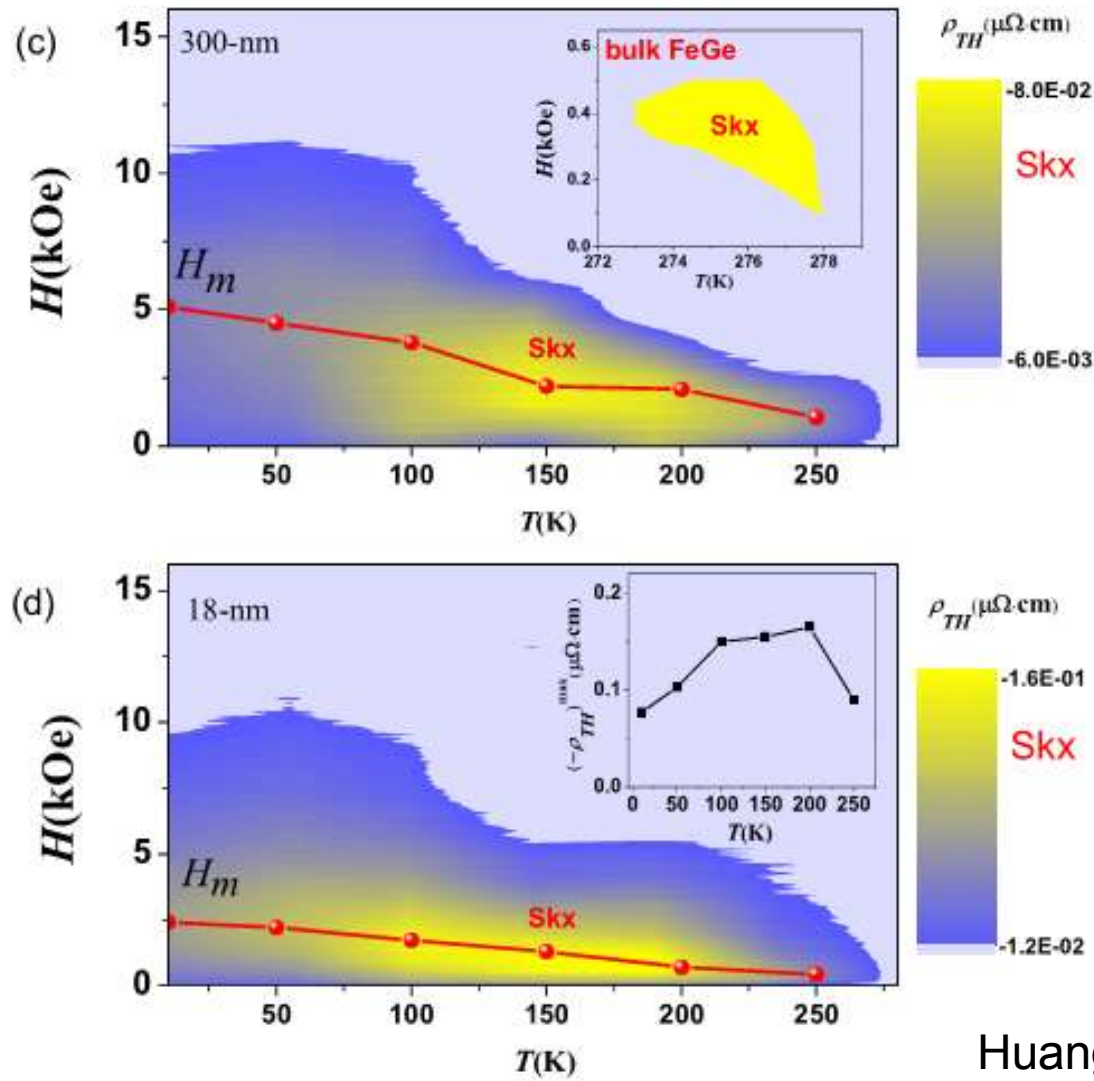
Yu, et al, Nature Materials (2010)

Near Room temperature Skyrmion

FeGe

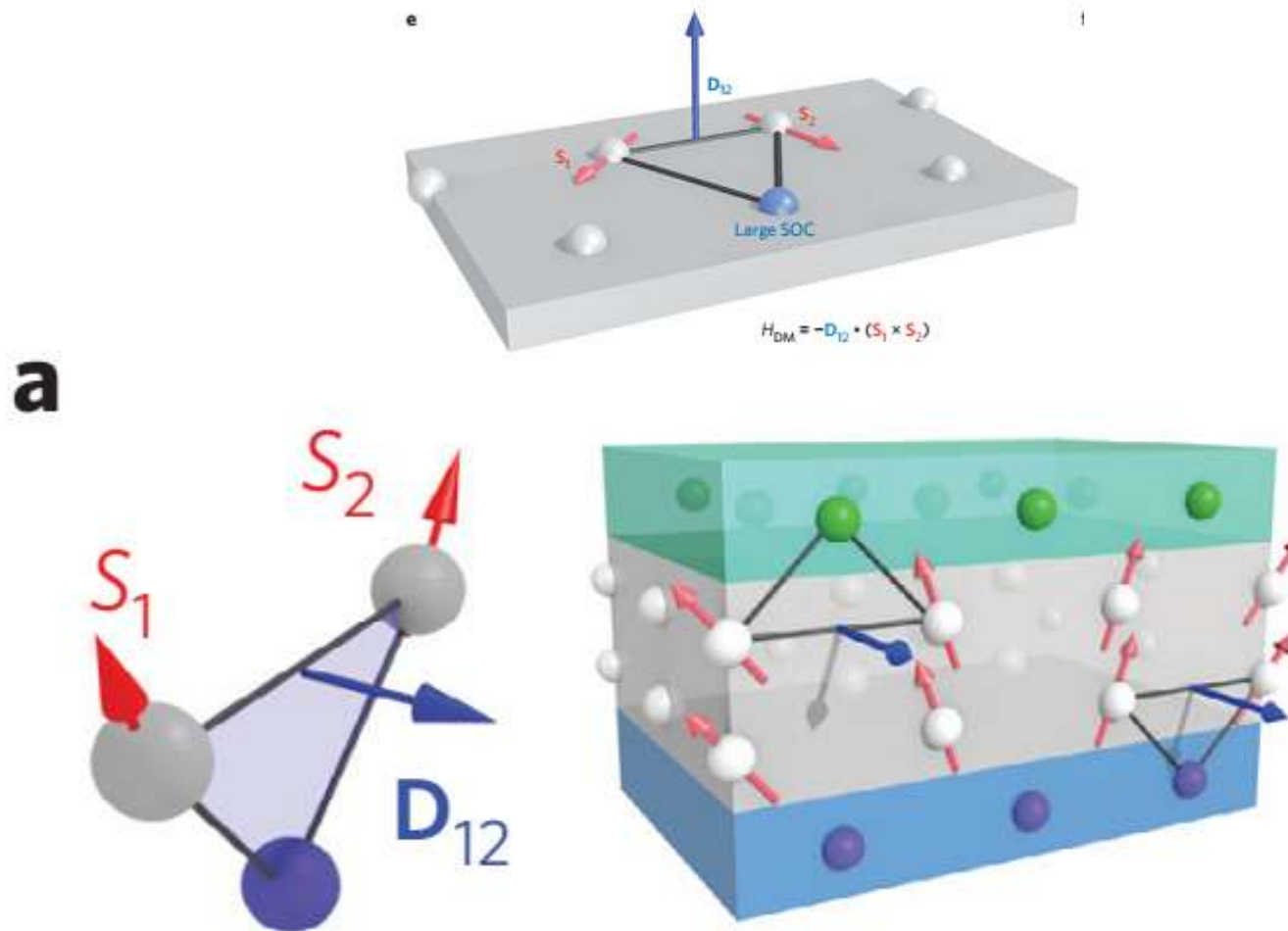


Room temperature Skyrmion



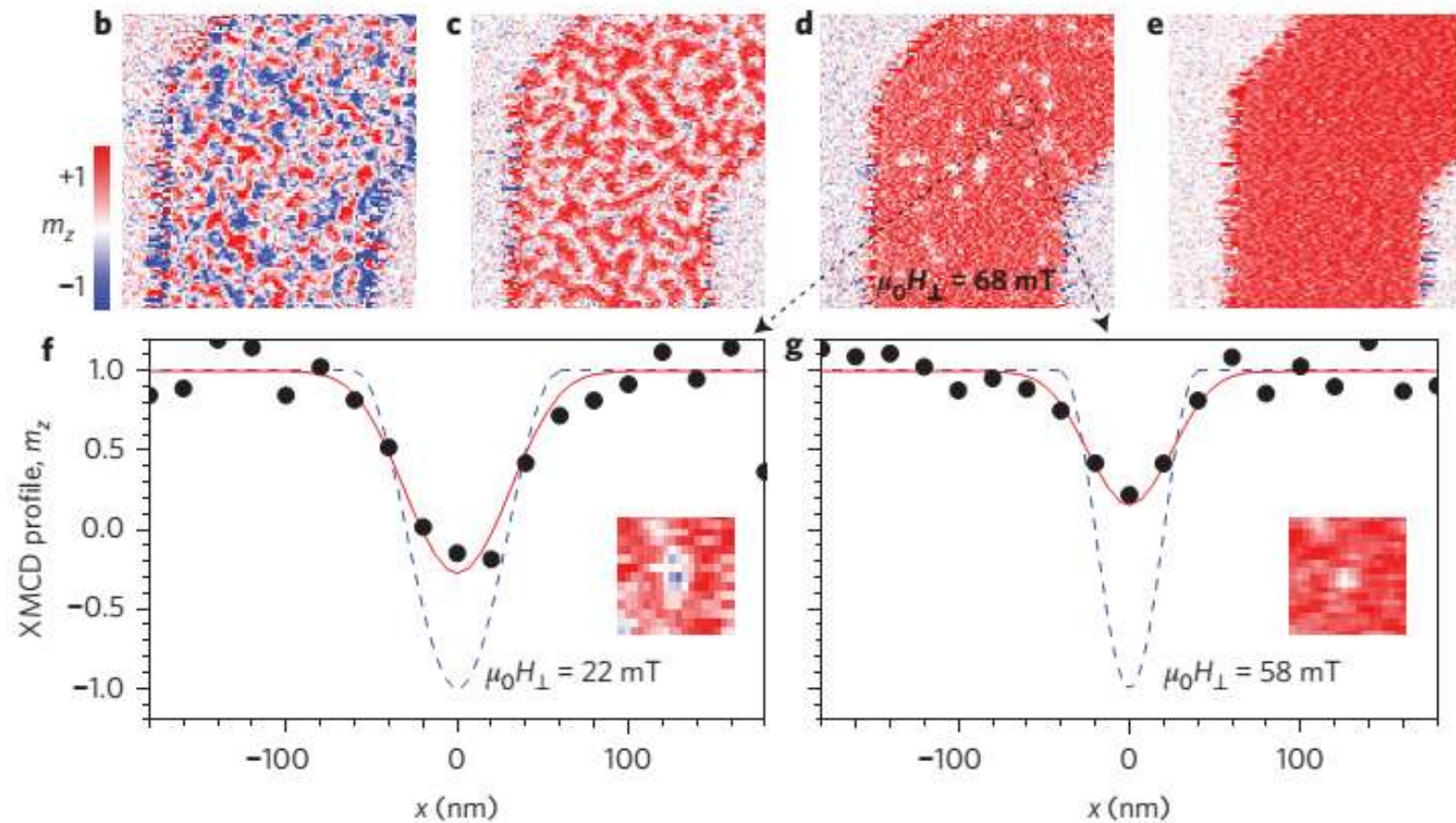
Huang, et al, PRL (2012)

Room temperature Skyrmion

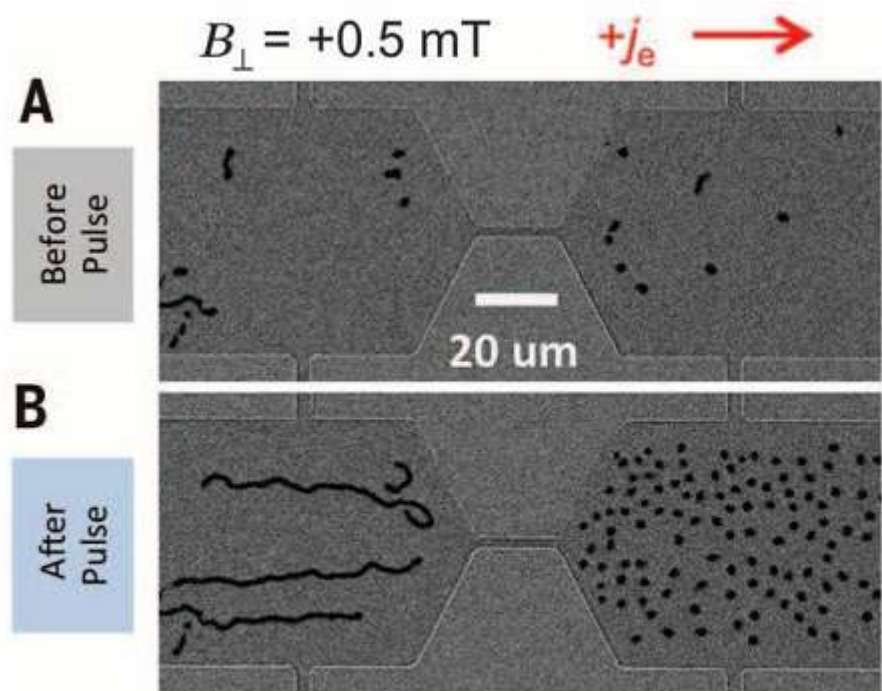
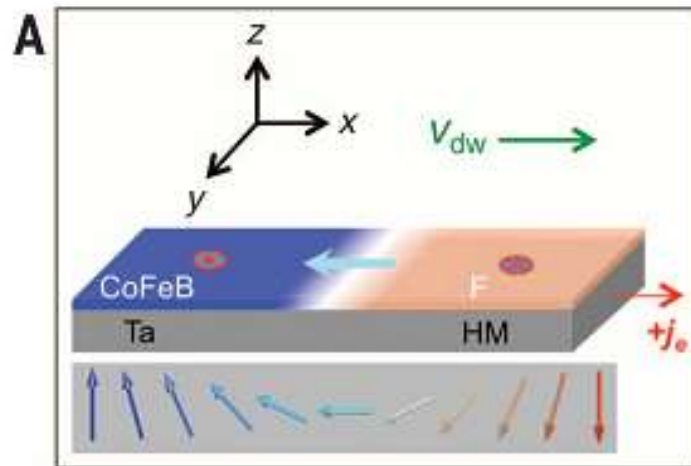


Moreau-Luchaire, et al, Nature Nano (2016)

Room temperature Skyrmion



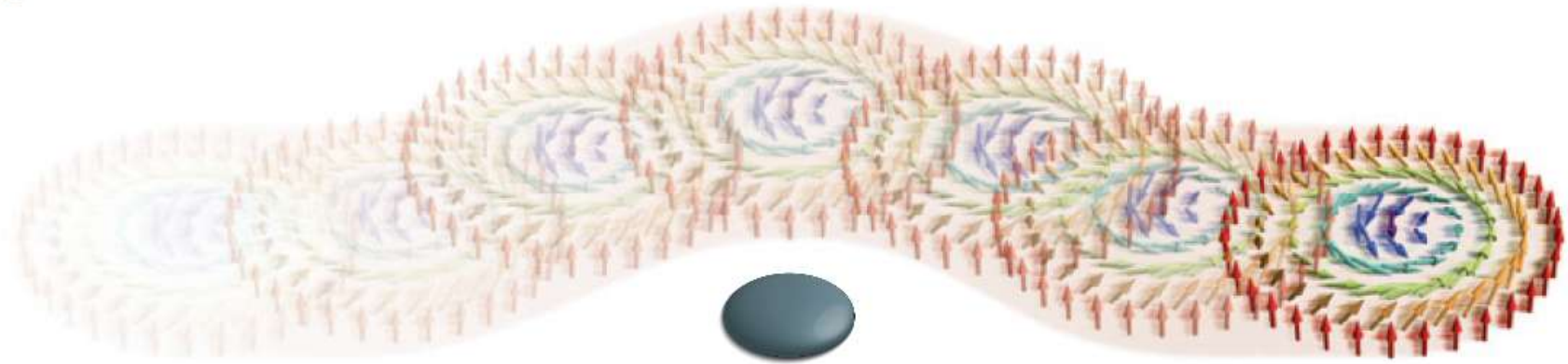
Room temperature Skyrmion



Jiang, et al, Science (2015)

Move a skyrmion

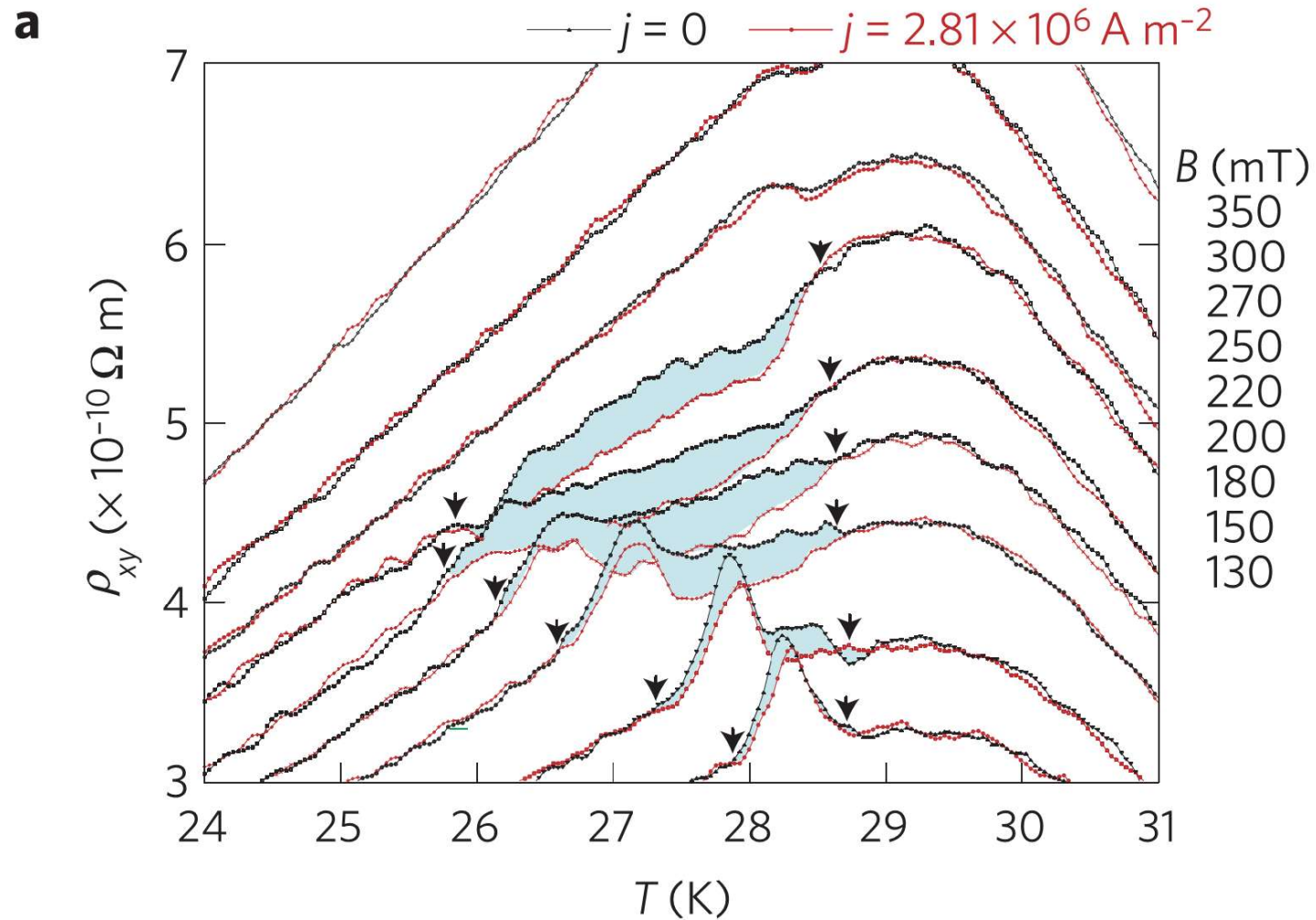
c



Skyrmion moving around obstacle

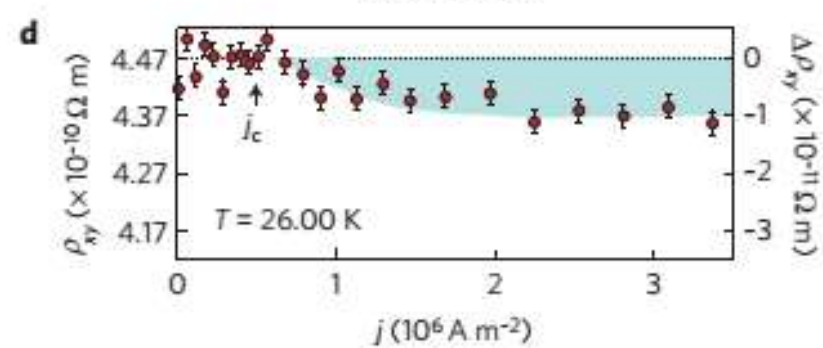
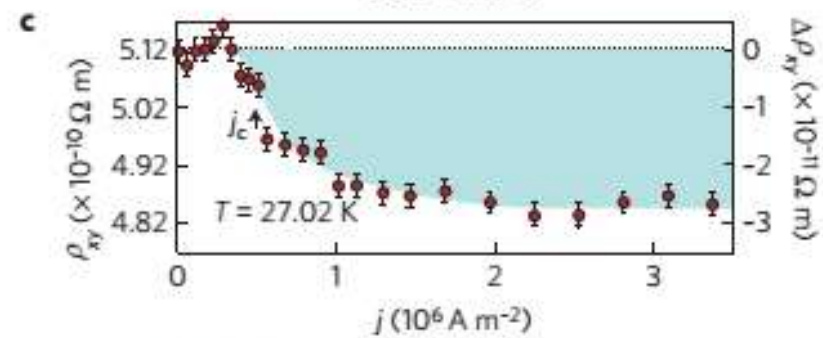
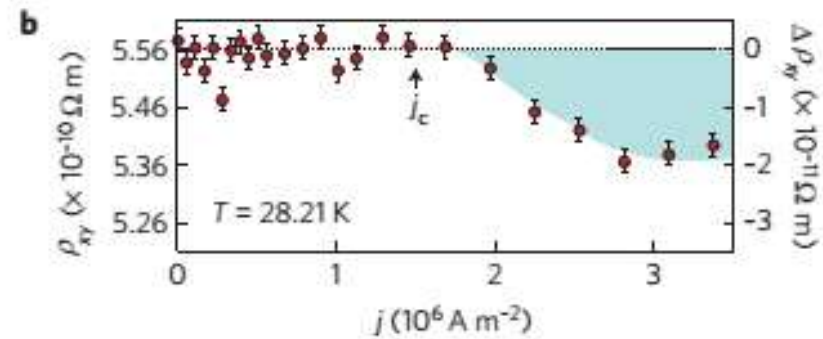
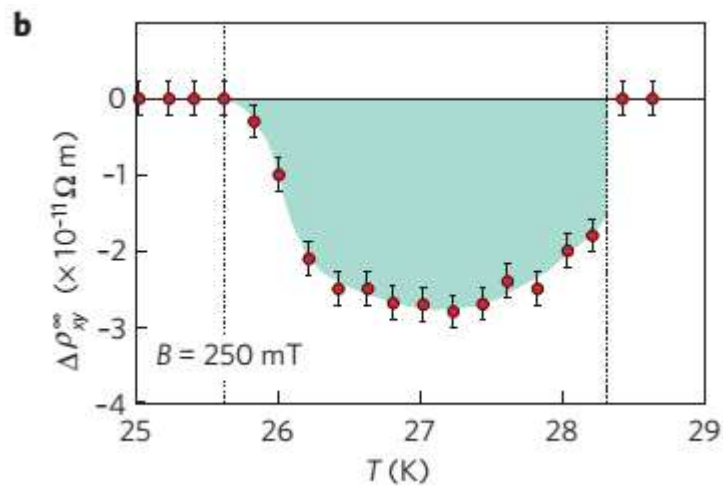
Rosch, et al, Nature Nano (2013)

Move a skyrmion



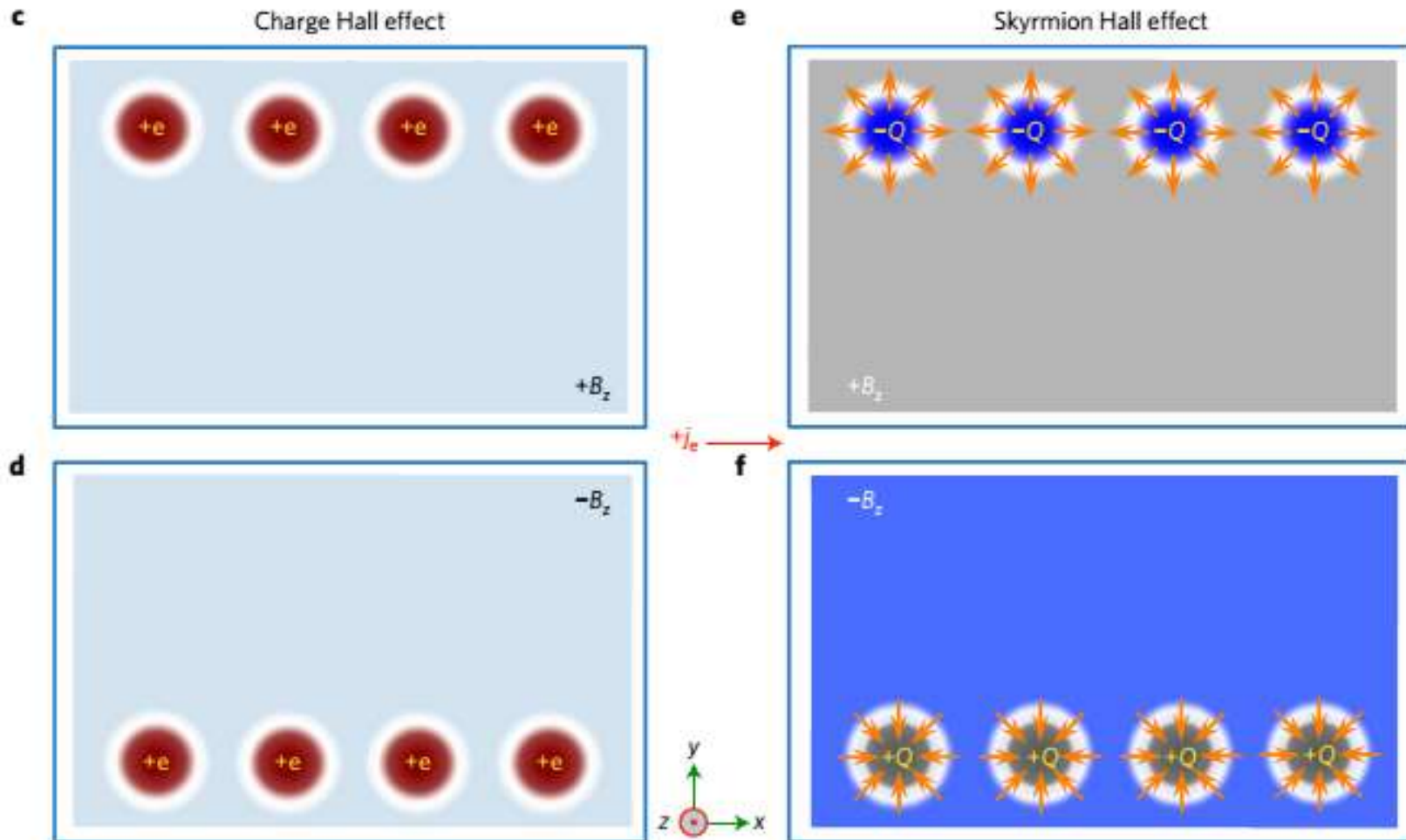
Schulz, et al, Nature Physics (2012)

Move a skyrmion

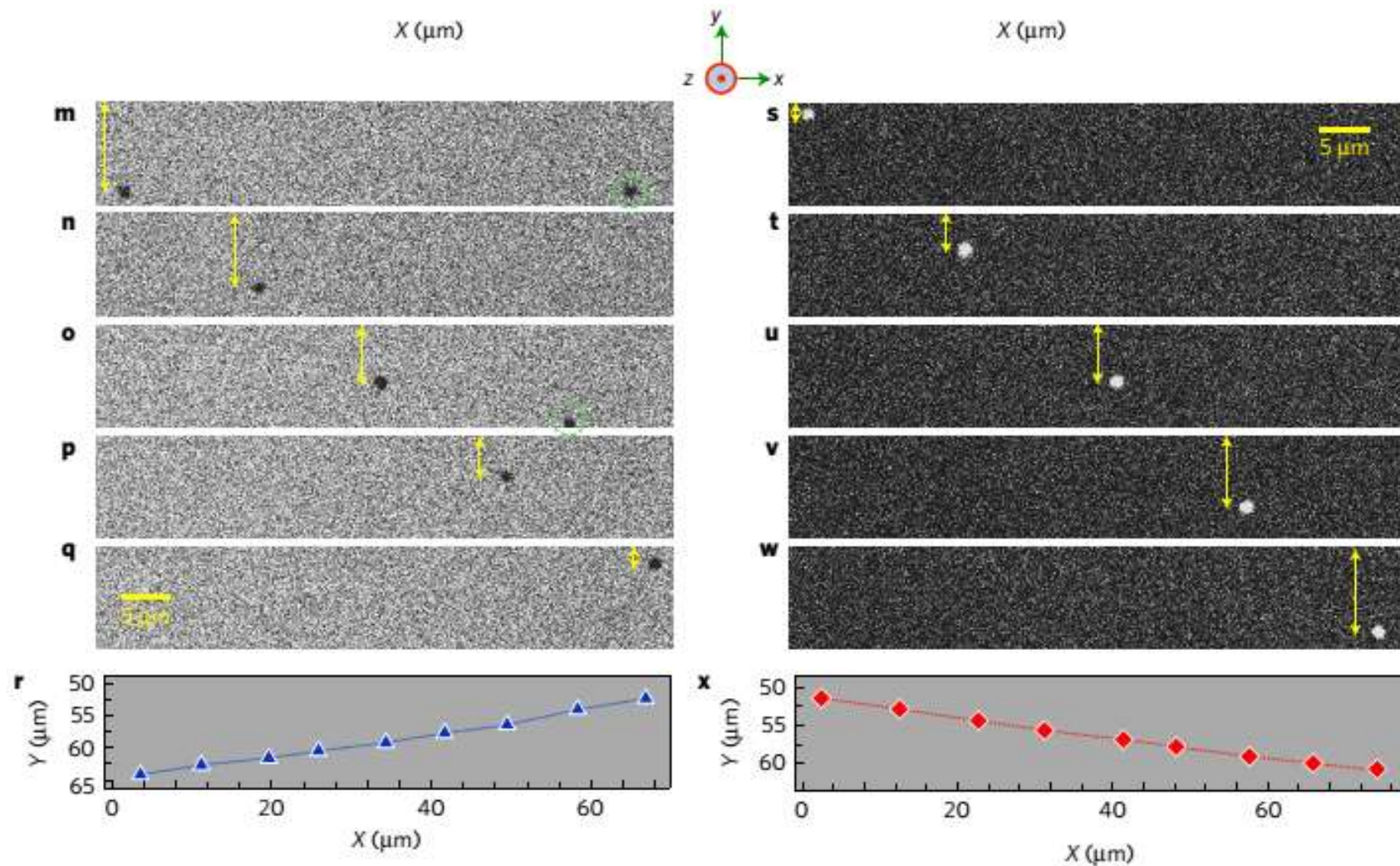


Schulz, et al, Nature Physics (2012)

Skyrmion Hall effect



Skyrmion Hall effect



Jiang, et al, Nature Physics (2016)

Skymion Materials

Table 1 | List of transition temperatures (T_N) and helical periods (λ) of helimagnets.

Material		T_N (K)	λ (nm)	Reference
MnSi	Bulk	30	18	23
	Epitaxial thin film	45	8.5	51
Mn _{1-x} Fe _x Si	x = 0.06	16.5	12.5	25
	x = 0.08	10.6	11	25
	x = 0.10	6.8	10	25
Fe _{1-x} Co _x Si	x = 0.10	11	43	29,33
	x = 0.5	36	90	29,33
	x = 0.6	24	174	29,33
	x = 0.7	7	230	29,33
MnGe	T = 20 K	170	3	50
	T = 100 K	-	3.4	50
	T = 150 K	-	5.5	50
Mn _{1-x} Fe _x Ge	x = 0.35	150	4.7	38
	x = 0.5	185	14.5	38
	x = 0.7	210	77	38
	x = 0.84	220	220	38
FeGe	Bulk	278	70	34
Cu ₂ OSeO ₃	Bulk	59	62	76
	Thinned plate	-	50	86

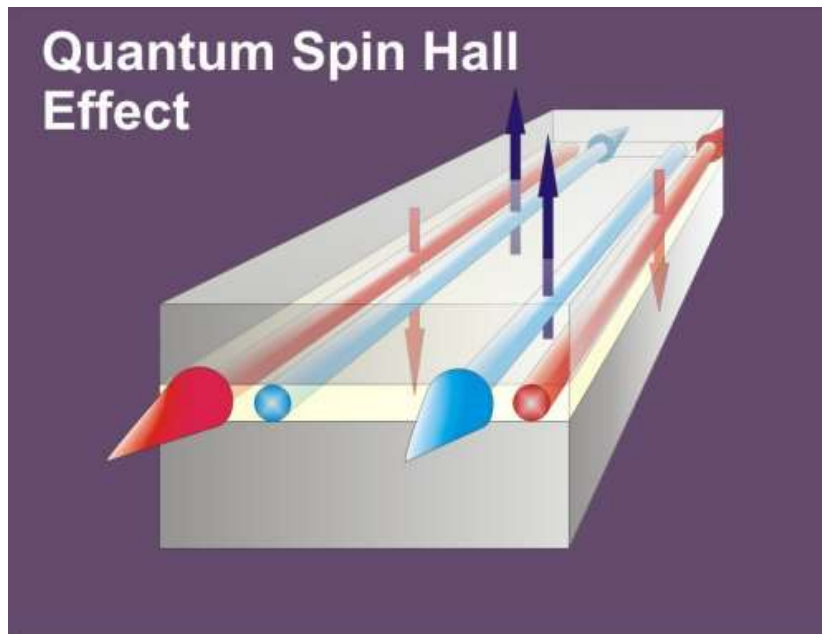
Nagaosa & Tokura,
Nature Nano (2013)

4. Spin-momentum locking of 3D TI

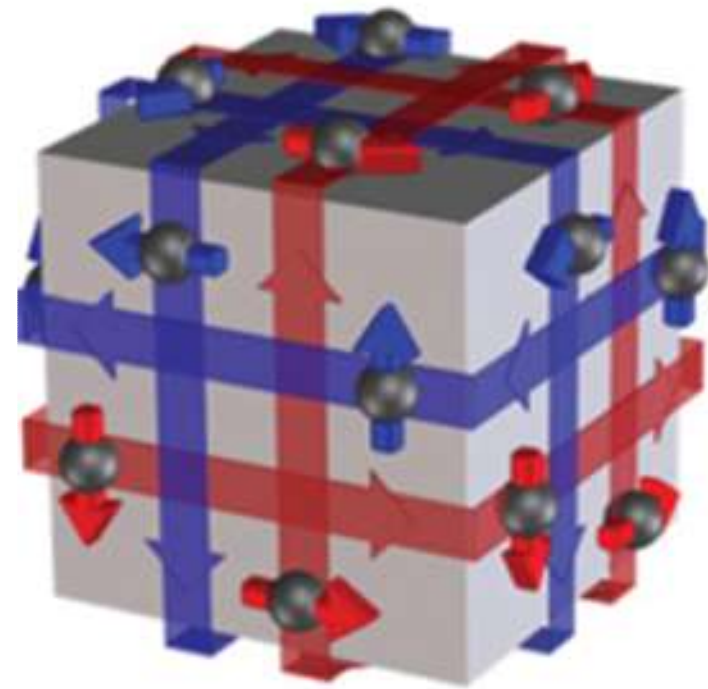
- Spin injection
- Spin orbit torque
- Spin Seebeck effect

Spin momentum locking

2D Topological insulator

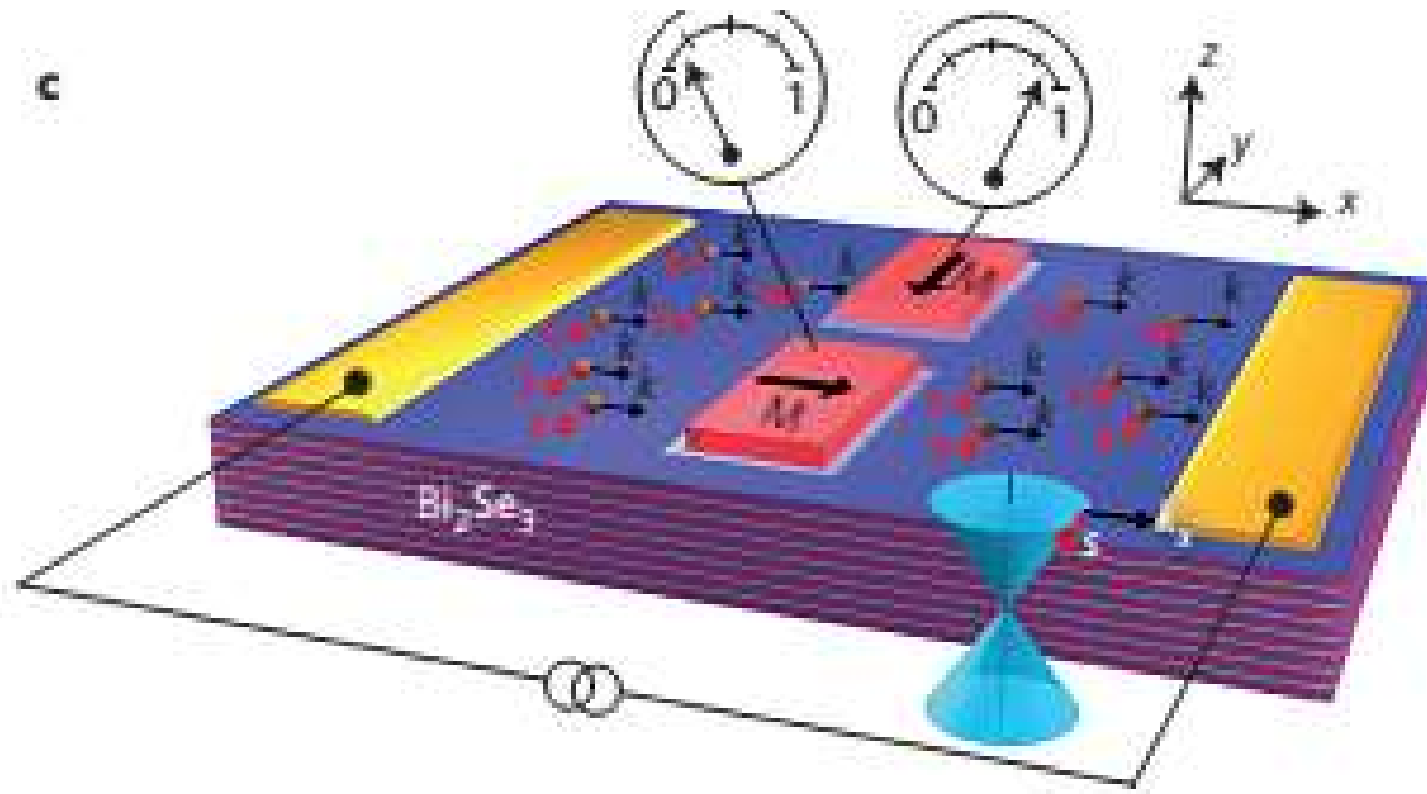


3D Topological insulator



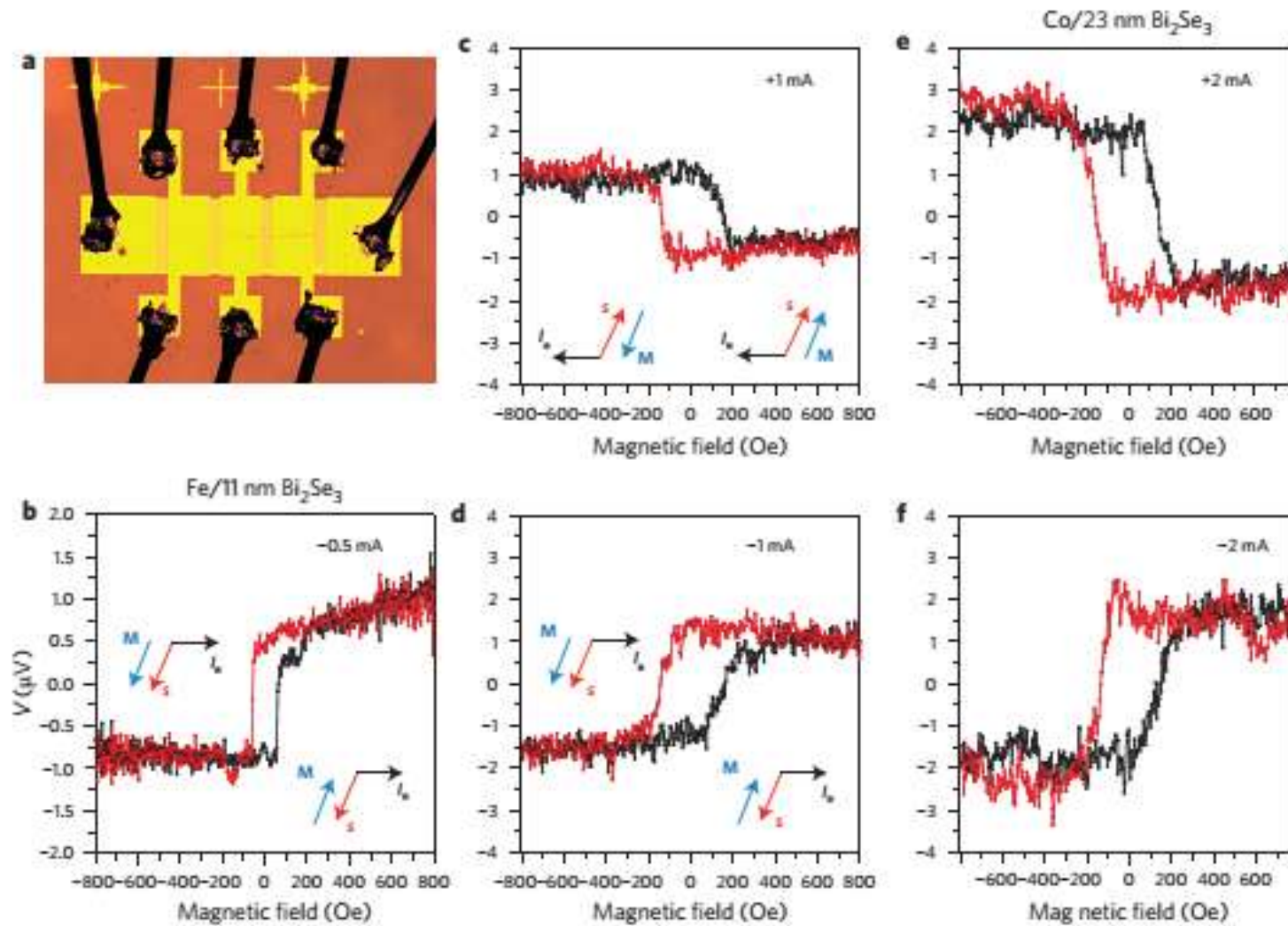
Hasan & Kane, Rev Mod Phys (2009)
Qi & Zhang, Rev Mod Phys (2011)

Spin momentum locking



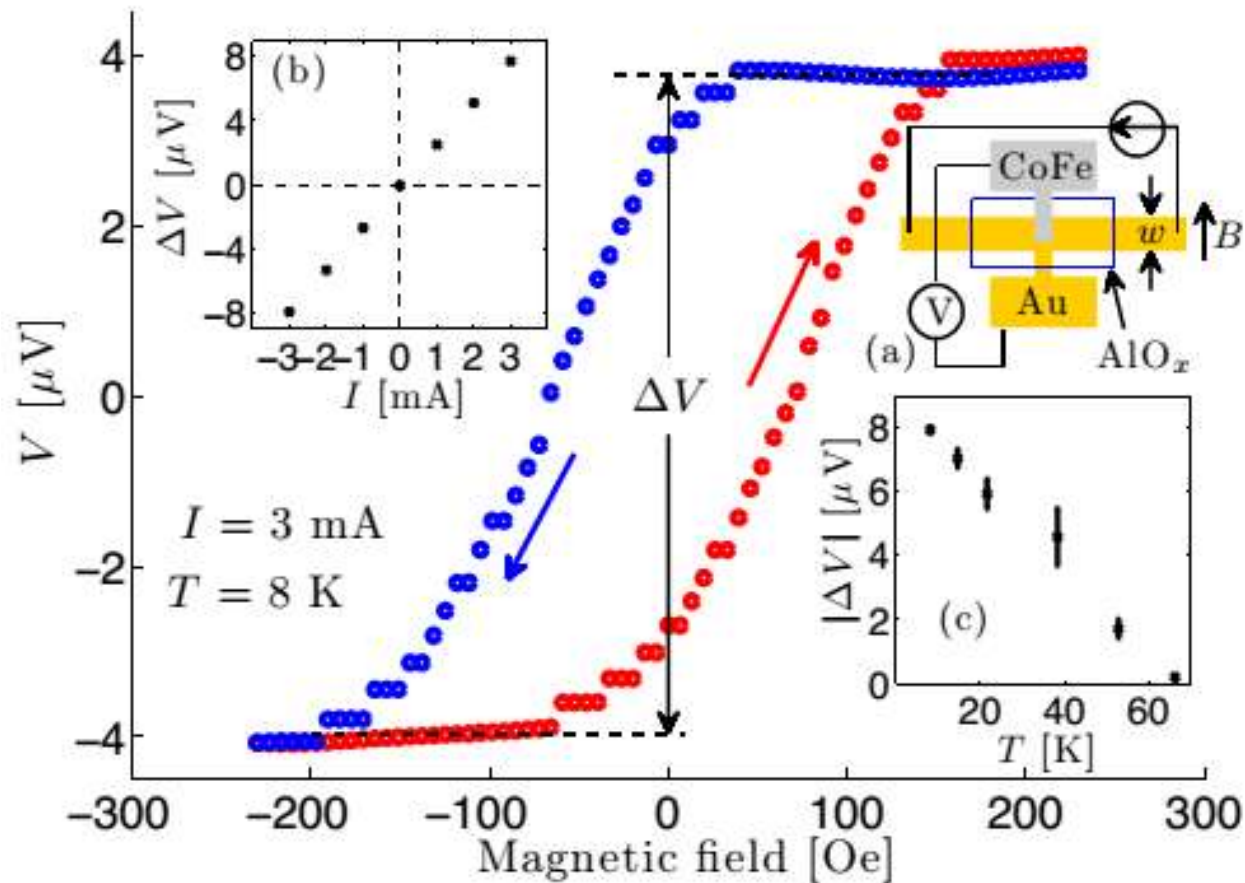
Li, et al, Nature Nanotechnology (2014).

Spin momentum locking



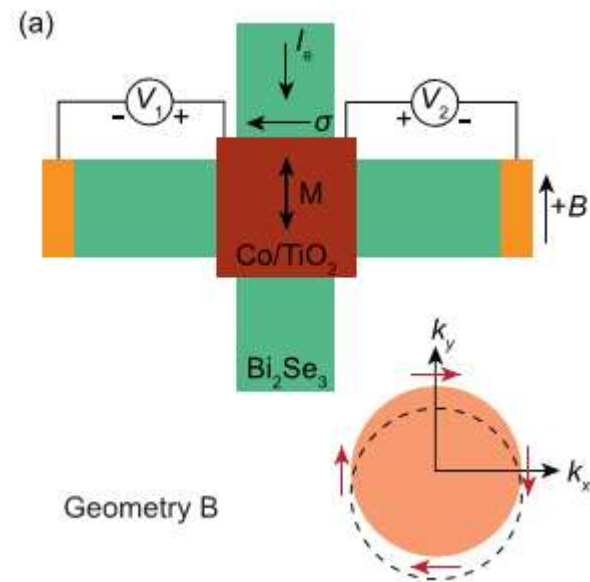
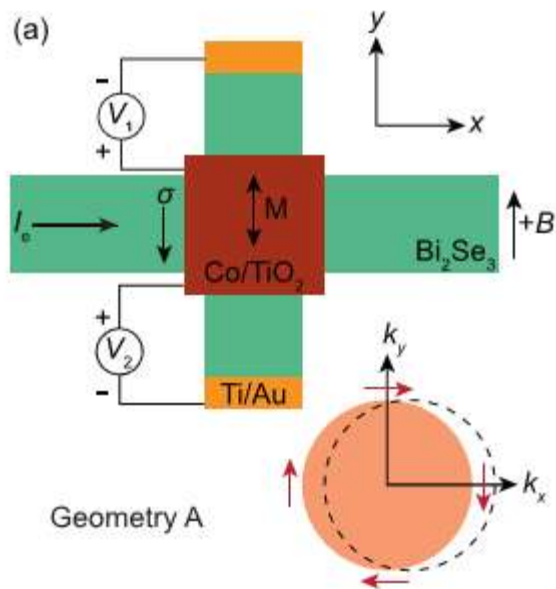
Spin momentum locking

Real spin or not?

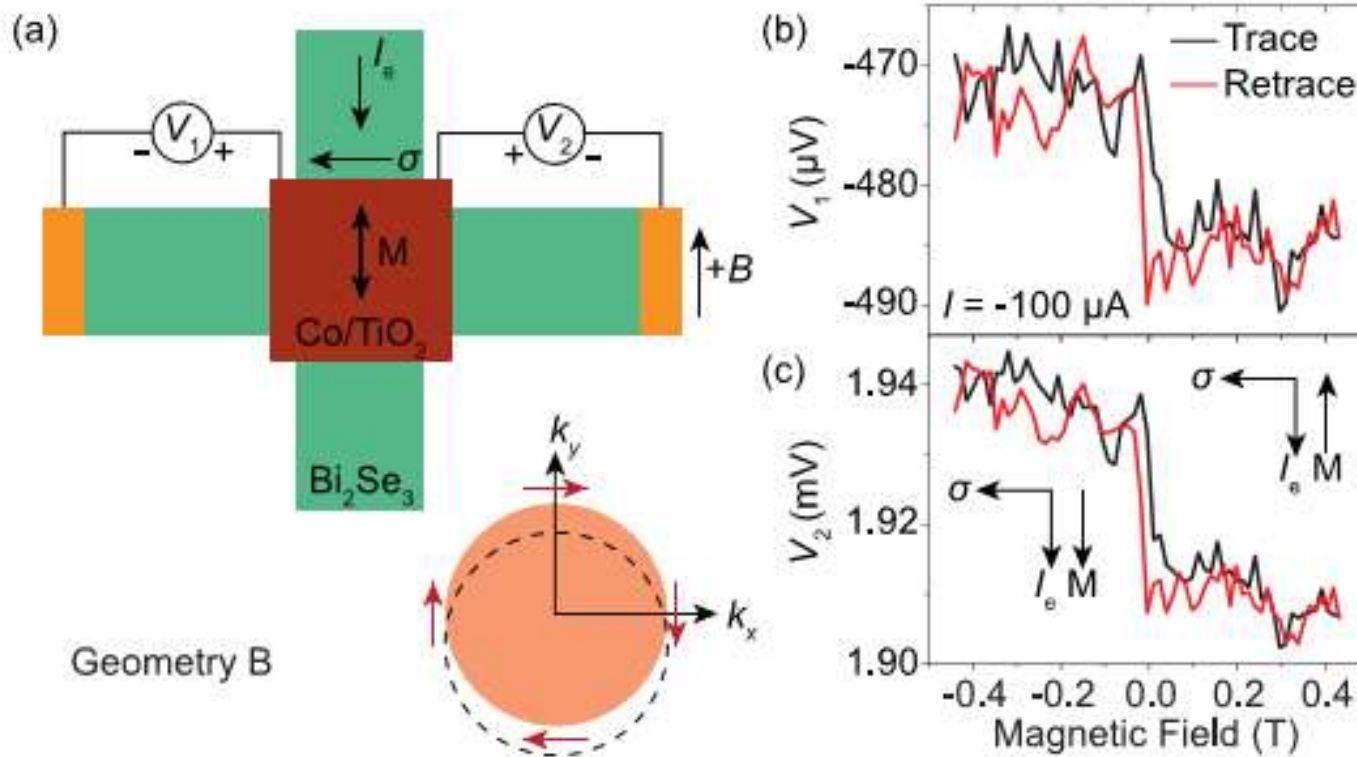


Li & Appelbaum, PRB (2016)

Spin momentum locking

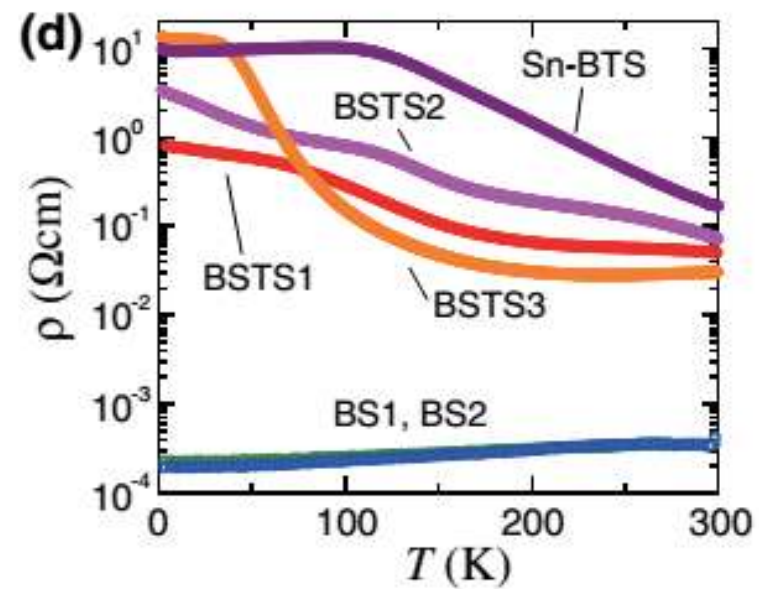
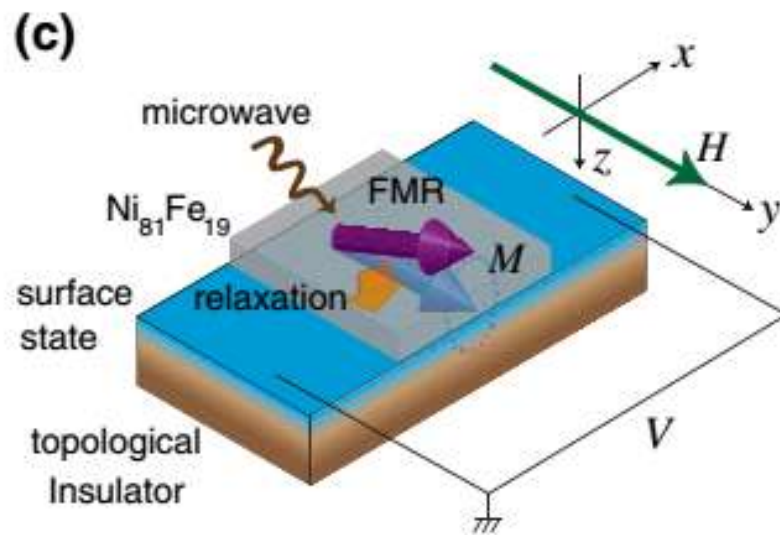


Spin momentum locking



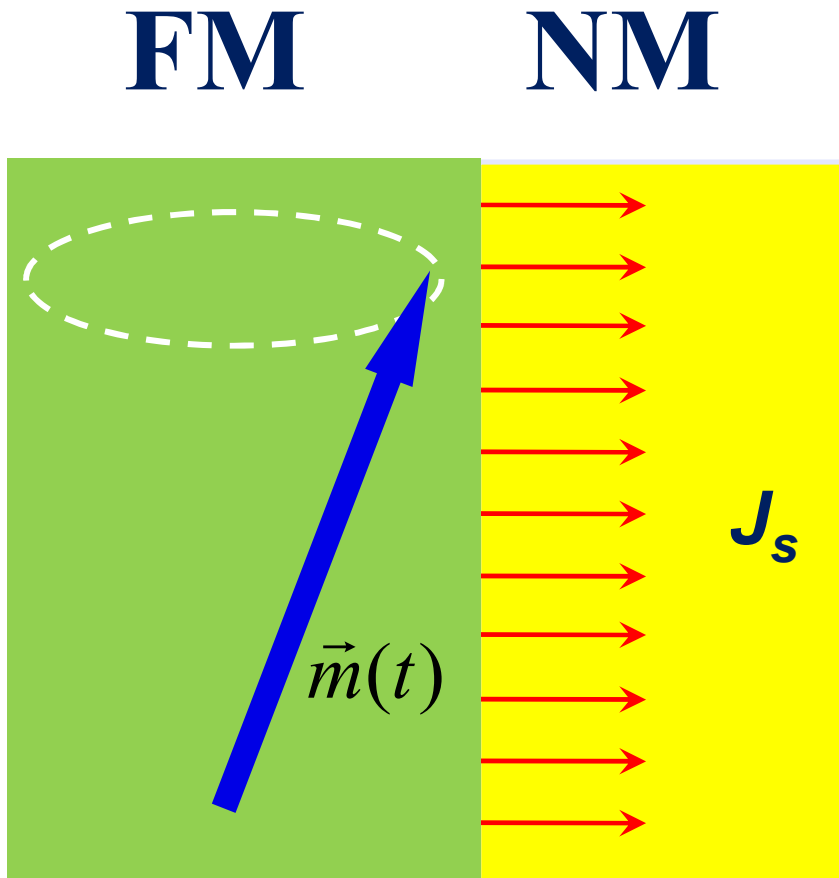
Signal not from the TI surface states !!

Spin momentum locking



Shiomi, et al, PRL (2014)

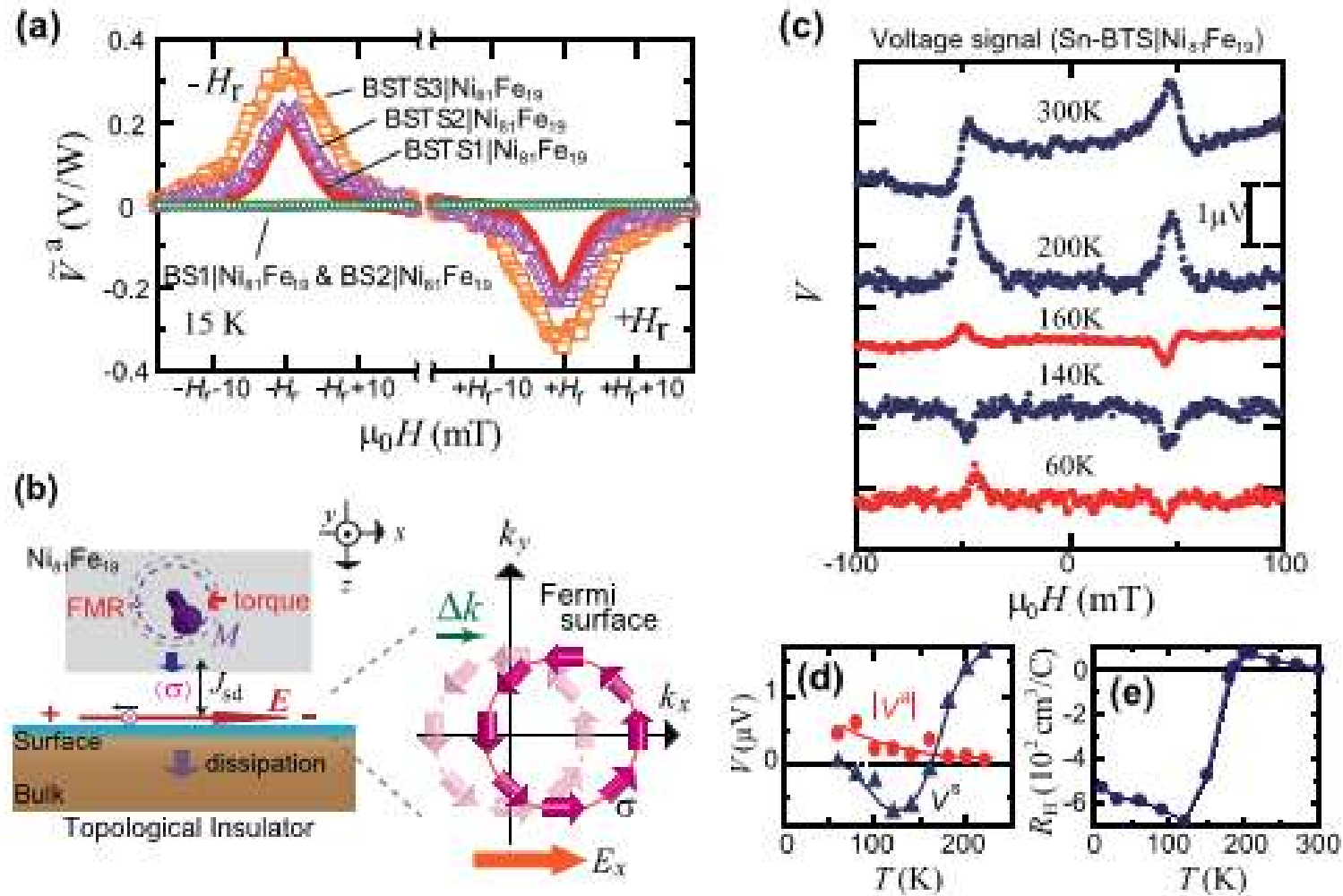
Spin momentum locking



$$\vec{J}_s = \frac{\hbar g_r^{\uparrow\downarrow}}{4\pi M^2} \left(\vec{M} \times \frac{\partial \vec{M}}{\partial t} \right)$$

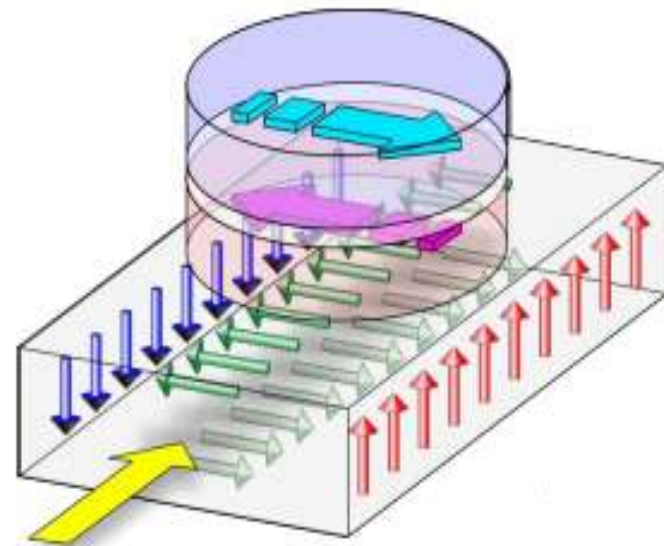
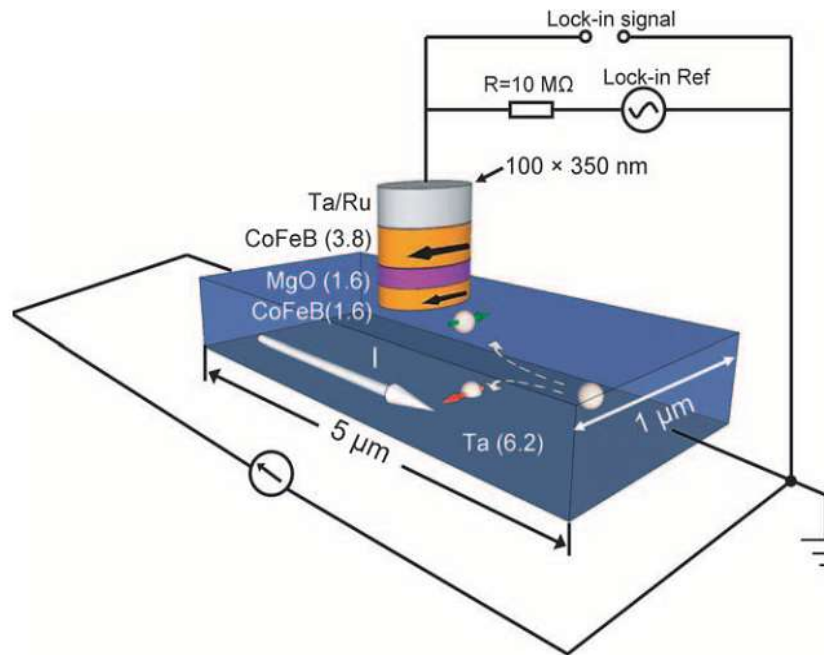
Precessing **magnetization** in
FM layer pump **spin** current
into NM layer
(Angular momentum
conservatoin)

Spin momentum locking



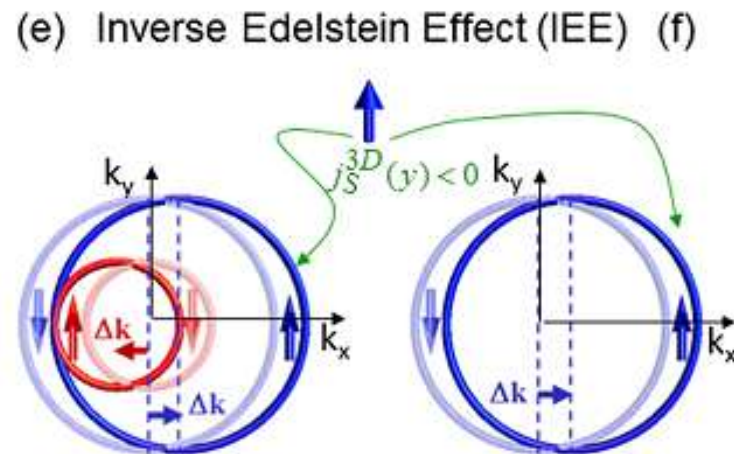
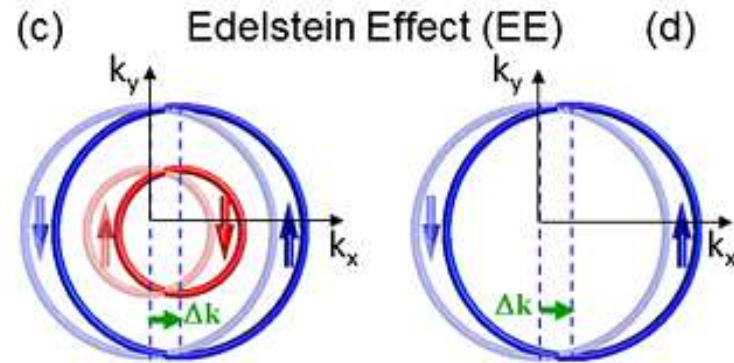
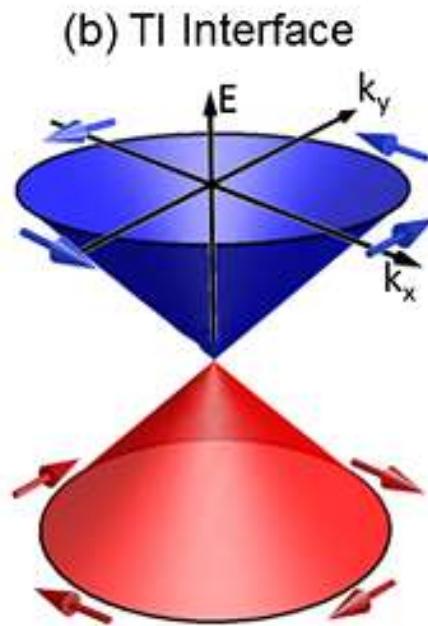
Shiomi, et al, PRL (2014)

Spin orbit torque



Liu, et al, Science (2012)

Spin orbit torque



$$j_C^{2D} = \lambda_{IEE} j_S^{3D}$$

$$\lambda_{IEE} = \frac{\alpha_R \tau}{\hbar}$$

$$j_C^{2D} = \lambda_{IEE} j_S^{3D}$$

$$\lambda_{IEE} = v_F \tau$$

Spin orbit torque

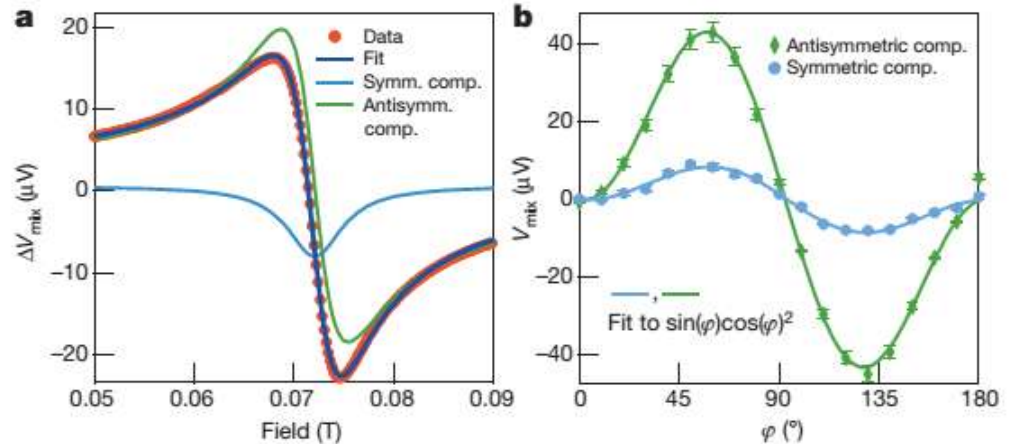
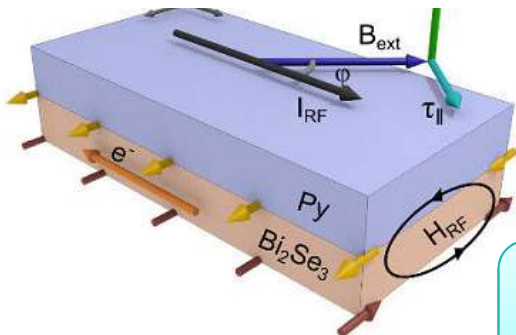
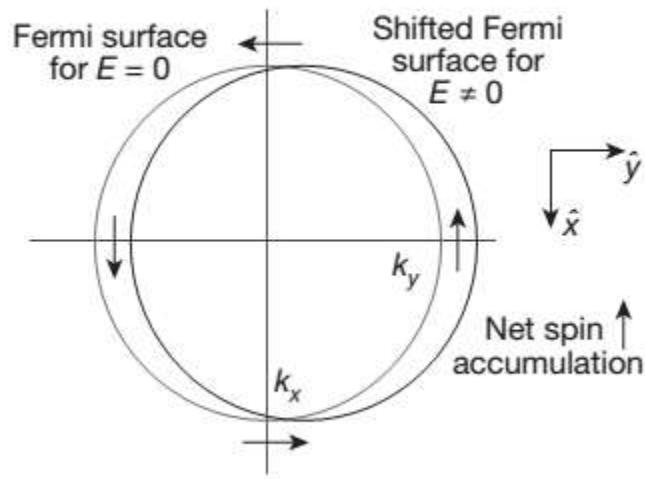
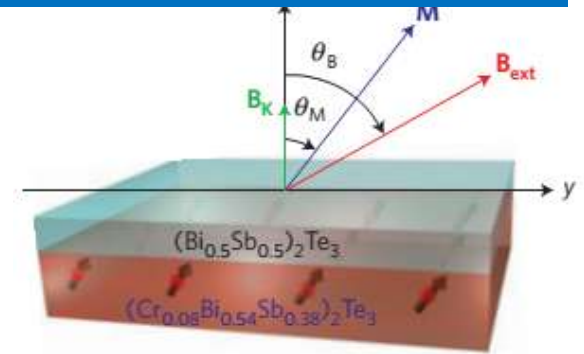
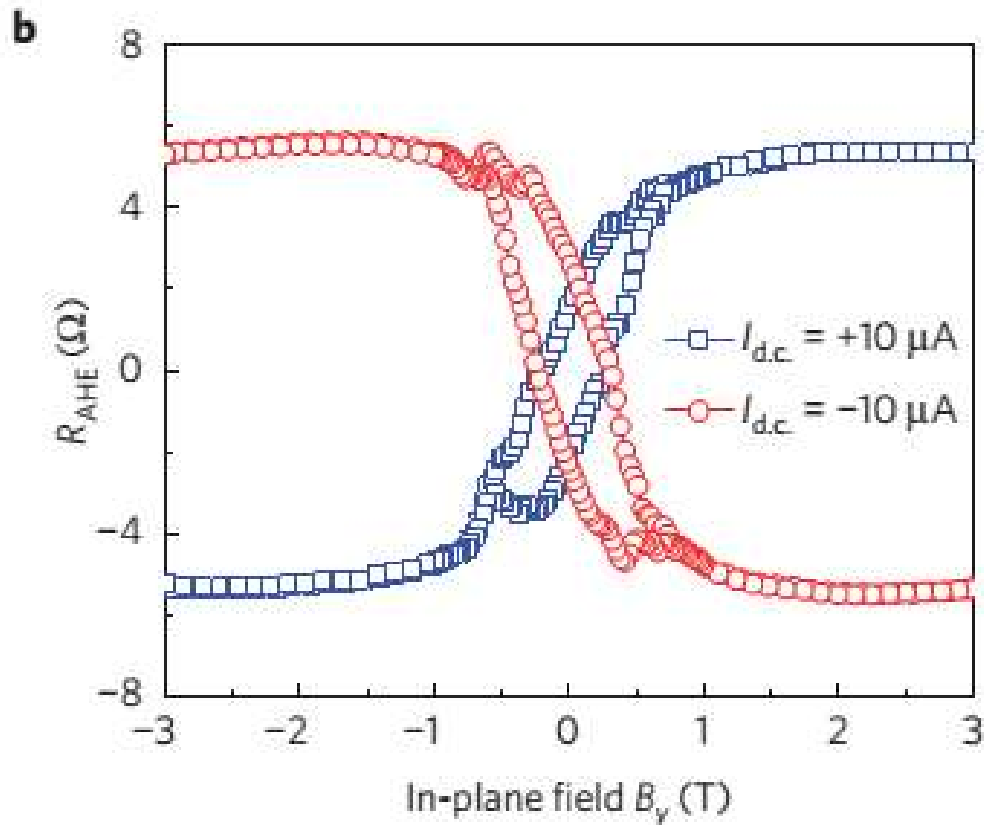


Table 1 | Comparison of room-temperature $\sigma_{\text{s},\parallel}$ and $\theta_{\text{s},\parallel}$ for Bi_2Se_3 with other materials

Parameter	Bi_2Se_3 (this work)	Pt (ref. 4)	β -Ta (ref. 6)	Cu(Bi) (ref. 23)	β -W (ref. 24)
θ_{SH}	2.0–3.5	0.08	0.15	0.24	0.3 1.8

Spin Hall angle: 2.0-3.5

Spin orbit torque



T=1.9 K
SHA > 100

Fan, et al, Nature Mater. (2014)

Spin orbit torque



SHA > 100??

PRL **119**, 137204 (2017)

PHYSICAL REVIEW LETTERS

week ending
29 SEPTEMBER 2017

Current-Nonlinear Hall Effect and Spin-Orbit Torque Magnetization Switching in a Magnetic Topological Insulator

K. Yasuda,^{1,*} A. Tsukazaki,² R. Yoshimi,³ K. Kondou,³ K. S. Takahashi,^{3,4} Y. Otani,^{3,5} M. Kawasaki,^{1,3} and Y. Tokura^{1,3}

¹Department of Applied Physics and Quantum-Phase Electronics Center (QPEC), University of Tokyo, Tokyo 113-8656, Japan

²Institute for Materials Research, Tohoku University, Sendai 980-8577, Japan

³RIKEN Center for Emergent Matter Science (CEMS), Wako 351-0198, Japan

⁴PRESTO, Japan Science and Technology Agency (JST), Chiyoda-ku, Tokyo, 102-0075, Japan

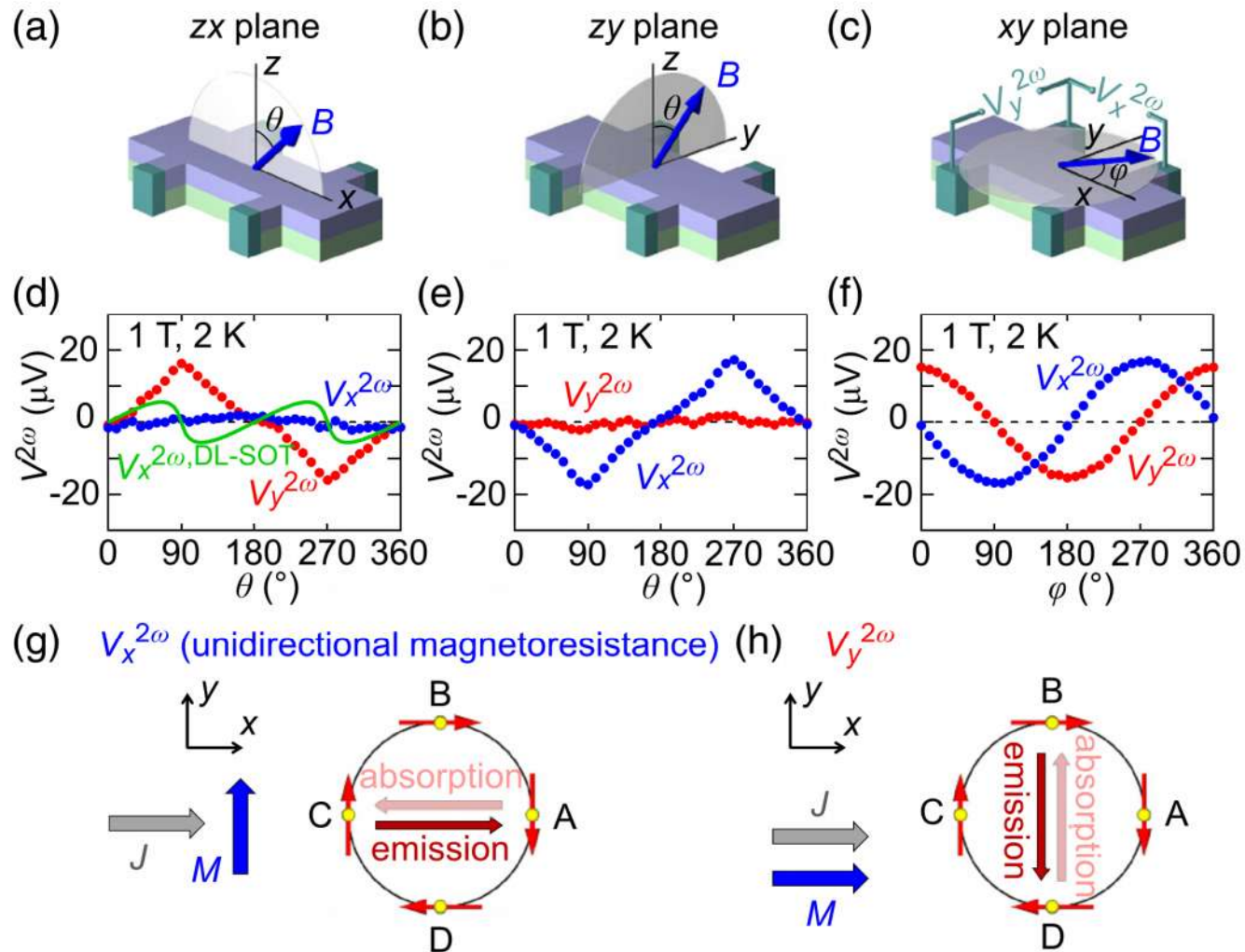
⁵Institute for Solid State Physics (ISSP), University of Tokyo, Kashiwa 277-8581, Japan

(Received 25 March 2017; published 28 September 2017)

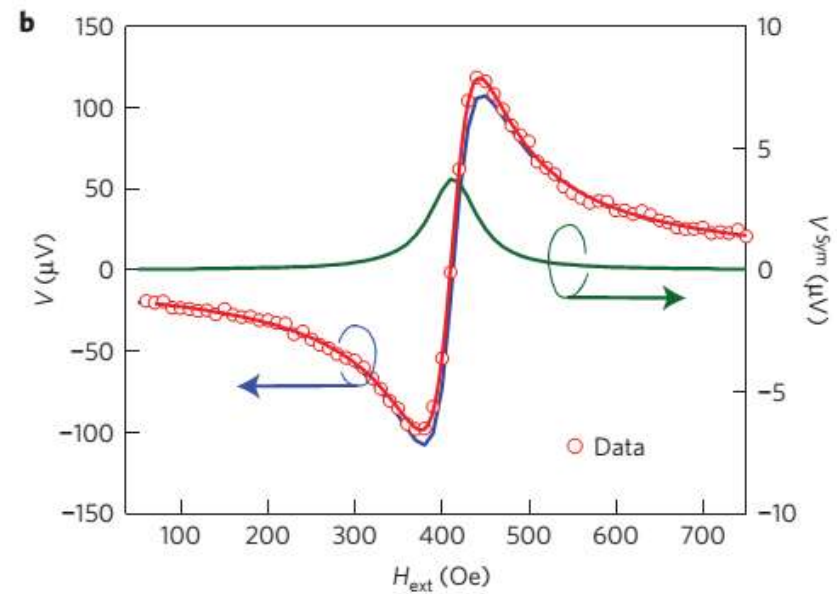
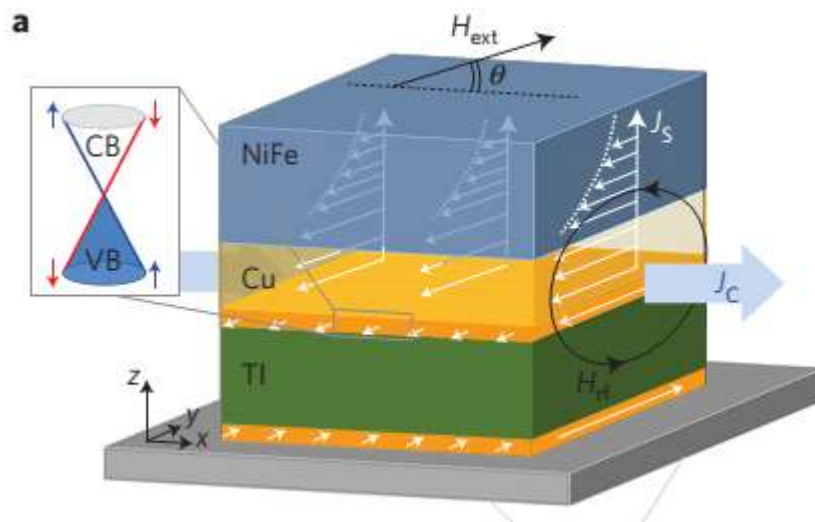
The current-nonlinear Hall effect or second harmonic Hall voltage is widely used as one of the methods for estimating charge-spin conversion efficiency, which is attributed to the magnetization oscillation by spin-orbit torque (SOT). Here, we argue the second harmonic Hall voltage under a large in-plane magnetic field with an in-plane magnetization configuration in magnetic-nonmagnetic topological insulator (TI) heterostructures, $\text{Cr}_x(\text{Bi}_{1-y}\text{Sb}_y)_{2-x}\text{Te}_3/(\text{Bi}_{1-y}\text{Sb}_y)_2\text{Te}_3$, where it is clearly shown that the large second harmonic voltage is governed not by SOT but mainly by asymmetric magnon scattering without macroscopic magnetization oscillation. Thus, this method does not allow an accurate estimation of charge-spin conversion efficiency in TI. Instead, the SOT contribution is exemplified by current pulse induced nonvolatile magnetization switching, which is realized with a current density of $2.5 \times 10^{10} \text{ A m}^{-2}$, showing its potential as a spintronic material.

Yasuda, et al, PRL (2017)

Spin orbit torque

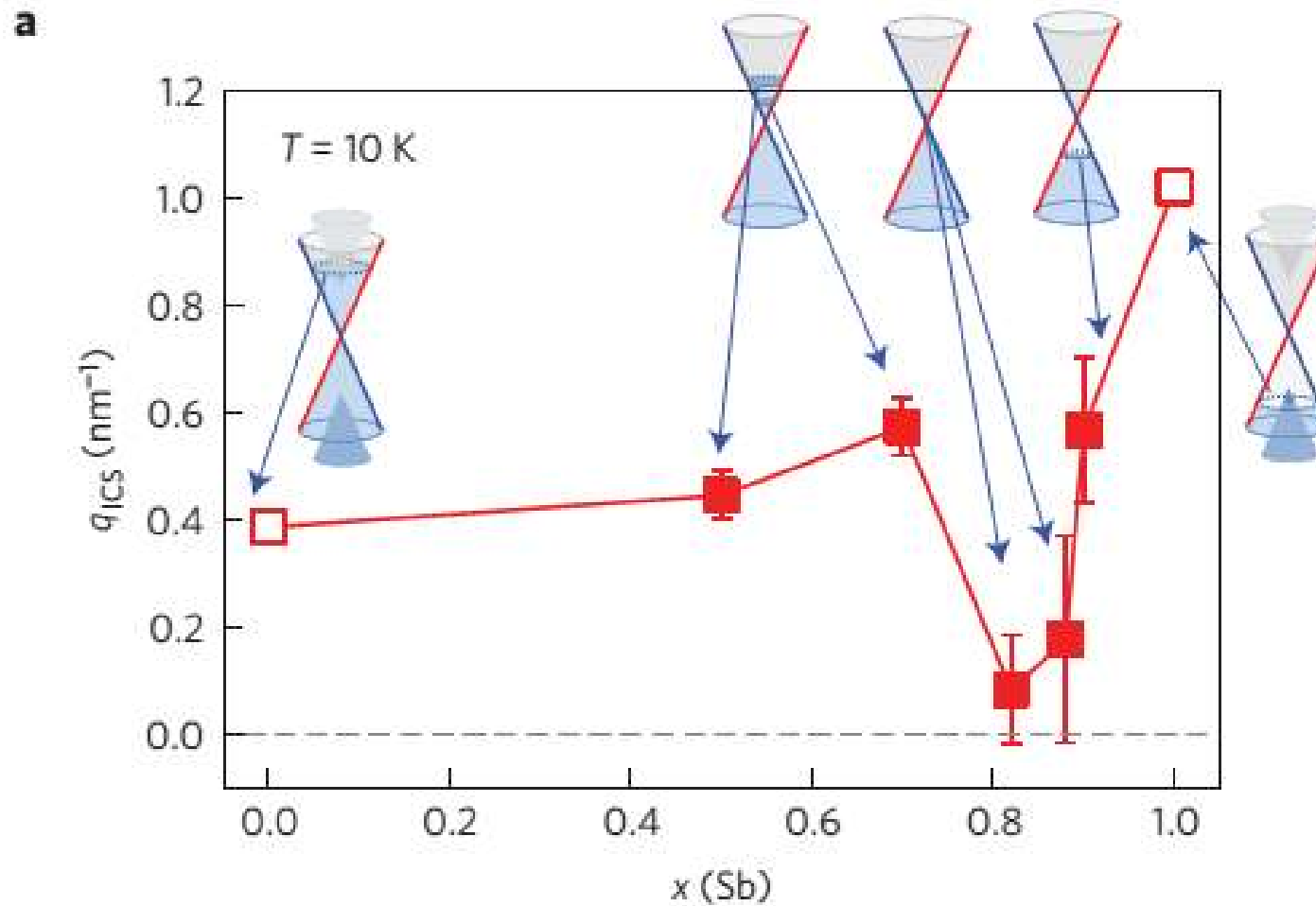


Gate tunable spin orbit torque

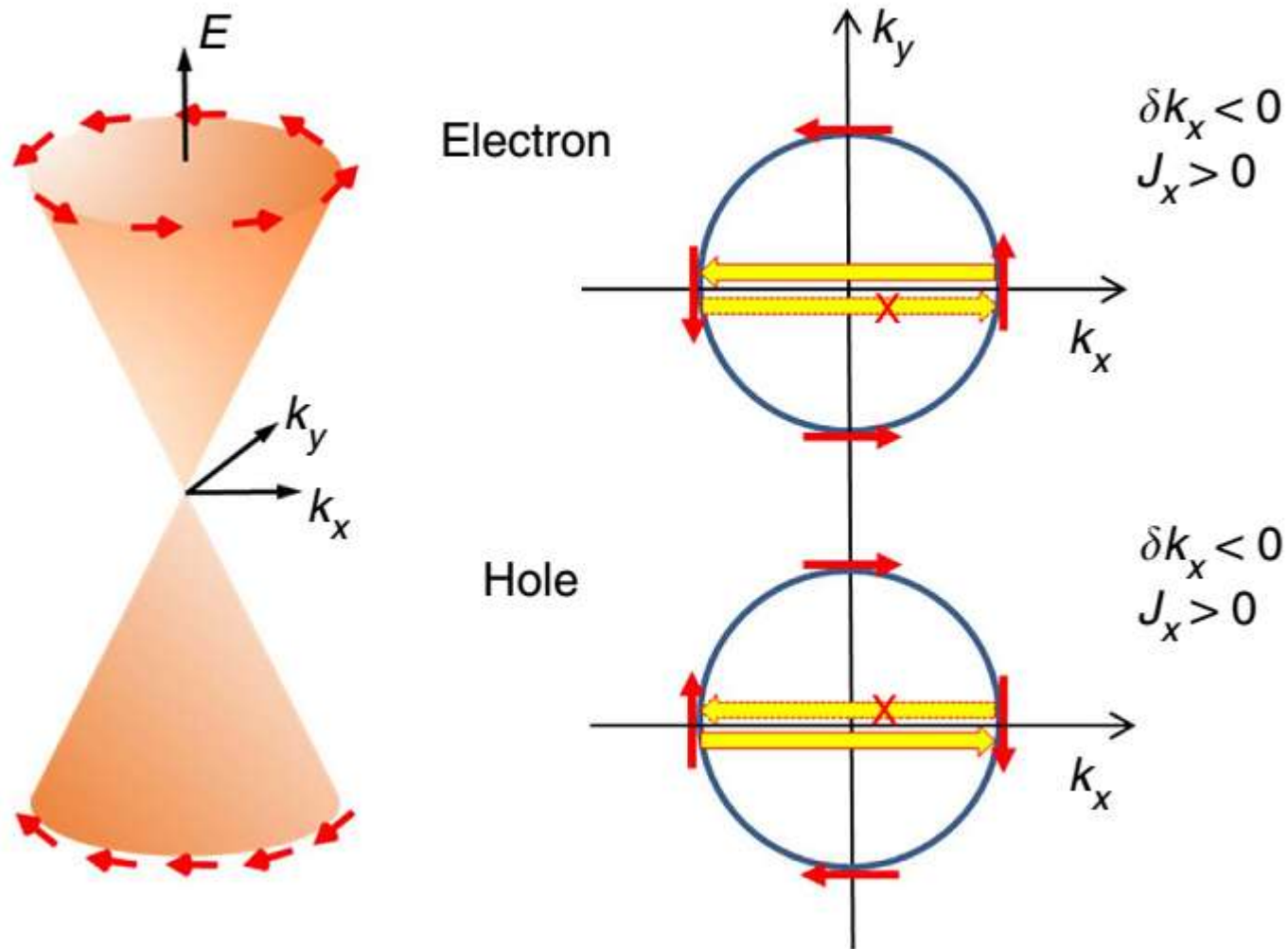


Kondou, et al, Nature Physics (2016)

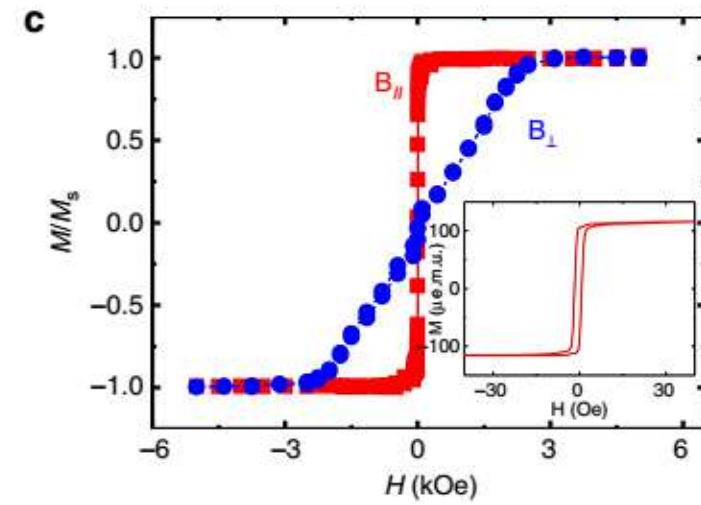
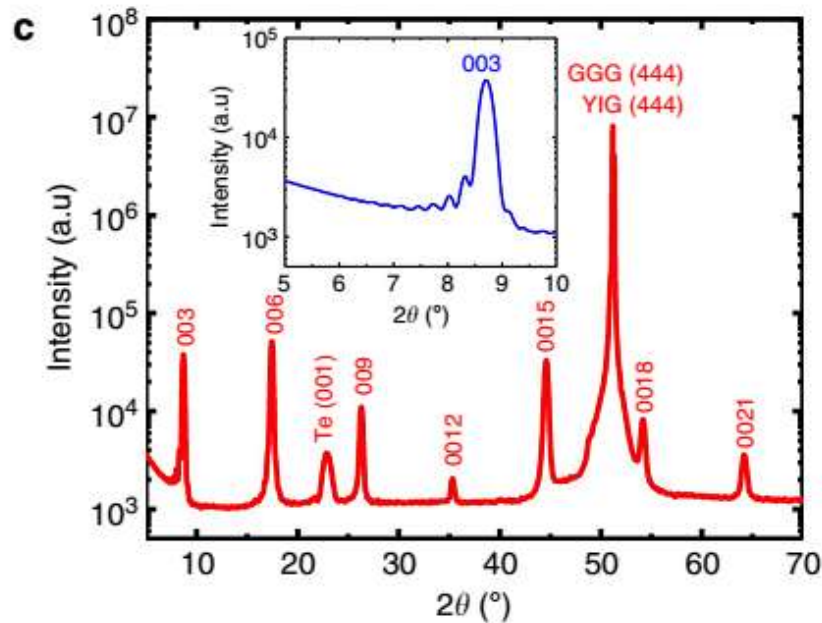
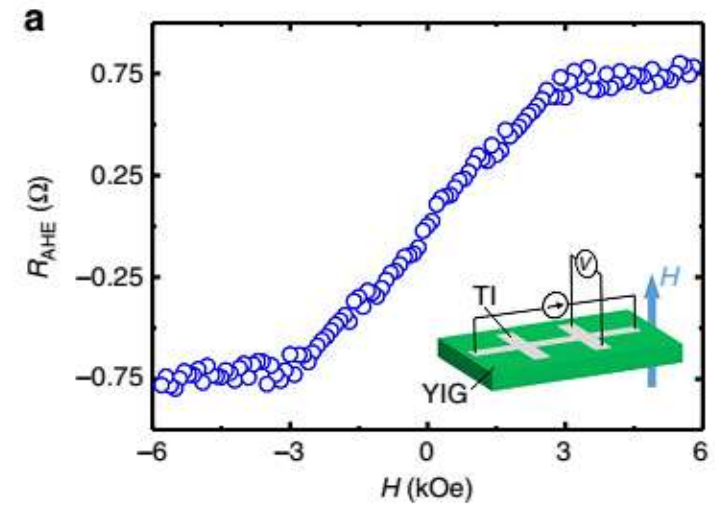
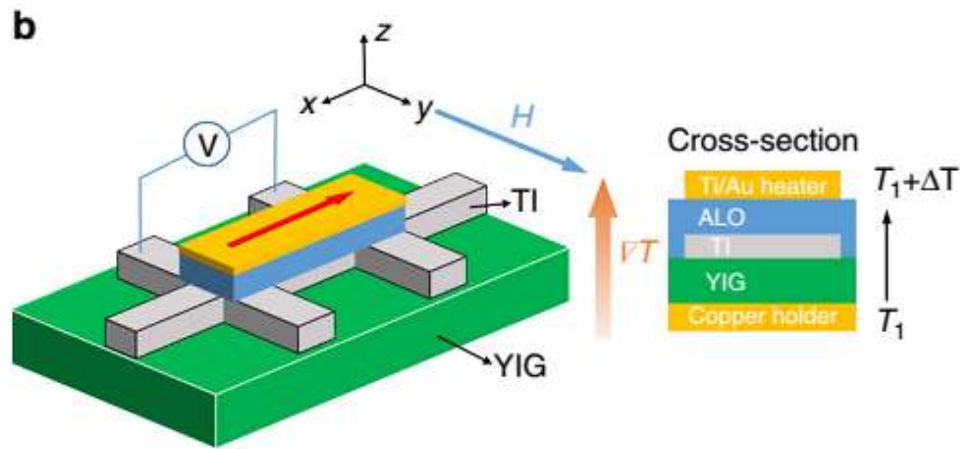
Gate tunable spin orbit torque



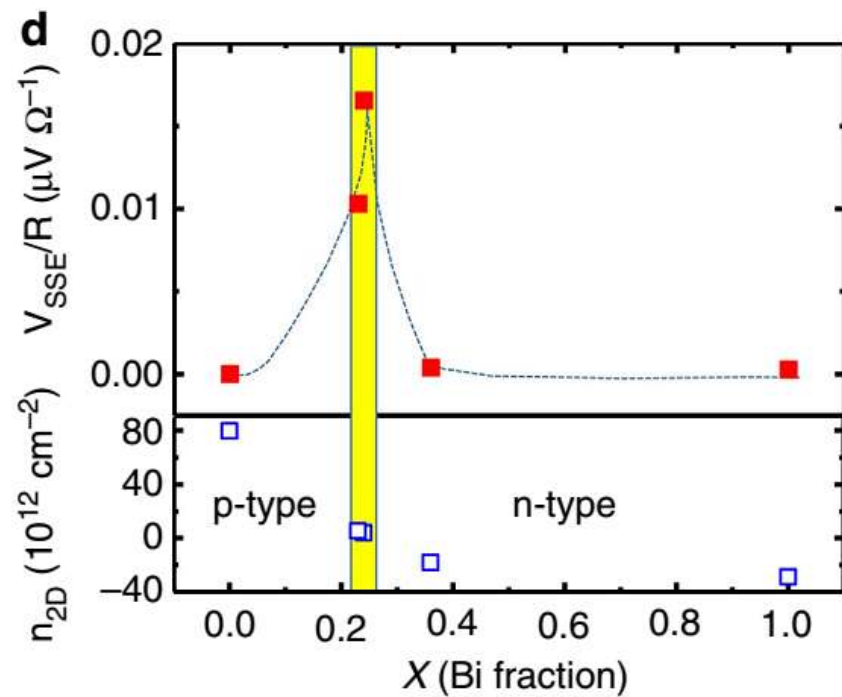
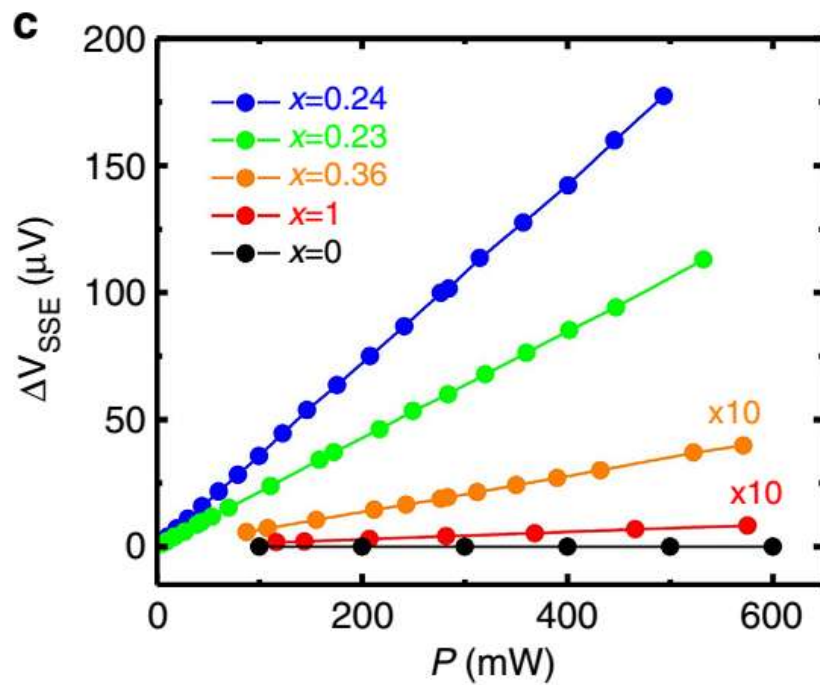
Spin Seebeck effect



Spin Seebeck effect



Spin Seebeck effect



Jinag, et al, Nature Commun. (2016)

Summary

1. Topology

2. Quantum anomalous Hall effect

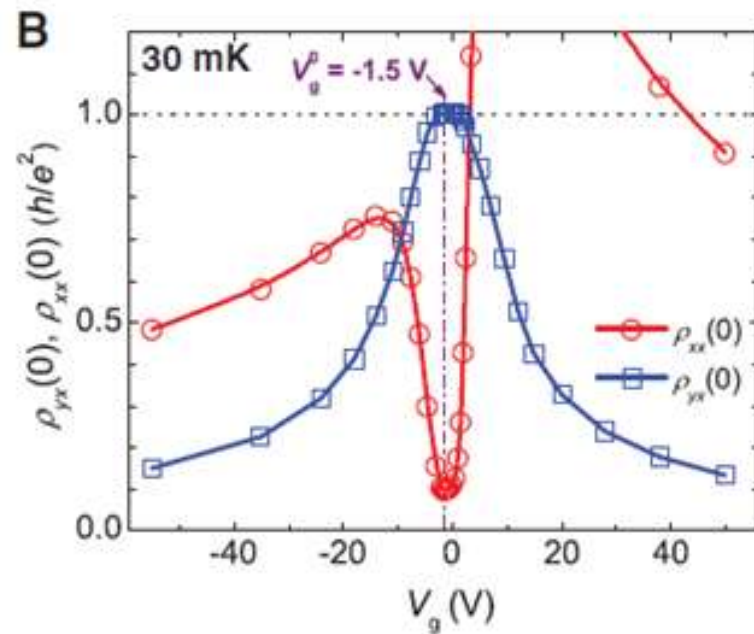
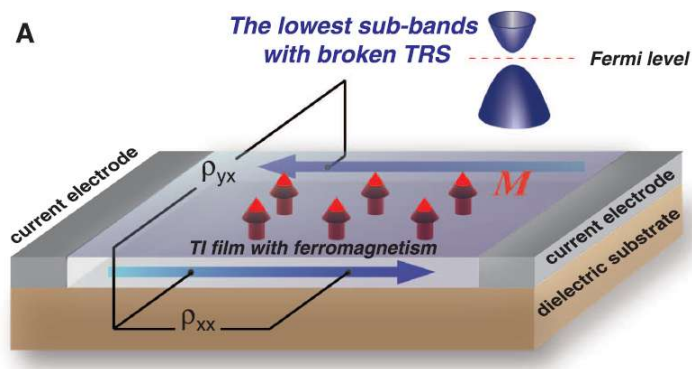
3. Skyrmions

4. Spin-momentum locking of 3D TI

- **Spin injection**
- **Spin orbit torque**
- **Spin Seebeck effect**

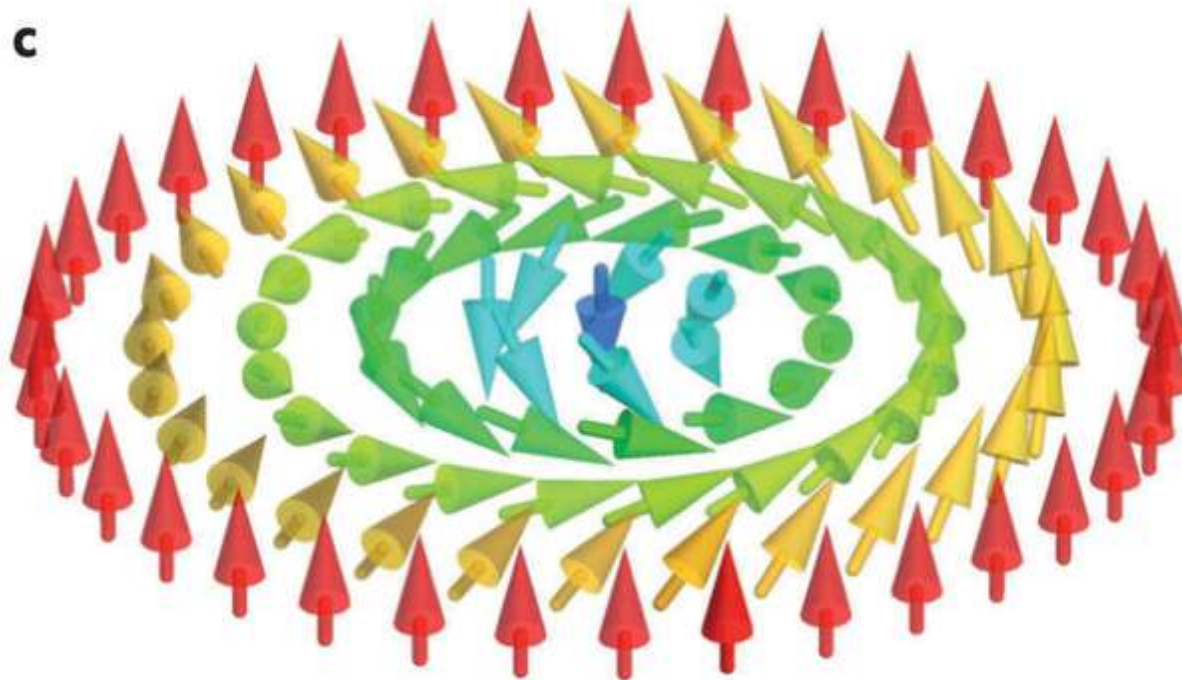
Summary

2. Quantum anomalous Hall effect



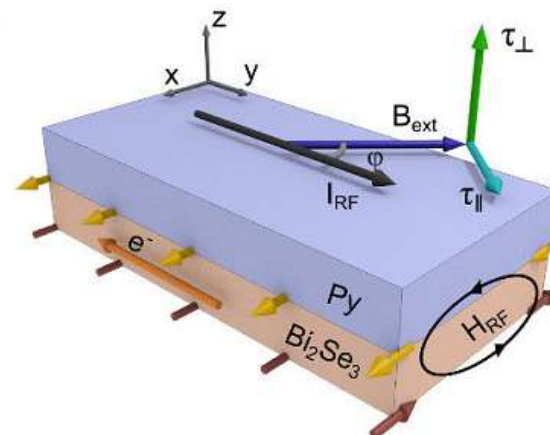
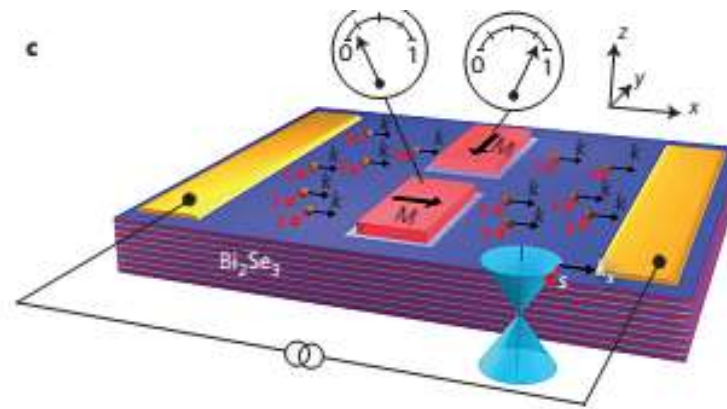
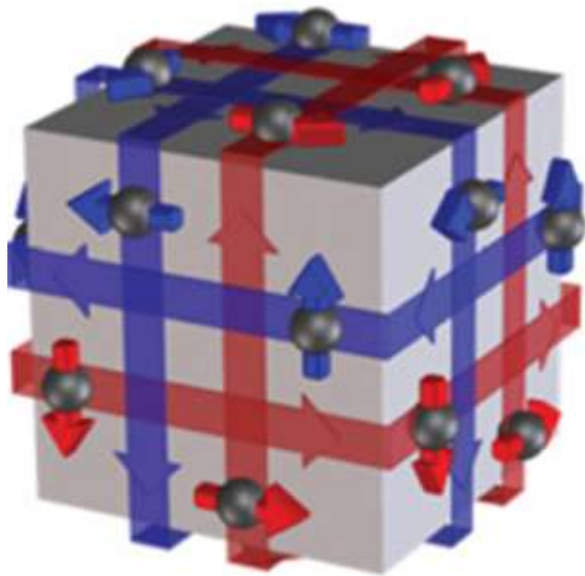
Summary

3. Skyrmions



Summary

4. Spin-momentum locking of 3D TI



最后两节课: Dec. 21th

Date	Group
Dec. 21 st 10:10 am- 11:00 am	Topic: Magnon BEC 何梦云、李思衡、李娜、孙慧敏、陈文杰
Dec. 21 st 11:10 am- 12:00 pm	Topic: Spin FET 张仕雄、丁石磊、梁栋、杨洁、朱鹏飞、赵嘉佑

最后两节课: Dec. 28th

Date	Group
Dec. 28 th 10:10 am- 11:00 am	Topic: Quantum Spin liquids 吉源 孙恺伟 尚念梓 王一帆
Dec. 28 th 11:10 am- 12:00 pm	Topic: Anomalous hall effect/spin hall effect 赵利利, 王善, 闫姣婕, 齐少勉, 李龙飞, 刘震

下一节课: Dec. 14th

Chapter 8: AFM Spintronics

课件下载：

<http://www.phy.pku.edu.cn/~LabSpin/teaching.html>